

PCTEST ENGINEERING LABORATORY, INC.

7185 Oakland Mills Road, Columbia, MD 21046 USA Tel. 410.290.6652 / Fax 410.290.6654 http://www.pctest.com



HEARING AID COMPATIBILITY

Applicant Name:

Samsung Electronics Co., Ltd. 129, Samsung-ro, Maetan dong, Yeongtong-gu, Suwon-si Gyeonggi-do 16677, Korea

Date of Testing: 11/06/2017 - 12/11/2017 **Test Site/Location:** PCTEST Lab, Columbia, MD, USA **Test Report Serial No.:** 1M1711010281-13-R1.A3L

FCC ID: A3LSMG960U

APPLICANT: SAMSUNG ELECTRONICS CO., LTD.

Scope of Test: RF Emissions Testing

Application Type: Certification FCC Rule Part(s): CFR §20.19(b) ANSI C63.19-2011 **HAC Standard:**

CTIA Test Plan for Hearing Aid Compatibility Rev 3.1, February 2017

285076 D01 HAC Guidance v05

285076 D02 T-Coil testing for CMRS IP v03

DUT Type: Portable Handset Model: SM-G960U

Additional Model(s): SM-G960U1, SM-G960W

Test Device Serial No.: Pre-Production Sample [S/N: 86391]

C63.19-2011 HAC

Category:

M4 (RF EMISSIONS CATEGORY)

Note: This revised Test Report (S/N: 1M1711010281-13-R1.A3L) supersedes and replaces the previously issued test report on the same subject device for the same type of testing as indicated. Please discard or destroy the previously issued test report(s) and dispose of it accordingly.

This wireless portable device has been shown to be hearing-aid compatible under the above rated category, specified in ANSI/IEEE Std. C63.19-2011 and has been tested in accordance with the specified measurement procedures. Hearing-Aid Compatibility is based on the assumption that all production units will be designed electrically identical to the device tested in this report. Test results reported herein relate only to the item(s) tested. North America bands only.

I attest to the accuracy of data. All measurements reported herein were performed by me or were made under my supervision and are correct to the best of my knowledge and belief. I assume full responsibility for the completeness of these measurements and vouch for the qualifications of all persons taking them.

Randy Ortanez President







FCC ID: A3LSMG960U	PCTEST H	HAC (RF EMISSIONS) TEST REPORT		Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogg 1 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 1 of 104

TABLE OF CONTENTS

1.	INTRODUCTION	3
2.	DUT DESCRIPTION	4
3.	ANSI/IEEE C63.19 PERFORMANCE CATEGORIES	7
4.	SYSTEM SPECIFICATIONS	8
5.	TEST PROCEDURE	13
6.	SYSTEM CHECK	15
7.	MODULATION INTERFERENCE FACTOR	18
8.	RF CONDUCTED POWER MEASUREMENTS	25
9.	JUSTIFICATION OF HELD TO EAR MODES TESTED	52
10.	LTE TDD UPLINK-DOWNLINK CONFIGURATION	54
11.	OVERALL MEASUREMENT SUMMARY	56
12.	EQUIPMENT LIST	59
13.	MEASUREMENT UNCERTAINTY	60
14.	TEST DATA	61
15.	CALIBRATION CERTIFICATES	71
16.	CONCLUSION	99
17.	REFERENCES	100
18.	TEST PHOTOGRAPHS	102

FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 2 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Faye 2 01 104

1. INTRODUCTION

On July 10, 2003, the Federal Communications Commission (FCC) adopted new rules requiring wireless manufacturers and service providers to provide digital wireless phones that are compatible with hearing aids. The FCC has modified the exemption for wireless phones under the Hearing Aid Compatibility Act of 1998 (HAC Act) in WT Docket 01-309 RM-8658¹ to extend the benefits of wireless telecommunications to individuals with hearing disabilities. These benefits encompass business, social and emergency communications, which increase the value of the wireless network for everyone. An estimated more than 10% of the population in the United States show signs of hearing impairment and of that fraction, almost 80% use hearing aids. Approximately 500 million people worldwide suffer from hearing loss.

Compatibility Tests Involved:

The standard calls for wireless communications devices to be measured for:

- RF Electric-field emissions
- T-coil mode, magnetic-signal strength in the audio band
- T-coil mode, magnetic-signal frequency response through the audio band
- T-coil mode, magnetic-signal and noise articulation index

The hearing aid must be measured for:

- RF immunity in microphone mode
- RF immunity in T-coil mode

In the following tests and results, this report includes the evaluation for a wireless communications device.



Figure 1-1 Hearing Aid in-vitu

¹ FCC Rule & Order, WT Docket 01-309 RM-8658

FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dago 2 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 3 of 104

2. DUT DESCRIPTION



FCC ID: A3LSMG960U

Manufacturer: Samsung Electronics Co., Ltd.

129, Samsung-ro, Maetan dong,

Yeongtong-gu, Suwon-si

Gyeonggi-do 16677, Korea

Model: SM-G960U

Additional Model(s): SM-G960U1, SM-G960W

Serial Number: 86391

Antenna Configurations: Internal Antenna

HAC Test Configurations: Cell. CDMA, 564*, 1013, 384, 777, BT Off, WLAN Off, LTE Off

PCS CDMA, 25, 600, 1175, BT Off, WLAN Off, LTE Off GSM 850, 128, 190, 251, BT Off, WLAN Off, LTE Off GSM 1900, 512, 661, 810, BT Off, WLAN Off, LTE Off

LTE TDD B41 PC2; BW's: 20MHz; 39750, 40185, 40620, 41055, 41490; BT Off, WLAN Off LTE TDD B41 PC3; BW's: 20MHz; 39750, 40185, 40620, 41055, 41490; BT Off, WLAN Off

*Note: Cell. CDMA Ch. 564 is the Part 90S test channel.

DUT Type: Portable Handset

I. LTE Band Selection

This device supports the following pair of LTE bands with similar frequencies: LTE B12 & B17, LTE B26 & B5, LTE B66 & B4, LTE B25 & B2 and LTE B41 & B38. Each pair of LTE bands share the same transmission path. Since the supported frequency spans for the smaller LTE bands are completely covered by the larger LTE bands, only the larger LTE bands (LTE B12, B26, B66, B25, & B41) were evaluated for hearing-aid compliance.

II. Power Reduction for WIFI

This device uses an independent fixed level power reduction mechanism for all WIFI operations during voice or VoIP held to ear scenarios. Reduced powers were used to evaluate for low-power exemption in Section 9.II for WIFI. Detailed descriptions of the power reduction mechanism are included in the operational description.

FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogo 4 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 4 of 104

© 2017 PCTEST Engineering Laboratory, Inc.

REV 3.1.M

Table 2-1: SM-G960U & SM-G960U1 HAC Air Interfaces

Table 2-1: SM-G9600 & SM-G96001 HAC AIR INTERfaces					
Air-Interface	Band (MHz)	Type Transport	HAC Tested	Simultaneous But Not Tested	Name of Voice Service
	835	V0	Vaa	Voc. WIEL on DT	CNADC Voice
CDMA	1900	VO	Yes	Yes: WIFI or BT	CMRS Voice
	EVDO	VD	No ¹	Yes: WIFI or BT	Google Duo
	850	VO	Vos	Yes: WIFI or BT	CMDS Voice
GSM	1900	VO	Yes	Yes: WIFI OF BT	CMRS Voice
	GPRS/EDGE	VD	No ¹	Yes: WIFI or BT	Google Duo
	850				
UMTS	1700	VD	No ¹	Yes: WIFI or BT	CMRS Voice
OIVIT3	1900				
	HSPA	VD	No ¹	Yes: WIFI or BT	Google Duo
	680 (B71)		I No' I Ves: WIFL or RT I		
	700 (B12)			Yes: WIFI or BT	
	700 (B17)				
	780 (B13)				
	800 (B14)				
	850 (B5)				V 175
LTE (FDD)	850 (B26)	VD			VoLTE Google Duo
	1700 (B4)				
	1700 (B66)				
	1900 (B2)				
	1900 (B25)				
	2300 (B30)				
	2500 (B7)				
LTE (TDD)	2600 (B38)	VD	Yes	Yes: WIFI or BT	Google Duo
LIE (IDD)	2600 (B41)	VD	163	Tes. WIIT OF BT	doogle Duo
	2450				
	5200 (U-NII 1)				VoWIFI
WIFI	5300 (U-NII 2A)	VD	No ¹	Yes: CDMA, GSM, UMTS, or LTE	Google Duo
	5500 (U-NII 2C)				22-8-2 - 1-2
	5800 (U-NII 3)				
BT	2450	DT	No	Yes: CDMA, GSM, UMTS, or LTE	N/A
_	У	for CMRS Service Ita Transport	Notes: 1. Evaluated f	or MIF and low-power exemption.	

FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dago 5 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 5 of 104

Table 2-2: SM-G960W HAC Air Interfaces

Air-Interface	Band (MHz)	Type Transport	HAC Tested	Simultaneous But Not Tested	Name of Voice Service
	850	VO	Yes	Yes: WIFI or BT	CMRS Voice
GSM	1900	VO			CIVING VOICE
	GPRS/EDGE	VD	VD No ¹ Yes: WIFI or BT		Google Duo
	850	850			
UMTS	1700	VD	No ¹	Yes: WIFI or BT	CMRS Voice
OIVITS	1900				
	HSPA	VD	No ¹	Yes: WIFI or BT	Google Duo
	700 (B12)				
	700 (B17)				VoLTE Google Duo
	780 (B13)		No ¹	Yes: WIFI or BT	
	850 (B5)	VD			
LTE (FDD)	1700 (B4)				
LIE (FUU)	1700 (B66)				
	1900 (B2)				
	1900 (B25)				
	2300 (B30)				
	2500 (B7)				
LTE (TDD)	2600 (B38)	VD		Caarla Dua	
LTE (TDD)	2600 (B41)	VD	Yes	Yes: WIFI or BT	Google Duo
	2450				
	5200 (U-NII 1)				
WIFI	5300 (U-NII 2A)	VD	No ¹	Yes: GSM, UMTS, or LTE	VoWIFI Google Duo
	5500 (U-NII 2C)				GOOGIE DUO
	5800 (U-NII 3)				
ВТ	2450	DT	No	Yes: GSM, UMTS, or LTE	N/A
Type Transport VO = Voice Only DT = Digital Data - Not intended for CMRS Service VD = CMRS and IP Voice over Data Transport			Notes: 1. Evaluated fo	or MIF and low-power exemption	

FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dago 6 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 6 of 104

3. ANSI/IEEE C63.19 PERFORMANCE CATEGORIES

I. RF EMISSIONS

The ANSI Standard presents performance requirements for acceptable interoperability of hearing aids with wireless communications devices. When these parameters are met, a hearing aid operates acceptably in close proximity to a wireless communications device.

Category	Telephone RF Parameters		
Near field Category	E-field emissions CW dB(V/m)		
	f < 960 MHz		
M1	50 to 55		
M2	45 to 50		
M3	40 to 45		
M4	< 40		
	f > 960 MHz		
M1	40 to 45		
M2	35 to 40		
M3	30 to 35		
M4	< 30		
WD near-field ca	Table 3-1 WD near-field categories as defined in ANSI C63.19-2011		

FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 7 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		raye / 01 104

4. SYSTEM SPECIFICATIONS

ER3DV6 E-Field Probe Description

Construction: One dipole parallel, two dipoles normal to probe axis

Built-in shielding against static charges

Calibration: In air from 100 MHz to 3.0 GHz

(absolute accuracy ±6.0%, k=2)

Frequency: 100 MHz to > 6 GHz;

Linearity: ± 0.2 dB (100 MHz to 3 GHz)

Directivity ± 0.2 dB in air (rotation around probe axis)

± 0.4 dB in air (rotation normal to probe axis)

Dynamic Range 2 V/m to > 1000 V/m

(M3 or better device readings fall well below diode

compression point)

Linearity: ± 0.2 dB

Dimensions Overall length: 330 mm (Tip: 16 mm)

Tip diameter: 8 mm (Body: 12 mm)

Distance from probe tip to dipole centers: 2.5 mm



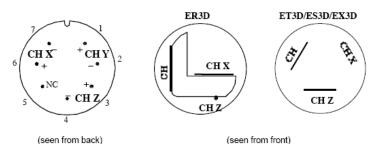
Figure 4-1 E-field Free-space Probe

Probe Tip Description

HAC field measurements take place in the close near field with high gradients. Increasing the measuring distance from the source will generally decrease the measured field values (in case of the validation dipole approx. 10% per mm).

The electric field probes have an irregular internal geometry because it is physically not possible to have the 3 orthogonal sensors situated with the same center. The effect of the different sensor centers is accounted for in the HAC uncertainty budget ("sensor displacement"). Their geometric center is at 2.5mm from the tip, and the element ends are 1.1mm closer to the tip.

Connector Plan



The antistatic shielding inside the probe is connected to the probe connector case.

FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 8 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		rage o or 104

Instrumentation Chain

Equation 1

Conversion of Connector Voltage u, to E-Field E,

$$E_i = \sqrt{\frac{u_i + (u_i^2 \cdot CF)/(DCP)}{Norm_i \cdot ConvF}}$$

whereby

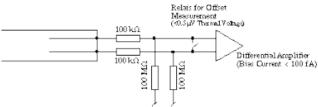
E_i: electric field in V/m

 u_i : voltage of channel i at the connector in μV Norm: sensitivity of channel i in $\mu V/(V/m)^2$ enhancement factor in liquid (ConvF=1 for Air)

DCP: diode compression point in μV

CF: signal crest factor (peak power/average power)

Conditions of Calibration

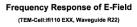


Please note:

- a lower input impedance of the amplifier will result in different sensitivity factors Norm, and DCP
- · larger bias currents will cause higher offset

Probe Response to Frequency

The E-field sensors have inherently a very flat frequency response. They are calibrated with a number of frequencies resulting in a common calibration factor, with the frequency behavior documented in the calibration certificate (See also below).



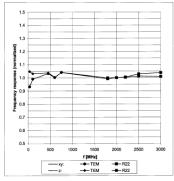


Figure 4-2 E-Field Probe Frequency Response

FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogg 0 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 9 of 104

SPEAG Robotic System

E-field measurements are performed using the DASY5 automated dosimetric assessment system. The DASY5 is made by Schmid & Partner Engineering AG (SPEAG) in Zurich, Switzerland and consists of high precision robotics system (Staubli), robot controller, Intel CORE i7 computer, near-field probe, probe alignment sensor, and the HAC phantom. The robot is a six-axis industrial robot performing precise movements to position the probe to the location (points) of maximum electromagnetic field (EMF).



Figure 4-3 SPEAG Robotic System

System Hardware

A cell controller system contains the power supply, robot controller, teach pendant (Joystick), and a remote control used to drive the robot motors. The PC consists of the computer with operating system and RF Measurement Software DASY5 v52.8 (with HAC Extension), A/D interface card, monitor, mouse, and keyboard. The Staubli Robot is connected to the cell controller to allow software manipulation of the robot. A data acquisition electronic (DAE) circuit that performs the signal amplification, signal multiplexing, AD-conversion, offset measurements, mechanical surface detection, collision detection, etc. is connected to the Electro-optical coupler (EOC). The EOC performs the conversion from the optical into digital electric signal of the DAE and transfers data to the PC plug-in card.

FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogg 10 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 10 of 104

System Electronics

The DAE consists of a highly sensitive electrometer-grade preamplifier with auto-zeroing, a channel and gain-switching multiplexer, a fast 16 bit AD-converter and a command decoder and control logic unit. Transmission to the PC-card is accomplished through an optical downlink for data and status information and an optical uplink for commands and clock lines. The mechanical probe mounting device includes two different sensor systems for frontal and sidewise probe contacts. They are also used for mechanical surface detection and probe collision detection. The robot uses its own controller with a built in VME-bus computer.

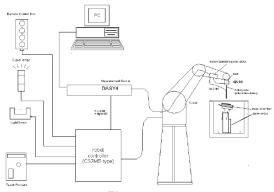


Figure 4-4 SPEAG Robotic System Diagram

DASY5 Instrumentation Chain

The first step of the evaluation is a linearization of the filtered input signal to account for the compression characteristics of the detector diode. The compensation depends on the input signal, the diode type and the DC-transmission factor from the diode to the evaluation electronics. If the exciting field is pulsed, the crest factor of the signal must be known to correctly compensate for peak power. The formula for each channel can be given as:

$$V_i = U_i + U_i^2 \cdot \frac{cf}{dcp_i}$$

with V_i = compensated signal of channel i (i = x, y, z) U_i = input signal of channel i (i = x, y, z) cf = crest factor of exciting field (DASY parameter) dcp_i = diode compression point (DASY parameter)

FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 11 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		raye 1101104

From the compensated input signals the primary field data for each channel can be evaluated:

$$\mathbf{E} - \text{fieldprobes}: \qquad E_i = \sqrt{\frac{V_i}{Norm_i \cdot ConvF}}$$

with V_i = compensated signal of channel i $Norm_i$ = sensor sensitivity of channel i (i = x, y, z)(i = x, v, z)

 $\mu V/(V/m)^2$ for E-field Probes

= sensitivity enhancement in solution

= electric field strength of channel i in V/m

The RSS value of the field components gives the total field strength (Hermitian magnitude):

$$E_{tot} = \sqrt{E_x^2 + E_y^2 + E_z^2}$$

The primary field data are used to calculate the derived field units.

The measurement/integration time per point, as specified by the system manufacturer is >500ms.

The signal response time is evaluated as the time required by the system to reach 90% of the expected final value after an on/off switch of the power source with an integration time of 500ms and a probe response time of <5 ms. In the current implementation, DASY5 waits longer than 100ms after having reached the grid point before starting a measurement, i.e., the response time uncertainty is negligible.

If the device under test does not emit a CW signal, the integration time applied to measure the electric field at a specific point may introduce additional uncertainties due to the discretization. The tolerances for the different systems had the worst-case of 2.6%.

FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 12 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 12 01 104

5. TEST PROCEDURE

I. RF EMISSIONS

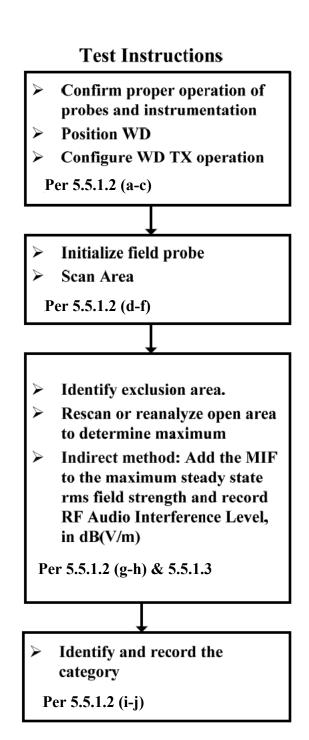


Figure 5-1 RF Emissions Flow Chart

	_			
FCC ID: A3LSMG960U	PCTEST	HAC (RF EMISSIONS) TEST REPORT		Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 13 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Fage 13 01 104

© 2017 PCTEST Engineering Laboratory, Inc.

Test Setup

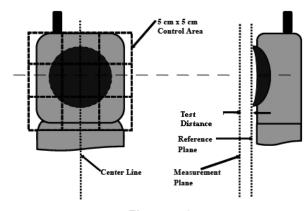


Figure 5-2
E-Field Emissions Test Setup Diagram (See Test Photographs for actual WD scan grid overlay)

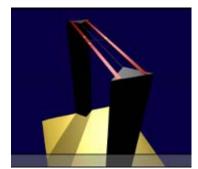


Figure 5-3 HAC Phantom

RF Emissions Test Procedure:

The following illustrate a typical RF emissions test scan over a wireless communications device:

- 1. Proper operation of the field probe, probe measurement system, other instrumentation, and the positioning system was confirmed.
- 2. WD is positioned in its intended test position, acoustic output point of the device perpendicular to the field probe.
- 3. The WD operation for maximum rated RF output power was configured and confirmed with the base station simulator, at the test channel and other normal operating parameters as intended for the test. The battery was ensured to be fully charged before each test.
- 4. The center sub-grid was centered over the center of the acoustic output (also audio band magnetic output, if applicable). The WD audio output was positioned tangent (as physically possible) to the measurement plane.
- 5. A surface calibration was performed before each setup change to ensure repeatable spacing and proper maintenance of the measurement plane using the HAC Phantom.
- 6. The measurement system measured the field strength at the reference location.
- 7. Measurements at 2mm or 5mm increments in the 5 x 5 cm region were performed at a distance 15 mm from the center point of the probe measurement element to the WD. A 360° rotation about the azimuth axis at the maximum interpolated position was measured. For the worst-case condition, the peak reading from this rotation was used in re-evaluating the HAC category.
- 8. The system performed a drift evaluation by measuring the field at the reference location. If the power drift deviated by more than 5%, the HAC test and drift measurements were repeated.

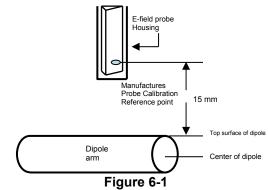
FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 14 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Fage 14 01 104

6. SYSTEM CHECK

I. System Check Parameters

The input signal was an un-modulated continuous wave. The following points were taken into consideration in performing this check:

- Average Input Power P = 100mW RMS (20dBm RMS) after adjustment for return loss
- The test fixture must meet the 2 wavelength separation criterion
- The proper measurement of the 15 mm probe to dipole separation, which is measured from top surface of the dipole to the calibration reference point of the sensor, defined by the probe manufacturer is shown in the following diagram:



Separation Distance from Dipole to Field Probe

RF power was recorded using both an average reading meter and a peak reading meter. Readings of the probe are provided by the measurement system.

To assure proper operation of the near-field measurement probe the input power to the dipole shall be commensurate with the full rated output power of the wireless device [e.g. - for a cellular phone wireless device the average peak antenna input power will be on the order of 100mW (20dBm) RMS] after adjustment for any mismatch.

II. Validation Procedure

A dipole antenna meeting the requirements given in C63.19 was placed in the position normally occupied by the WD.

The length of the dipole was scanned, and the average peak value was recorded.

Measurement of CW

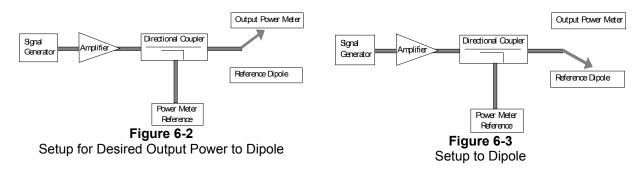
Using the near-field measurement system, scan the antenna over the radiating dipole and record the greatest field reading observed. Due to the nature of E-fields about free-space dipoles, the two E-field peaks measured over the dipole are averaged to compensate for non-parallelity of the setup (see manufacturer method on dipole calibration certificates, page 2). Field strength measurements shall be made only when the probe is stationary.

FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogg 15 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 15 of 104

© 2017 PCTEST Engineering Laboratory, Inc.

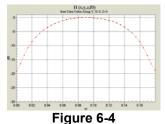
REV 3.1.M

RF power was recorded using both an average and a peak power reading meter.



Using this setup configuration, the signal generator was adjusted for the desired output power (100mW) at a specified frequency. The reference power from the coupled port of the directional coupler is recorded. Next, the output cable is connected to the reference dipole, as shown in Figure 6-3.

The input signal level was adjusted until the reference power from the coupled port of the directional coupler was the same as previously recorded, to compensate for the impedance mismatch between the output cable and the reference dipole. To assure proper operation of the near-field measurement probe the input power to the reference dipole was verified to the full rated output power of the wireless device. The dipole was secured in a holder in a manner to meet the 20 dB reflection. The near-field measurement probe was positioned over the dipole. The antenna was scanned over the appropriate sized area to cover the dipole from end to end. SPEAG uses 2D interpolation algorithms between the measured points. Please see below two dimensional plots showing that the interpolated values interpolate smoothly between 5mm steps for a free-space RF dipole:



2-D Raw Data from scan along dipole axis

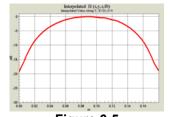
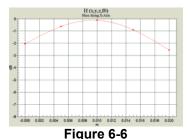


Figure 6-5
2-D Interpolated points from scan along dipole axis



2-D Raw Data from scan along transverse axis



2-D Interpolated points from scan along transverse axis

FCC ID: A3LSMG960U	PCTEST (INCIDENTIAL CALIFORNIAL CALIFORNIA CALIFORA CALIFORNIA CALIFORNIA CALIFORNIA CALIFORNIA CALIFORNIA CALIFORN	HAC (RF EMISSIONS) TEST REPORT		Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 16 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		raye 10 01 104

III. System Check Results

Validation Results

Date	Frequency (MHz)	Probe S/N	DAE S/N	Dipole S/N	Input Power (dBm)	E-field Result (V/m)	Target Field (V/m)	% Deviation
11/6/2017	835	2353	859	1082	20.0	111.6	106.8	4.5%
11/0/2017	1880	2353	859	1064	20.0	95.3	89.6	6.4%
12/11/2017	2600	2353	859	1013	20.0	89.7	84.5	6.2%

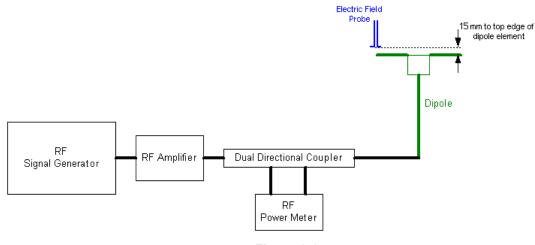


Figure 6-8 System Check Setup

FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogg 17 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 17 of 104

7. MODULATION INTERFERENCE FACTOR

I. Measuring Modulation Interference Factors

For any specific fixed and repeatable modulated signal, a modulation interference factor (MIF, expressed in dB) may be determined that relates its interference potential to its steady-state RMS signal level or average power level. This factor is a function only of the audio-frequency amplitude modulation characteristics of the signal and is the same for field-strength and conducted power measurements. The MIF is valid only for a specific repeatable audio-frequency amplitude modulation characteristic; any change in modulation characteristic requires determination and application of a new MIF.

The MIF may be determined using a radiated RF field or a conducted RF signal:

- a. Using RF illumination or conducted coupling, apply the specific modulated signal in question to the measurement system at a level within its confirmed operating dynamic range.
- b. Measure the steady-state RMS level at the output of the fast probe or sensor.
- c. Measure the steady-state average level at the weighting output.
- d. Without changing the square-law detector or weighting system, and using RF illumination or conducted coupling, substitute for the specific modulated signal a 1 kHz, 80% amplitude modulated carrier at the same frequency and adjust its strength until the level at the weighting output equals the step c) measurement.
- e. Without changing the carrier level from step d), remove the 1 kHz modulation and again measure the steady-state RMS level indicated at the output of the fast probe or sensor.
- f. The MIF for the specific modulation characteristic is provided by the ratio of the step e) measurement to the step b) measurement, expressed in dB (20 × log[(step e)/(step b)]).

The following procedure was used to measure the MIF using the SPEAG Audio Interference Analyzer (AIA), Type No: SE UMS 170 CB, Serial No.: 1010:

- 1. The device was placed into a simulated call using a base station simulator or set to transmit using test software for a given mode.
- 2. The device was then set to continuously transmit at maximum power.
- 3. Using a coupler if needed, the device output signal was connected to the RF In port of the AIA, which was connected to a desktop computer. Alternatively, a radiated RF signal may be used with the AIA's built-in antenna.
- 4. The MIF measurement procedure in the DASY software was run, and the resulting MIF value was recorded.
- 5. Steps 1-4 were repeated for all CMRS air interfaces, frequency bands, and modulations.

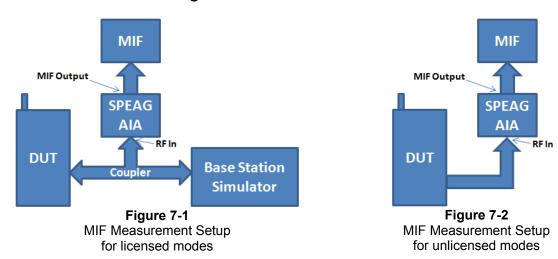
The modulation interference factors obtained were applied to readings taken of the actual wireless device in order to obtain an accurate audio interference level reading using the formula:

Audio Interference Level [dB(V/m)] = 20 * log[Raw Field Value (V/m)] + MIF (dB)

Because the MIF value is output power independent, MIF values for a given mode should be constant across all devices; however, per C63.19-2011 §D.7, MIF values should be measured for each device being evaluated. The voice modes for this device have been investigated in this section of the report.

FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 18 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		rage 10 01 104

II. MIF Measurement Block Diagrams



III. Measured Modulation Interference Factors:

Table 7-1CDMA Modulation Interference Factors¹

	CDIVIA MODULATION INTERPRETACIONS							
		Cell				PCS		
Mo	ode	908	22H	22H	22H	24E	24E	24E
		564	1013	384	777	25	600	1175
	RC1/SO3	3.07	3.05	3.03	3.04	3.02	3.02	3.05
CDMA	RC1/SO55	-19.58	-19.83	-19.63	-19.48	-19.61	-19.60	-19.61
	EVDO	-19.33	-19.75	-20.04	-19.70	-19.95	-19.85	-20.24

Table 7-2GSM Modulation Interference Factors¹

Mode			GSM850		GSM1900				
		128	190	251 512 661					
GSM	Voice	3.55	3.55	3.55	3.56	3.56	3.56		
GSIVI	EDGE	3.76	3.77	3.78	3.56	3.40	3.26		

¹ Note: Measured MIF values may be lower than sample MIF values provided in ANSI C63.19-2011 Annex D.7 Table D.5 due to manufacturing variations for each device, however per Annex D.7, the sample MIF values of Table D.5 are not intended to substitute for measurements of actual devices under test and their respective operating modes.

FCC ID: A3LSMG960U	PCTEST*	HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 19 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Fage 19 01 104

Table 7-3 UMTS Modulation Interference Factors¹

M	odo	UMTS V				UMTS IV		UMTS II		
Mode		4132	4183	4233	1312	1412	1513	9262	9400	9538
	12.2 kbps RMC	-24.30	-24.12	-21.12	-23.70	-24.23	-25.01	-24.33	-24.49	-24.71
UMTS	12.2 kbps AMR	-12.84	-12.98	-13.05	-13.16	-12.95	-12.77	-12.82	-12.87	-12.88
	HSUPA Subtest1	-23.47	-22.95	-22.21	-23.45	-23.28	-23.53	-22.99	-23.48	-23.27

Table 7-4 LTE FDD Modulation Interference Factors 1,2,3

LTE Band	Frequency [MHz]	Channel	Bandwidth [MHz]	Modulation	RB Size	RB Offset	MIF [dB]
71	680.5	133297	20	16QAM	1	0	-9.78
12	707.5	23095	10	16QAM	1	0	-9.87
13	782.0	23230	10	16QAM	1	0	-9.65
14	793.0	2330	10	16QAM	1	0	-9.73
26	831.5	26865	15	16QAM	1	0	-9.78
66	1745.0	132322	20	16QAM	1	0	-9.85
25	1882.5	26365	20	16QAM	1	0	-9.70
7	2535.0	21100	20	16QAM	1	0	-9.81
30	2310.0	27710	10	16QAM	1	0	-9.77
13	782.0	23230	10	QPSK	1	0	-13.90
13	782.0	23230	10	64QAM	1	0	-9.66
13	782.0	23230	10	16QAM	1	25	-9.69
13	782.0	23230	10	16QAM	1	49	-9.53
13	782.0	23230	10	16QAM	25	0	-15.36
13	782.0	23230	10	16QAM	50	0	-16.96
13	782.0	23230	5	16QAM	1	24	-9.61

¹ Note: Measured MIF values may be lower than sample MIF values provided in ANSI C63.19-2011 Annex D.7 Table D.5 due to manufacturing variations for each device, however per Annex D.7, the sample MIF values of Table D.5 are not intended to substitute for measurements of actual devices under test and their respective operating modes.

FCC ID: A3LSMG960U	PCTEST	HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 20 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Fage 20 01 104

² Note: All FDD LTE bands were found to have substantially similar MIF values given similar RB, BW, and modulation configurations.

³ Note: Since LTE Band 13 at 10 MHz bandwidth is the overall worst case LTE MIF and does not support 3 nonoverlapping channels, MIF measurements were made only on the middle channel.

Table 7-5 LTE TDD Power Class 3 Modulation Interference Factors^{1,2}

	ETE TEET OWE Glass of Modulation interference Lactors									
LTE Band	Frequency [MHz]	Channel	Bandwidth [MHz]	Modulation	RB Size	RB Offset	MIF [dB]			
41	2593.0	40620	20	16QAM	1	0	1.62			
41	2593.0	40620	20	QPSK	1	0	1.43			
41	2593.0	40620	20	64QAM	1	0	1.41			
41	2593.0	40620	20	16QAM	1	50	1.60			
41	2593.0	40620	20	16QAM	1	99	1.60			
41	2593.0	40620	20	16QAM	50	0	1.35			
41	2593.0	40620	20	16QAM	100	0	1.34			
41	2593.0	40620	15	16QAM	1	0	1.61			
41	2593.0	40620	10	16QAM	1	0	1.59			
41	2593.0	40620	5	16QAM	1	0	1.60			
41	2506.0	39750	20	16QAM	1	0	1.61			
41	2549.5	40185	20	16QAM	1	0	1.62			
41	2636.5	41055	20	16QAM	1	0	1.60			
41	2680.0	41490	20	16QAM	1	0	1.61			

Table 7-6 LTE TDD Power Class 2 Modulation Interference Factors^{1,2}

				diation int			
LTE Band	Frequency [MHz]	Channel	Bandwidth [MHz]	Modulation	RB Size	RB Offset	MIF [dB]
41	2593	40620	20	16QAM	1	0	1.67
41	2593	40620	20	QPSK	1	0	1.45
41	2593	40620	20	64QAM	1	0	1.46
41	2593	40620	20	16QAM	1	50	1.65
41	2593	40620	20	16QAM	1	99	1.64
41	2593	40620	20	16QAM	50	0	1.40
41	2593	40620	20	16QAM	100	0	1.39
41	2593	40620	15	16QAM	1	0	1.65
41	2593	40620	10	16QAM	1	0	1.64
41	2593	40620	5	16QAM	1	0	1.65
41	2506.0	39750	20	16QAM	1	0	1.65
41	2549.5	40185	20	16QAM	1	0	1.65
41	2636.5	41055	20	16QAM	1	0	1.64
41	2680.0	41490	20	16QAM	1	0	1.65

Table 7-7 LTE TDD Uplink Carrier Aggregation Modulation Interference Factor^{1,3}

					, op	Ou	0. , 	. 09466	,,,,,,,,,	ala tioi		01.00				
		PCC							SCC							
	Combination	PCC Band	PCC Bandwidth [MHz]		PCC (UL/DL) Frequency [MHz]	Modulation	PCC UL# RB	PCC UL RB Offset	SCC Band	SCC Bandwidth [MHz]	SCC (UL/DL) Channel	SCC (UL/DL) Frequency [MHz]	Modulation	SCC UL# RB	SCC UL RB Offset	MIF (dB)
ĺ	CA_41C	LTE B41	20	40185	2549.5	16QAM	1	0	LTE B41	20	39987	2529.7	16QAM	1	99	1.47

¹ Note: Measured MIF values may be lower than sample MIF values provided in ANSI C63.19-2011 Annex D.7 Table D.5 due to manufacturing variations for each device, however per Annex D.7, the sample MIF values of Table D.5 are not intended to substitute for measurements of actual devices under test and their respective operating modes.

³ Note: The configuration for LTE TDD ULCA was determined from the worst-case configuration from Table 7-5. The worst-case channel 40185 was evaluated to ensure worst case modulation was evaluated for PCC due to the CA combination constraint of CA 41C.

FCC ID: A3LSMG960U	PCTEST	HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dago 21 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 21 of 104

² Note: LTE TDD MIFs for both Power Class 3 and Power Class 2 were taken using UL-DL Configuration 2. More information about the chosen UL-DL Configuration can be found in Section 10.

Table 7-8802.11b (2.4GHz. SISO) Modulation Interference Factors^{1,2}

	802.1	1b MIF Mea	asurement	s [dB]					
Mode		Data Rate [Mbps]							
	1 2 5.5 11								
802.11b	-10.29	-10.29 -9.58 -7.34 -6.38							

Table 7-9

802.11g (2.4GHz, SISO) Modulation Interference Factors^{1,2}

		`	802.1	1g MIF Me	asurement	s [dB]					
Mode		Data Rate [Mbps]									
	6 9 12 18 24 36 48 5										
802.11g	-7.58	7.58 -6.79 -6.24 -5.46 -5.11 -4.79 -4.81 -5.01									

Table 7-10

802.11g (2.4GHz, MIMO) Modulation Interference Factors^{1,2}

		`	802.1	1g MIF Me	asurement	s [dB]			
Mode		Data Rate [Mbps]							
	12	18	24	36	48	72	96	108	
802.11g	-7.57	-6.78	-6.25	-5.46	-5.10	-4.75	-4.74	-5.01	

Table 7-11

802.11n (2.4GHz, SISO) Modulation Interference Factors^{1,2}

		•	802.11n (2	.4GHz) MIF	Measurer	ments [dB]						
Mode		Data Rate [Mbps]										
	6.5	13	19.5	26	39	52	58.5	65				
802.11n	-7.47	-7.47 -6.18 -5.51 -5.09 -4.82 -4.83 -4.95 -5.06										

Table 7-12

802.11n (2.4GHz, MIMO) Modulation Interference Factors^{1,2}

	802.11n (2.4GHz) MIF Measurements [dB]											
Mode		Data Rate [Mbps]										
	13	26	39	52	78	104	117	130				
802.11n	-7.46	-7.46 -6.17 -5.51 -5.08 -4.81 -4.82 -4.94 -5.05										

Table 7-13

802.11a (5GHz. 20MHz BW. SISO) Modulation Interference Factors^{1,2}

		802.11a MIF Measurements [dB]										
Mode		Data Rate [Mbps]										
	6	9	12	18	24	36	48	54				
802.11a	-13.77	-13.77 -12.89 -12.65 -11.64 -11.55 -11.92 -12.39 -13.36										

Table 7-14

802.11a (5GHz, 20MHz BW, MIMO) Modulation Interference Factors^{1,2}

	,	802.11a MIF Measurements [dB]										
Mode		Data Rate [Mbps]										
	12	18	24	36	48	72	92	108				
802.11a	-13.56	-13.56 -12.87 -12.33 -11.25 -11.46 -11.86 -12.19 -13.33										

¹ Note: Measured MIF values may be lower than sample MIF values provided in ANSI C63.19-2011 Annex D.7 Table D.5 due to manufacturing variations for each device, however per Annex D.7, the sample MIF values of Table D.5 are not intended to substitute for measurements of actual devices under test and their respective operating modes.

² Note: WIFI MIF values were found to be independent of the transmit channel.

FCC ID: A3LSMG960U	PETEST*	IAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 22 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Fage 22 01 104

Table 7-15

802.11n (5GHz, 20MHz BW, SISO) Modulation Interference Factors^{1,2}

	\	20MH	lz BW 802	.11n (5GHz) MIF Mea	surements	[dB]				
Mode		Data Rate [Mbps]									
	6.5	13	19.5	26	39	52	58.5	65			
802.11n	-13.62	-12.44	-12.01	-11.77	-11.99	-12.41	-12.89	-13.06			

Table 7-16

802 11n (5GHz 20MHz BW MIMO) Modulation Interference Factors^{1,2}

002.1	111 (001	2, 2011111	<u> </u>	11010) 1010	adiation	1111011010	1100 1 401	010					
		20MHz BW 802.11n (5GHz) MIF Measurements [dB]											
Mode		Data Rate [Mbps]											
	13	26	39	52	78	104	117	130					
802.11n	-13.02	-12.42	-12.01	-11.66	-11.89	-12.32	-12.03	-13.00					

Table 7-17

802.11ac (5GHz, 20MHz BW, SISO) Modulation Interference Factors^{1,2}

	<u> </u>	00112, 2	OIVII IZ D	•••, C.CC	, ivioaaic	ation into	110101100	1 401010				
			20MHz BW	802.11ac	(5GHz) MII	F Measure	ments [dB]					
Mode		Data Rate [Mbps]										
	6.5 13 19.5 26 39 52 58.5 65 78											
802.11ac	-13.72	-12.63	-11.88	-11.72	-11.90	-12.43	-12.69	-13.01	-13.33			

Table 7-18

802.11ac (5GHz, 20MHz BW, MIMO) Modulation Interference Factors^{1,2}

			20MHz BW	/ 802.11ac	(5GHz) MII	F Measure	ments [dB]						
Mode		Data Rate [Mbps]											
	13	26	39	52	78	104	117	130	156				
802.11ac	-12.20	-11.85	-11.94	-12.19	-13.17	-13.08	-13.12	-13.18	-14.87				

Table 7-19

802.11n (5GHz, 40MHz BW, SISO) Modulation Interference Factors^{1,2}

	40MHz BW 802.11n (5GHz) MIF Measurements [dB]											
Mode		Data Rate [Mbps]										
	13.5	27	40.5	54	81	108	121.5	135				
802.11n	-11.67	-11.06	-11.46	-11.94	-13.30	-14.16	-14.64	-15.12				

Table 7-20

802.11n (5GHz, 40MHz BW, MIMO) Modulation Interference Factors^{1,2}

002.1	111 (3011	iz, Tolvil i		IIVIO) IVIO	dulation	IIIICIICIC	nice i aci	013		
		40MI	Iz BW 802	2.11n (5GHz) MIF Measurements [dB]						
Mode	Data Rate [Mbps]									
	27	54	81	108	162	216	243	270		
802.11n	-11.64	-11.03	-11.49	-11.95	-11.97	-14.11	-14.63	-15.09		

Table 7-21

802.11ac (5GHz, 40MHz BW, SISO) Modulation Interference Factors^{1,2}

		40MHz BW 802.11ac (5GHz) MIF Measurements [dB]										
Mode		Data Rate [Mbps]										
	13.5	27	40.5	54	81	108	121.5	135	180			
802.11ac	-11.61	-10.82	-11.30	-11.86	-13.15	-14.08	-14.37	-14.66	-15.43			

¹ Note: Measured MIF values may be lower than sample MIF values provided in ANSI C63.19-2011 Annex D.7 Table D.5 due to manufacturing variations for each device, however per Annex D.7, the sample MIF values of Table D.5 are not intended to substitute for measurements of actual devices under test and their respective operating modes.

² Note: WIFI MIF values were found to be independent of the transmit channel.

FCC ID: A3LSMG960U	PETEST*	IAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 23 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Fage 23 01 104

Table 7-22 802.11ac (5GHz, 40MHz BW, MIMO) Modulation Interference Factors^{1,2}

					(5GHz) MIF							
Mode		Data Rate [Mbps]										
	27 54 81 108 162 216 243 270 360											
802.11ac	-11.03	1.03 -11.93 -13.10 -14.09 -14.92 -16.30 -16.67 -16.54 -16.28										

Table 7-23

802 11ac (5GHz 80MHz BW, SISO) Modulation Interference Factors^{1,2}

		002.110	ooz. That (och iz, cominz bw, cloo) modalation interior action												
		80MHz BW 802.11ac (5GHz) MIF Measurements [dB]													
Мо	Mode Data Rate [Mbps]														
		29.3 58.5 87.8 117 175.5 234 263.3 292.5 351 39													
802.	11ac	-11.34	1.34 -12.47 -13.54 -14.32 -15.43 -16.62 -16.08 -15.78 -16.12 -17.26												

Table 7-24

802.11ac (5GHz, 80MHz BW, MIMO) Modulation Interference Factors^{1,2}

			80MH	z BW 802.	11ac (5GH	z) MIF Mea	surement	s [dB]		
Mode	Data Rate [Mbps] 58.5 117 175.5 234 351 468 526.5 585 702 780									
										780
802.11ac	-11.71	-13.68	-13.65	-14.34	-16.66	-17.33	-17.34	-17.83	-17.85	-18.39

Table 7-25

Simultaneous 2.4GHz and 5GHz WIFI Modulation Interference Factors^{1,2,3}

# Tx		z WIFI Bm]		łz WIFI Bm]	Measured MIF
ıx.	Ant1	Ant2	Ant1	Ant2	(dB)
2	х	-	-	х	-6.00
2	-	х	х	-	-6.09
2	x	-	х	-	-5.79
2	-	х	-	х	-6.36
3	х	х	х	-	-5.96
3	х	х	-	х	-6.44
3	х	-	х	х	-6.21
3	-	х	х	х	-5.45
4	х	х	х	х	-6.65

¹ Note: Measured MIF values may be lower than sample MIF values provided in ANSI C63.19-2011 Annex D.7 Table D.5 due to manufacturing variations for each device, however per Annex D.7, the sample MIF values of Table D.5 are not intended to substitute for measurements of actual devices under test and their respective operating modes.

³ Note: The configuration for each scenario (e.g. bandwidth, data rate, etc.) was determined using the worst-case configuration from SISO and MIMO MIF measurements.

FCC ID: A3LSMG960U	PCTEST	HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 24 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Fage 24 01 104

² Note: WLAN MIF values were found to be independent of the transmit channel.

8. RF CONDUCTED POWER MEASUREMENTS

I. Procedures Used to Establish RF Signal for HAC Testing

The handset was placed into a simulated call using a base station simulator in a shielded chamber. Such test signals offer a consistent means for testing HAC and are recommended for evaluating HAC. Measurements were taken with a fully charged battery. In order to verify that the device was tested and maintained at full power, this was configured with the base station simulator.

II. HAC Measurement Conditions

Output Power Verification

Maximum output power is verified on the High, Middle and Low channels for all applicable air interfaces. See Table 8-1 for air interface specific settings of transmit power parameters.

Table 8-1
Power Control Parameters and Settings by Air Interface

Air Interface:	Parameter Name:	Parameter Set To:
CDMA	Power Control Bits	"All Up"
GSM	PCL	GSM850: "5"; GSM1900: "0"
UMTS	TPC	"All 1's"
LTE	TPC	"Max Power"
WIFI	PLS	Mfr Specified

III. Setup Used to Measure RF Conducted Powers

Power measurements for licensed modes were performed using a base station simulator under digital average power. Power measurements for unlicensed modes were performed using a power meter and power sensor.

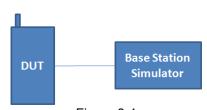


Figure 8-1 Power Measurement Setup for licensed modes

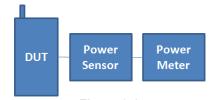


Figure 8-2
Power Measurement Setup for unlicensed modes

IV. CDMA Conducted Powers

Band	Channel	Rule Part	Frequency	SO2 [dBm]	SO2 [dBm]	SO2 [dBm]	SO55 [dBm]	SO55 [dBm]	SO75 [dBm]	SO9 [dBm]	SO9 [dBm]	SO3 [dBm]	SO3 [dBm]	SO3 [dBm]	1x EvDO Rev. A [dBm]
	F-RC		MHz	RC1	RC3	RC4	RC1	RC3	RC11	RC2	RC5	RC1	RC3	RC4	(RETAP)
Cellular	564	90S	820.1	24.86	24.85	24.86	24.88	24.84	24.84	24.88	24.84	24.83	24.84	24.85	24.87
	1013	22H	824.7	24.35	24.33	24.34	24.36	24.34	24.35	24.36	24.32	24.31	24.32	24.33	24.44
Cellular	384	22H	836.52	24.51	24.48	24.49	24.51	24.49	24.47	24.52	24.48	24.45	24.48	24.48	24.59
	777	22H	848.31	24.52	24.50	24.51	24.54	24.51	24.52	24.54	24.50	24.47	24.50	24.50	24.58
	25	24E	1851.25	24.24	24.27	24.29	24.31	24.25	24.23	24.29	24.27	24.25	24.28	24.29	24.10
PCS	600	24E	1880	24.16	24.17	24.15	24.19	24.17	24.16	24.18	24.16	24.16	24.22	24.22	24.01
	1175	24E	1908.75	24.32	24.32	24.28	24.30	24.32	24.29	24.28	24.33	24.30	24.31	24.33	24.15

FCC ID: A3LSMG960U	PCTEST HA	AC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogo 25 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 25 of 104

© 2017 PCTEST Engineering Laboratory, Inc.

V. GSM Conducted Powers

Band	Channel	GSM [dBm] CS (1 Slot)	EDGE [dBm] 1 Tx Slot
	128	32.87	27.00
GSM 850	190	32.80	26.89
	251	33.00	26.99
	512	29.64	25.48
GSM 1900	661	29.47	25.31
	810	29.64	25.49

VI. UMTS Conducted Powers

Mode 3GPP 34.121 Subtest		Cellular Band [dBm]			AWS Band [dBm]			PCS Band [dBm]		
	Subtest	4132	4183	4233	1312	1412	1513	9262	9400	9538
WCDMA	12.2 kbps RMC	24.68	24.67	24.69	24.12	24.05	24.06	24.00	24.01	24.03
VVCDIVIA	12.2 kbps AMR	24.69	24.72	24.68	24.08	24.05	24.07	23.97	23.99	24.01
HSUPA	Subtest 1	23.98	23.70	23.85	23.24	23.14	23.19	23.17	23.20	23.22

VII. LTE Conducted Powers

a. LTE Band 71

Table 8-2 LTE Band 71 (680.5MHz) Conducted Powers – 20MHz Bandwidth

	. (000.		LTE Band 71 20 MHz Bandwidth		
Modulation	RB Size	RB Offset	Mid Channel 133297 (680.5 MHz) Conducted Power [dBm]	MPR Allowed per 3GPP [dB]	MPR [dB]
	1	0	24.81		0
	1	50	24.64	0	0
	1	99	24.28		0
QPSK	50	0	23.83		1
	50	25	23.72	0-1	1
	50	50	23.60	0-1	1
	100	0	23.70		1
	1	0	23.92		1
	1	50	23.87	0-1	1
	1	99	23.40		1
16QAM	50	0	22.90		2
	50	25	22.80	0-2	2
	50	50	22.64) °2	2
	100	0	22.73		2
	1	0	23.00		2
	1	50	22.98	0-2	2
	1	99	22.61		2
64QAM	50	0	21.91		3
	50	25	21.83	0-3	3
	50	50	21.66		3
	100	0	21.76		3

Note: Since LTE Band 71 at 20MHz bandwidth does not support 3 non-overlapping channels, conducted power measurements were made only on the middle channel.

FCC ID: A3LSMG960U	PCTEST HA	AC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogg 26 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 26 of 104

Table 8-3
LTE Band 71 (680.5MHz) Conducted Powers – 15MHz Bandwidth

			LTE Band 71 15 MHz Bandwidth		
			Mid Channel		
Modulation	RB Size	RB Offset	133297 (680.5 MHz) Conducted Power [dBm]	MPR Allowed per 3GPP [dB]	MPR [dB]
	1	0	24.65		0
	1	36	24.59	0	0
	1	74	24.37		0
QPSK	36	0	23.68		1
	36	18	23.65	0-1	1
	36	37	23.52	0-1	1
	75	0	23.66		1
	1	0	23.87		1
	1	36	23.72	0-1	1
	1	74	23.46		1
16QAM	36	0	22.79		2
	36	18	22.71	0-2	2
	36	37	22.67	0-2	2
	75	0	22.63		2
	1	0	22.91		2
	1	36	22.87	0-2	2
	1	74	22.59		2
64QAM	36	0	21.75		3
	36	18	21.71	0-3	3
	36	37	21.62	0-3	3
	75	0	21.68		3

Note: Since LTE Band 71 at 15MHz bandwidth does not support 3 non-overlapping channels, conducted power measurements were made only on the middle channel.

Table 8-4
LTE Band 71 (680.5MHz) Conducted Powers – 10MHz Bandwidth

			(:::3:0:::::=)	LTE Band 71		- Banawiati	
				10 MHz Bandwidth			
			Low Channel	Mid Channel	High Channel		
Modulation	RB Size	RB Offset	133172 (668.0 MHz)	133297 (680.5 MHz)	133422 (693.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			d	Conducted Power [dBm	n]		
	1	0	24.65	24.56	24.52		0
	1	25	24.61	24.54	24.38	0	0
	1	49	24.52	24.43	24.23		0
QPSK	25	0	23.71	23.60	23.51		1
	25	12	23.63	23.62	23.40	0-1	1
	25	25	23.62	23.58	23.35		1
	50	0	23.67	23.54	23.44		1
	1	0	23.82	23.82	23.78		1
	1	25	23.83	23.88	23.72	0-1	1
	1	49	23.77	23.73	23.51		1
16QAM	25	0	22.80	22.68	22.64		2
	25	12	22.78	22.65	22.50	0-2	2
	25	25	22.66	22.57	22.46	0-2	2
	50	0	22.71	22.69	22.52		2
	1	0	22.87	22.83	22.81		2
	1	25	22.75	22.68	22.64	0-2	2
	1	49	22.61	22.59	22.51		2
64QAM	25	0	21.74	21.76	21.65		3
	25	12	21.68	21.66	21.53	0-3	3
	25	25	21.62	21.59	21.43	0-3	3
	50	0	21.71	21.67	21.59		3

FCC ID: A3LSMG960U	PCTEST	HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 27 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		raye 21 01 104

Table 8-5 LTE Band 71 (680.5MHz) Conducted Powers - 5MHz Bandwidth

				LTE Band 71 5 MHz Bandwidth			
			Low Channel	Mid Channel	High Channel		
Modulation RB Siz	RB Size	RB Offset	133147 (665.5 MHz)	133297 (680.5 MHz)	133447 (695.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			(Conducted Power [dBm	1]		
	1	0	24.67	24.64	24.28		0
	1	12	24.49	24.52	24.20	0	0
	1	24	24.53	24.49	24.21		0
QPSK	12	0	23.57	23.59	23.22		1
	12	6	23.58	23.62	23.21	0-1	1
	12	13	23.64	23.57	23.25	0-1	1
	25	0	23.69	23.61	23.23		1
	1	0	23.84	23.86	23.53		1
	1	12	23.77	23.78	23.51	0-1	1
	1	24	23.78	23.79	23.55	1	1
16QAM	12	0	22.69	22.71	22.44		2
	12	6	22.76	22.73	22.38	0-2	2
	12	13	22.75	22.68	22.34	0-2	2
	25	0	22.71	22.64	22.31	1	2
	1	0	22.79	22.79	22.53		2
	1	12	22.76	22.81	22.46	0-2	2
	1	24	22.65	22.72	22.45	7	2
64QAM	12	0	21.70	21.71	21.41		3
	12	6	21.66	21.72	21.36	0-3	3
	12	13	21.63	21.69	21.33	0-3	3
	25	0	21.73	21.66	21.37	7	3

b. LTE Band 12

Table 8-6 LTE Band 12 (707.5MHz) Conducted Powers - 10MHz Bandwidth

			LTE Band 12 10 MHz Bandwidth		
			Mid Channel		
Modulation	RB Size	RB Offset	23095 (707.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			Conducted Power		
			[dBm]		
	1	0	24.47		0
	1	25	24.57	0	0
	1	49	24.46		0
QPSK	25	0	23.66		1
	25	12	23.62	0-1	1
	25	25	23.53	0-1	1
	50	0	23.60		1
	1	0	23.50		1
	1	25	23.79	0-1	1
	1	49	23.55		1
16QAM	25	0	22.76		2
	25	12	22.70	0-2	2
	25	25	22.62	0-2	2
	50	0	22.69		2
	1	0	22.57		2
	1	25	22.86	0-2	2
	1	49	22.70		2
64QAM	25	0	21.75		3
	25	12	21.70		3
	25	25	21.64	0-3	3
	50	0	21.71		3

Note: Since LTE Band 12 at 10MHz bandwidth does not support 3 non-overlapping channels, conducted power measurements were made only on the middle channel.

FCC ID: A3LSMG960U	PCTEST HA	AC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogg 20 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 28 of 104

Table 8-7
LTE Band 12 (707.5MHz) Conducted Powers – 5MHz Bandwidth

				LTE Band 12 5 MHz Bandwidth			
			Low Channel	Mid Channel	High Channel	MPR Allowed per	
Modulation RB Size	RB Size	RB Offset	23035 (701.5 MHz)	23095 (707.5 MHz)	23155 (713.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			(Conducted Power [dBm	1]		
	1	0	24.67	24.61	24.52		0
	1	12	24.26	24.53	24.10	0	0
	1	24	24.40	24.55	23.97		0
QPSK	12	0	23.64	23.60	23.49		1
	12	6	23.38	23.59	23.05	0-1	1
	12	13	23.20	23.62	22.84	0-1	1
	25	0	23.42	23.61	23.16		1
	1	0	23.72	23.70	23.59		1
	1	12	23.79	23.88	23.53	0-1	1
	1	24	23.66	23.72	23.42		1
16QAM	12	0	22.72	22.73	22.56		2
	12	6	22.59	22.76	22.39	0-2	2
	12	13	22.49	22.72	22.20	0-2	2
	25	0	22.56	22.68	22.34		2
	1	0	22.73	22.67	22.59		2
	1	12	22.63	22.69	22.45	0-2	2
	1	24	22.53	22.64	22.37		2
64QAM	12	0	21.73	21.73	21.56		3
	12	6	21.61	21.78	21.44	0-3	3
	12	13	21.45	21.67	21.11	J 0-3	3
	25	0	21.57	21.79	21.35	7	3

Table 8-8 LTE Band 12 (707.5MHz) Conducted Powers – 3MHz Bandwidth

				LTE Band 12 3 MHz Bandwidth			
			Low Channel	Mid Channel	High Channel		
Modulation	RB Size	RB Offset	23025 (700.5 MHz)	23095 (707.5 MHz)	23165 (714.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			(Conducted Power [dBm	1]		
	1	0	24.70	24.65	24.17		0
	1	7	24.74	24.71	24.09	0	0
	1	14	24.26	24.56	24.06	1 [0
QPSK	8	0	23.65	23.63	22.98		1
	8	4	23.64	23.60	22.88	0-1	1
	8	7	23.44	23.57	22.94] "-"	1
	15	0	23.63	23.61	22.99	1	1
	1	0	23.84	23.79	23.53		1
	1	7	23.87	23.82	23.46	0-1	1
	1	14	23.69	23.80	23.41	1	1
16QAM	8	0	22.79	22.78	22.25		2
	8	4	22.73	22.79	22.16	0-2	2
	8	7	22.67	22.76	22.12	0-2	2
	15	0	22.71	22.71	22.12		2
	1	0	22.80	22.69	22.30		2
	1	7	22.76	22.80	22.32	0-2	2
	1	14	22.78	22.82	22.36	1	2
64QAM	8	0	21.77	21.77	21.20		3
	8	4	21.74	21.69	21.09	0-3	3
	8	7	21.57	21.79	21.15	0-3	3
	15	0	21.75	21.73	21.17	1	3

FCC ID: A3LSMG960U	PCTEST HA	AC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogo 20 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 29 of 104

Table 8-9
LTE Band 12 (707.5MHz) Conducted Powers – 1.4MHz Bandwidth

			(LTE Band 12			
				1.4 MHz Bandwidth			
			Low Channel	Mid Channel	High Channel		
Modulation	RB Size	Size RB Offset	23017 (699.7 MHz)	23095 (707.5 MHz)	23173 (715.3 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			(Conducted Power [dBn	1]		
	1	0	24.59	24.58	23.66		0
	1	2	24.64	24.67	23.76		0
	1	5	24.56	24.52	23.86] 0	0
QPSK	3	0	24.57	24.57	23.74	T	0
	3	2	24.60	24.65	23.79		0
	3	3	24.56	24.56	23.78	0-1	0
	6	0	23.61	23.52	22.81		1
	1	0	23.87	23.72	23.18		1
	1	2	23.79	23.75	23.15		1
	1	5	23.83	23.76	23.30	0-1	1
16QAM	3	0	23.86	23.72	22.92	0-1	1
	3	2	23.74	23.70	22.99	1	1
	3	3	23.69	23.67	22.94		1
	6	0	22.65	22.56	22.08	0-2	2
	1	0	22.69	22.87	21.97		2
	1	2	22.73	22.72	22.07		2
ļ	1	5	22.76	22.59	22.19	0-2	2
64QAM	3	0	22.70	22.73	22.11	0-2	2
	3	2	22.73	22.76	22.00		2
ľ	3	3	22.79	22.67	22.13	7	2
	6	0	21.71	21.56	21.01	0-3	3

c. LTE Band 13

Table 8-10 LTE Band 13 (780.0MHz) Conducted Powers – 10MHz Bandwidth

Dana	0 (100.	• · · · · · · · · · · · · · · · · · · ·	Jonadolea i	011010 10	WITTE Ballaw
			LTE Band 13 10 MHz Bandwidth		
			Mid Channel		
Modulation	RB Size	RB Offset	23230 (782.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			Conducted Power [dBm]	0011 [05]	
	1	0	24.58		0
	1	25	24.55	0	0
	1	49	24.35		0
QPSK	25	0	23.70		1
	25	12	23.68	0-1	1
	25	25	23.62	0-1	1
	50	0	23.65		1
	1	0	23.73		1
	1	25	23.68	0-1	1
	1	49	23.53		1
16QAM	25	0	22.73		2
	25	12	22.74	0-2	2
	25	25	22.68	0-2	2
	50	0	22.70		2
	1	0	22.83		2
	1	25	22.80	0-2	2
	1	49	22.60		2
64QAM	25	0	21.77		3
	25	12	21.72	0-3	3
	25	25	21.70	0-3	3
	50	0	21.71		3

FCC ID: A3LSMG960U	PCTEST HA	AC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogg 20 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 30 of 104

Table 8-11 LTE Band 13 (780.0MHz) Conducted Powers – 5MHz Bandwidth

			LTE Band 13 5 MHz Bandwidth		
			Mid Channel		
Modulation	RB Size	RB Offset	23230 (782.0 MHz) Conducted Power [dBm]	MPR Allowed per 3GPP [dB]	MPR [dB]
	1	0	24.56		0
	1	12	24.53	0	0
	1	24	24.54		0
QPSK	12	0	23.62		1
	12	6	23.69	0-1	1
	12	13	23.62	0-1	1
	25	0	23.64		1
	1	0	23.71		1
	1	12	23.70	0-1	1
	1	24	23.72		1
16QAM	12	0	22.67		2
	12	6	22.74	0-2	2
	12	13	22.68	0-2	2
	25	0	22.71		2
	1	0	22.58		2
	1	12	22.61	0-2	2
	1	24	22.70		2
64QAM	12	0	21.74		3
	12	6	21.75	0-3	3
	12	13	21.68	0-3	3
	25	0	21.71		3

Note: Since LTE Band 13 at 5MHz bandwidth does not support 3 non-overlapping channels, conducted power measurements were made only on the middle channel.

d. LTE Band 14

Table 8-12 LTE Band 14 (793.0MHz) Conducted Powers – 10MHz Bandwidth

Duna	17 (100.	<u> </u>	Jonadelea i	011010 10	WITTE Bullav
			LTE Band 14 10 MHz Bandwidth		
			Mid Channel		
Modulation	RB Size	RB Offset	23330 (793.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			Conducted Power [dBm]	JOH F [UD]	
	1	0	24.75		0
	1	25	24.61	0	0
	1	49	24.58		0
QPSK	25	0	23.72		1
	25	12	23.65	0-1	1
	25	25	23.56	J-1	1
	50	0	23.64		1
	1	0	23.84		1
	1	25	23.76	0-1	1
	1	49	23.73		1
16QAM	25	0	22.72		2
	25	12	22.73	0-2	2
	25	25	22.67	J-2	2
	50	0	22.70		2
	1	0	22.94		2
	1	25	22.83	0-2	2
	1	49	22.82		2
64QAM	25	0	21.79		3
	25	12	21.67	0-3	3
	25	25	21.65]	3
	50	0	21.74		3

Note: Since LTE Band 14 at 10MHz bandwidth does not support 3 non-overlapping channels, conducted power measurements were made only on the middle channel.

FCC ID: A3LSMG960U	PCTEST HA	AC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogo 21 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 31 of 104

Table 8-13 LTE Band 14 (793.0MHz) Conducted Powers – 5MHz Bandwidth

		•	LTE Band 14 5 MHz Bandwidth		
Modulation	RB Size	RB Offset	Mid Channel 23330 (793.0 MHz) Conducted Power [dBm]	MPR Allowed per 3GPP [dB]	MPR [dB]
	1	0	24.69		0
	1	12	24.61	0	0
	1	24	24.64		0
QPSK	12	0	23.70		1
	12	6	23.66	0-1	1
	12	13	23.60	0-1	1
	25	0	23.63		1
	1	0	23.76		1
	1	12	23.79	0-1	1
	1	24	23.81		1
16QAM	12	0	22.76		2
	12	6	22.71	0-2	2
	12	13	22.68	0-2	2
	25	0	22.70		2
	1	0	22.87		2
	1	12	22.86	0-2	2
	1	24	22.84		2
64QAM	12	0	21.80		3
	12	6	21.79	0-3	3
	12	13	21.76	0-3	3
	25	0	21.73		3

Note: Since LTE Band 14 at 5MHz bandwidth does not support 3 non-overlapping channels, conducted power measurements were made only on the middle channel.

e. LTE Band 26

Table 8-14
LTE Band 26 (836.5MHz) Conducted Powers – 15MHz Bandwidth

			LTE Band 26 (Cell) 15 MHz Bandwidth		
Modulation	RB Size	RB Offset	Mid Channel 26865 (831.5 MHz) Conducted Power [dBm]	MPR Allowed per 3GPP [dB]	MPR [dB]
	1	0	23.91		0
	1	36	24.21	0	0
	1	74	24.37		0
QPSK	36	0	23.10		1
	36	18	23.19	0-1	1
	36	37	23.28	0-1	1
	75	0	23.11		1
	1	0	23.24		1
	1	36	23.56	0-1	1
	1	74	23.69		1
16QAM	36	0	22.22		2
	36	18	22.27	0-2	2
	36	37	22.37	0-2	2
	75	0	22.21		2
	1	0	22.21		2
	1	36	22.47	0-2	2
	1	74	22.59		2
64QAM	36	0	21.27		3
	36	18	21.31	0-3	3
	36	37	21.41	0.0	3
	75	0	21.24		3

Note: Since LTE Band 26 at 15MHz bandwidth does not support 3 non-overlapping channels, conducted power measurements were made only on the middle channel.

FCC ID: A3LSMG960U	PCTEST HA	AC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogg 22 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 32 of 104

Table 8-15
LTE Band 26 (831.5MHz) Conducted Powers – 10MHz Bandwidth

				LTE Band 26 (Cell) 10 MHz Bandwidth			
Modulation	RB Size	RB Offset	Low Channel 26740 (819.0 MHz)	Mid Channel 26865 (831.5 MHz)	High Channel 26990 (844.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
				Conducted Power [dBm	1]		
	1	0	23.57	23.99	24.35		0
	1	25	23.77	24.16	24.49	0	0
	1	49	23.89	24.26	24.13		0
QPSK	25	0	22.72	23.06	23.51		1
	25	12	22.80	23.14	23.56	0-1	1
	25	25	22.81	23.17	23.48	0-1	1
	50	0	22.78	23.13	23.54		1
	1	0	22.91	23.42	23.71		1
	1	25	23.10	23.52	23.83	0-1	1
	1	49	23.27	23.61	23.51		1
16QAM	25	0	21.81	22.12	22.60		2
	25	12	21.89	22.20	22.68	0-2	2
	25	25	21.94	22.26	22.57	0-2	2
	50	0	21.86	22.21	22.63		2
	1	0	21.82	22.31	22.64		2
	1	25	22.03	22.42	22.76	0-2	2
	1	49	22.13	22.54	22.56		2
64QAM	25	0	20.83	21.12	21.61		3
	25	12	20.89	21.22	21.65		3
	25	25	20.93	21.28	21.58	0-3	3
-	50	0	20.88	21.24	21.66		3

Table 8-16 LTE Band 26 (831.5MHz) Conducted Powers – 5MHz Bandwidth

			20 (00 1.011112	LTE Band 26 (Cell)		Banawiath	
				5 MHz Bandwidth			
			Low Channel	Mid Channel	High Channel		
Modulation	RB Size	RB Offset	26715 (816.5 MHz)	26865 (831.5 MHz)	27015 (846.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			(Conducted Power [dBm	1]		
	1	0	23.52	24.10	24.50		0
	1	12	23.60	24.15	24.54	0	0
	1	24	23.68	24.23	24.12		0
QPSK	12	0	22.64	23.14	23.51		1
	12	6	22.72	23.14	23.63	0-1	1
	12	13	22.69	23.18	23.56	0-1	1
	25	0	22.71	23.10	23.48		1
	1	0	22.88	23.46	23.87		1
	1	12	22.96	23.48	23.88	0-1	1
	1	24	22.99	23.57	23.42		1
16QAM	12	0	21.77	22.26	22.66		2
	12	6	21.85	22.25	22.74	0-2	2
	12	13	21.80	22.28	22.68	0-2	2
	25	0	21.81	22.21	22.58	1	2
	1	0	21.80	22.34	22.82		2
ľ	1	12	21.86	22.42	22.82	0-2	2
ļ	1	24	21.93	22.50	22.31	1	2
64QAM	12	0	20.82	21.31	21.69		3
	12	6	20.89	21.28	21.76	1 00	3
	12	13	20.84	21.33	21.72	0-3	3
	25	0	20.80	21.20	21.58	1 – –	3

FCC ID: A3LSMG960U	PCTEST HA	AC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogo 22 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 33 of 104

Table 8-17 LTE Band 26 (831.5MHz) Conducted Powers – 3MHz Bandwidth

				LTE Band 26 (Cell) 3 MHz Bandwidth			
	DD Sine	RB Size RB Offset	Low Channel 26705	Mid Channel 26865	High Channel 27025	MPR Allowed per	MPR [dB]
Modulation	KB Size		(815.5 MHz)	(831.5 MHz)	(847.5 MHz)	3GPP [dB]	мек (ав)
				Conducted Power [dBm			
	1	0	23.54	24.04	24.54	_	0
	1	7	23.70	24.22	24.61	0	0
	1	14	23.58	24.11	24.03		0
QPSK	8	0	22.61	23.10	23.57		1
	8	4	22.65	23.11	23.58	0-1	1
	8	7	22.57	23.18	23.54	0-1	1
	15	0	22.62	23.09	23.57]	1
	1	0	22.85	23.38	23.90		1
	1	7	23.04	23.57	23.93	0-1	1
	1	14	22.92	23.49	23.31		1
16QAM	8	0	21.76	22.24	22.69		2
	8	4	21.76	22.25	22.70	0-2	2
	8	7	21.71	22.28	22.64	0-2	2
	15	0	21.67	22.17	22.62	1	2
	1	0	21.77	22.35	22.82		2
	1	7	21.98	22.52	22.86	0-2	2
	1	14	21.85	22.38	22.31	1	2
64QAM	8	0	20.78	21.26	21.73		3
	8	4	20.79	21.25	21.72	1 ,	3
	8	7	20.76	21.32	21.68	0-3	3
	15	0	20.72	21.19	21.66	1	3

Table 8-18 LTE Band 26 (831.5MHz) Conducted Powers – 1.4MHz Bandwidth

				LTE Band 26 (Cell) 1.4 MHz Bandwidth			
Modulation	Modulation RB Size	RB Offset	26697 (814.7 MHz)	Mid Channel 26865 (831.5 MHz)	High Channel 27033 (848.3 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			(Conducted Power [dBn	1]		
	1	0	23.44	23.97	24.41		0
	1	2	23.50	24.14	24.45		0
	1	5	23.52	24.05	23.87	0	0
QPSK	3	0	23.47	23.99	24.42		0
	3	2	23.50	24.12	24.13		0
	3	3	23.54	24.09	23.93		0
	6	0	22.56	23.02	23.37	0-1	1
	1	0	22.78	23.31	23.72		1
	1	2	22.87	23.48	23.72	1	1
	1	5	22.85	23.41	23.22	0-1	1
16QAM	3	0	22.68	23.23	23.60		1
	3	2	22.74	23.36	23.48		1
	3	3	22.77	23.29	23.20		1
	6	0	21.72	22.18	22.56	0-2	2
	1	0	21.73	22.27	22.67		2
	1	2	21.79	22.38	22.71	1	2
	1	5	21.82	22.34	22.22	0-2	2
64QAM 3	0	21.74	22.23	22.67	0-2	2	
	3	2	21.76	22.37	22.59	1	2
	3	3	21.80	22.32	22.32	1	2
	6	0	20.67	21.12	21.56	0-3	3

FCC ID: A3LSMG960U	PCTEST	SAMSUNG	Approved by: Quality Manager	
Filename:	Test Dates:	DUT Type:		Page 34 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		raye 34 01 104

f. LTE Band 66

Table 8-19
LTE Band 66 (1745.0MHz) Conducted Powers – 20MHz Bandwidth

LTE Band 66 (AWS)									
20 MHz Bandwidth									
			Low Channel	Mid Channel	High Channel				
Modulation	RB Size	RB Offset	132072 (1720.0 MHz)	132322 (1745.0 MHz)	132572 (1770.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]		
			(Conducted Power [dBm	1]				
	1	0	24.00	24.28	24.31		0		
	1	50	23.76	24.00	23.99	0	0		
	1	99	24.04	23.80	23.85		0		
QPSK	50	0	22.54	23.21	23.14		1		
	50	25	22.31	23.13	23.06	0-1	1		
	50	50	22.64	22.85	22.97	0-1	1		
	100	0	22.54	23.08	23.04		1		
	1	0	22.94	23.40	23.30	0-1	1		
	1	50	22.51	23.43	23.23		1		
	1	99	22.95	23.33	23.00		1		
16QAM	50	0	21.65	22.29	22.18		2		
	50	25	21.62	22.21	22.08	0-2	2		
	50	50	21.70	22.06	22.02		2		
	100	0	21.56	22.17	22.12		2		
	1	0	22.30	22.19	22.45		2		
	1	50	21.97	21.92	22.17	0-2	2		
	1	99	21.99	21.90	22.10		2		
64QAM	50	0	20.80	21.37	21.19	0-3	3		
	50	25	20.64	21.20	21.10		3		
	50	50	20.74	21.05	21.03		3		
	100	0	20.61	21.16	21.10		3		

Table 8-20 LTE Band 66 (1745.0MHz) Conducted Powers – 15MHz Bandwidth

LTE Band 66 (AWS)										
	15 MHz Bandwidth Low Channel Mid Channel High Channel									
Modulation	RB Size	RB Offset	132047 (1717.5 MHz)	132322 (1745.0 MHz)	132597 (1772.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]			
			(Conducted Power [dBm	1]					
	1	0	24.10	24.33	24.38		0			
	1	36	23.77	24.25	24.19	0	0			
	1	74	23.98	24.27	24.17		0			
QPSK	36	0	22.94	23.42	23.32		1			
	36	18	22.90	23.37	23.29	0-1	1			
	36	37	22.77	23.35	23.22	0-1	1			
	75	0	22.80	23.34	23.27		1			
	1	0	23.16	23.55	23.51	0-1	1			
	1	36	22.97	23.38	23.33		1			
	1	74	23.16	23.42	23.28		1			
16QAM	36	0	22.04	22.49	22.36		2			
	36	18	21.99	22.48	22.33		2			
	36	37	21.91	22.40	22.27		2			
	75	0	21.90	22.42	22.35		2			
	1	0	22.27	22.59	22.60		2			
	1	36	22.16	22.51	22.40	0-2	2			
	1	74	22.22	22.47	22.40	<u> </u>	2			
64QAM	36	0	21.25	21.53	21.40		3			
	36	18	21.10	21.51	21.36	0-3	3			
	36	37	20.99	21.44	21.35		3			
	75	0	20.95	21.45	21.38]	3			

FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 35 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Fage 33 01 104

Table 8-21
LTE Band 66 (1745.0MHz) Conducted Powers – 10MHz Bandwidth

	LTE Band 66 (1745.0WHZ) CONDUCTED FOWERS - TOWINZ Bandwidth									
	10 MHz Bandwidth									
			Low Channel	Mid Channel	High Channel					
Modulation	RB Size	RB Offset	132022 (1715.0 MHz)	132322 (1745.0 MHz)	132622 (1775.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]			
			(Conducted Power [dBm	n]					
	1	0	24.12	24.37	24.26		0			
	1	25	23.84	24.26	24.03	0	0			
	1	49	23.60	24.25	24.14		0			
QPSK	25	0	22.79	23.38	23.36		1			
	25	12	22.71	23.37	23.25	0-1	1			
	25	25	22.50	23.33	23.20	0-1	1			
	50	0	22.47	23.39	23.16		1			
	1	0	23.39	23.54	23.52	0-1	1			
	1	25	22.98	23.39	23.34		1			
	1	49	22.81	23.32	23.32		1			
16QAM	25	0	21.93	22.45	22.42		2			
	25	12	21.82	22.41	22.41	0-2	2			
	25	25	21.64	22.41	22.34	0-2	2			
	50	0	21.62	22.42	22.35		2			
	1	0	22.39	22.58	22.60		2			
	1	25	22.07	22.52	22.50	0-2	2			
	1	49	21.79	22.50	22.45		2			
64QAM	25	0	20.99	21.47	21.42	0-3	3			
	25	12	20.92	21.45	21.45		3			
	25	25	20.64	21.40	21.40		3			
	50	0	20.66	21.43	21.32		3			

Table 8-22 LTE Band 66 (1745.0MHz) Conducted Powers – 5MHz Bandwidth

	LTE Band 66 (AWS) 5 MHz Bandwidth								
Modulation	RB Size		Low Channel Mid Channel High Channel	High Channel					
		RB Offset	131997 (1712.5 MHz)	132322 (1745.0 MHz)	132647 (1777.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]		
			(Conducted Power [dBm]				
	1	0	24.12	24.20	23.97		0		
	1	12	23.92	24.14	23.86	0	0		
	1	24	23.58	24.04	23.75		0		
QPSK	12	0	23.13	23.22	22.98	0-1	1		
	12	6	23.01	23.21	22.90		1		
	12	13	22.87	23.15	22.89		1		
	25	0	22.88	23.17	22.84		1		
	1	0	23.45	23.46	23.30	0-1	1		
	1	12	23.36	23.43	23.31		1		
	1	24	23.12	23.36	23.23		1		
16QAM	12	0	22.28	22.33	22.15		2		
	12	6	22.16	22.31	22.10		2		
	12	13	22.07	22.30	22.06	0-2	2		
	25	0	22.03	22.28	21.94		2		
	1	0	22.43	22.47	22.28		2		
	1	12	22.34	22.39	22.12	0-2	2		
İ	1	24	22.08	22.31	22.14		2		
64QAM	12	0	21.33	21.34	21.17	0-3	3		
l	12	6	21.27	21.37	21.16		3		
ľ	12	13	21.14	21.26	21.11		3		
	25	0	21.09	21.31	21.04		3		

FCC ID: A3LSMG960U	PCTEST HA	HAC (RF EMISSIONS) TEST REPORT		Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogo 26 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 36 of 104

Table 8-23
LTE Band 66 (1745.0MHz) Conducted Powers – 3MHz Bandwidth

		IE Band (ob (1/45.UIVIHZ) Conducted P	owers – 3MHz	Bandwidth	
				LTE Band 66 (AWS) 3 MHz Bandwidth			
			Low Channel	Mid Channel	High Channel		
Modulation	RB Size	RB Offset	ffset 131987 (1711.5 MHz)	132322 (1745.0 MHz)	132657 (1778.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			(
	1	0	24.16	24.20	23.87		0
	1	7	24.13	24.25	23.93	0	0
	1	14	23.98	24.11	23.81		0
QPSK	8	0	23.19	23.22	22.87		1
	8	4	23.14	23.25	22.89	0-1	1
	8	7	22.99	23.19	22.83		1
	15	0	23.02	23.17	22.85		1
	1	0	23.40	23.53	23.14	0-1	1
	1	7	23.53	23.61	23.39		1
	1	14	23.36	23.44	23.19		1
16QAM	8	0	22.37	22.40	22.02		2
	8	4	22.42	22.38	22.09	0-2	2
	8	7	22.32	22.34	22.07	0-2	2
	15	0	22.28	22.22	21.98		2
	1	0	22.41	22.43	22.21		2
	1	7	22.36	22.49	22.17	0-2	2
	1	14	22.29	22.38	22.20		2
64QAM	8	0	21.31	21.36	21.07	0-3	3
	8	4	21.36	21.34	21.02		3
	8	7	21.33	21.33	21.05		3
	15	0	21.27	21.30	20.99		3

Table 8-24 LTE Band 66 (1745.0MHz) Conducted Powers – 1.4MHz Bandwidth

LTE Band 66 (AWS)										
				1.4 MHz Bandwidth						
			Low Channel	Mid Channel	High Channel					
Modulation	RB Size	RB Offset	131979 (1710.7 MHz)	132322 (1745.0 MHz)	132665 (1779.3 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]			
			(Conducted Power [dBm	1]					
	1	0	24.12	24.23	23.80		0			
	1	2	24.18	24.30	24.03		0			
	1	5	24.05	24.27	23.76	0	0			
QPSK	3	0	24.11	24.22	23.76		0			
	3	2	24.16	24.26	23.80		0			
	3	3	24.09	24.26	23.82		0			
	6	0	23.16	23.28	22.78	0-1	1			
	1	0	23.48	23.51	23.12	0-1	1			
	1	2	23.42	23.62	23.22		1			
	1	5	23.44	23.54	23.02		1			
16QAM	3	0	23.32	23.40	22.99]	1			
	3	2	23.36	23.39	23.13	1	1			
	3	3	23.26	23.40	22.96	1	1			
	6	0	22.28	22.36	21.99	0-2	2			
	1	0	22.41	22.46	22.15		2			
Ī	1	2	22.45	22.60	22.21	1	2			
ľ	1	5	22.33	22.52	22.12	0-2	2			
64QAM	3	0	22.35	22.42	22.07	- 0-2	2			
Ī	3	2	22.38	22.44	22.19		2			
Ī	3	3	22.34	22.43	22.06	7	2			
Ī	6	0	21.23	21.38	20.96	0-3	3			

FCC ID: A3LSMG960U	PCTEST HA	AC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager	
Filename:	Test Dates:	DUT Type:		Dogo 27 of 104	
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 37 of 104	

g. LTE Band 25

Table 8-25 LTE Band 25 (1882.5MHz) Conducted Powers – 20MHz Bandwidth

	LTE Band 25 (1862: SWITZ) CONTROLLED FOWERS - 20WITZ BANGWIGHT										
				20 MHz Bandwidth							
Modulation	RB Size	RB Offset	Low Channel 26140 (1860.0 MHz)	Mid Channel 26365 (1882.5 MHz)	High Channel 26590 (1905.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]				
			Conducted Power [dBm]								
	1	0	24.29	24.12	24.07		0				
	1	50	23.92	23.72	23.86	0	0				
	1	99	24.10	23.89	23.89		0				
QPSK	50	0	23.05	22.94	23.12		1				
	50	25	22.99	22.93	23.05	0-1	1				
	50	50	22.94	22.92	23.02		1				
	100	0	22.98	22.92	23.06] [1				
	1	0	23.35	23.27	23.13	0-1	1				
	1	50	23.23	22.91	22.87		1				
	1	99	23.48	23.12	22.89		1				
16QAM	50	0	22.12	22.06	22.17		2				
	50	25	22.04	22.00	22.12	0-2	2				
	50	50	21.95	21.96	22.08]	2				
	100	0	22.05	22.01	22.12		2				
	1	0	22.22	22.45	22.48		2				
	1	50	22.27	22.05	22.30	0-2	2				
	1	99	22.10	22.21	22.35		2				
64QAM	50	0	21.17	21.08	21.21	0-3	3				
	50	25	21.06	20.98	21.16		3				
	50	50	21.04	20.94	21.16		3				
	100	0	21.09	20.97	21.18	1	3				

Table 8-26 LTE Band 25 (1882.5MHz) Conducted Powers – 15MHz Bandwidth

LTE Datid 25 (1902.5Mill2) Orthodoled 1 Owers - 15Mill2 Datidwidth									
				LTE Band 25 (PCS) 15 MHz Bandwidth					
			Low Channel	Mid Channel	High Channel				
Modulation	RB Size	RB Offset	26115 (1857.5 MHz)	26365 (1882.5 MHz)	26615 (1907.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]		
			C	Conducted Power [dBm	1]				
	1	0	24.09	23.93	24.08		0		
	1	36	23.75	23.85	23.95	0	0		
	1	74	23.73	23.83	24.00		0		
QPSK	36	0	22.92	22.91	22.95		1		
	36	18	22.85	22.89	22.94	0-1	1		
	36	37	22.78	22.86	22.90		1		
	75	0	22.87	22.92	22.93		1		
	1	0	23.22	23.15	23.13	0-1	1		
	1	36	22.83	22.89	22.74		1		
	1	74	22.81	22.90	23.13		1		
16QAM	36	0	21.97	22.04	22.06		2		
	36	18	21.91	22.00	22.02	0-2	2		
	36	37	21.86	21.98	22.00	0-2	2		
	75	0	21.96	22.02	21.98		2		
	1	0	21.91	22.29	22.39		2		
	1	36	21.69	22.11	22.18	0-2	2		
	1	74	22.13	22.13	22.23		2		
64QAM	36	0	21.04	21.03	21.05		3		
	36	18	20.96	21.00	21.02	0-3	3		
	36	37	20.89	20.94	21.04		3		
	75	0	20.94	20.98	21.06		3		

FCC ID: A3LSMG960U	PCTEST HA	AC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 38 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Fage 36 01 104

Table 8-27
LTE Band 25 (1882.5MHz) Conducted Powers – 10MHz Bandwidth

	LTE Band 25 (PCS) 10 MHz Bandwidth										
Modulation	RB Size	RB Offset	Low Channel 26090 (1855.0 MHz)	Mid Channel 26365 (1882.5 MHz) Conducted Power [dBm	High Channel 26640 (1910.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]				
	1	0	24.14	23.97	23.89		0				
ľ	1	25	23.70	23.67	23.79	0	0				
	1	49	23.87	23.86	23.80	1	0				
QPSK	25	0	22.89	22.77	22.89		1				
	25	12	22.87	22.78	22.86	0-1	1				
	25	25	22.82	22.74	22.87		1				
	50	0	22.82	22.79	22.88		1				
	1	0	23.30	22.95	23.33	0-1	1				
	1	25	23.00	22.63	23.44		1				
	1	49	23.20	22.84	23.49		1				
16QAM	25	0	21.97	21.93	21.96		2				
	25	12	21.91	21.90	21.91	0-2	2				
	25	25	21.85	21.87	21.92	0-2	2				
	50	0	21.93	21.87	21.92		2				
	1	0	22.44	22.35	22.30		2				
	1	25	22.07	22.06	22.03	0-2	2				
	1	49	21.88	22.28	22.02		2				
64QAM	25	0	20.96	20.86	20.96	0-3	3				
	25	12	20.96	20.87	20.93		3				
	25	25	20.93	20.80	20.91		3				
	50	0	20.91	20.90	20.92		3				

Table 8-28 LTE Band 25 (1882.5MHz) Conducted Powers – 5MHz Bandwidth

LTE Band 25 (PCS)										
				5 MHz Bandwidth						
			Low Channel	Mid Channel	High Channel					
Modulation	RB Size	RB Offset	26065 (1852.5 MHz)	26365 (1882.5 MHz)	26665 (1912.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]			
			(Conducted Power [dBm	1]					
	1	0	23.86	23.74	23.75		0			
	1	12	23.80	23.72	23.71	0	0			
	1	24	23.80	23.69	23.88		0			
QPSK	12	0	22.83	22.76	22.85		1			
	12	6	22.84	22.76	22.83	0-1	1			
	12	13	22.78	22.74	22.82		1			
	25	0	22.79	22.71	22.82		1			
	1	0	23.09	23.06	22.80	0-1	1			
	1	12	23.01	23.05	22.84		1			
	1	24	23.05	23.32	22.83		1			
16QAM	12	0	21.97	21.88	21.90		2			
	12	6	21.93	21.86	21.93	0-2	2			
	12	13	21.88	21.83	21.94	0-2	2			
	25	0	21.93	21.79	21.84		2			
	1	0	21.95	22.09	22.27		2			
	1	12	21.88	22.06	22.21	0-2	2			
	1	24	21.87	22.11	22.15	1	2			
64QAM	12	0	21.05	20.86	20.97		3			
	12	6	21.03	20.85	20.91	0-3	3			
	12	13	20.98	20.80	20.89		3			
	25	0	20.90	20.80	20.88]	3			

FCC ID: A3LSMG960U	PCTEST HA	AC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager	
Filename:	Test Dates:	DUT Type:		Dogo 20 of 104	
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 39 of 104	

Table 8-29 LTE Band 25 (1882.5MHz) Conducted Powers – 3MHz Bandwidth

				LTE Band 25 (PCS) 3 MHz Bandwidth			
Modulation	RB Size	RB Offset	Low Channel 26055 (1851.5 MHz)	Mid Channel 26365 (1882.5 MHz)	High Channel 26675 (1913.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
				Conducted Power [dBn	1]		
	1	0	23.78	23.72	23.82		0
	1	7	23.81	23.80	23.91	0	0
	1	14	23.74	23.68	23.87		0
QPSK	8	0	22.85	22.70	22.81		1
	8	4	22.86	22.74	22.84	0-1	1
	8	7	22.83	22.72	22.81		1
	15	0	22.85	22.70	22.84		1
	1	0	23.12	22.78	23.16	0-1	1
	1	7	23.21	22.89	23.28		1
	1	14	23.08	22.82	22.86		1
16QAM	8	0	21.87	21.82	21.99		2
	8	4	21.88	21.77	22.03	0-2	2
	8	7	21.87	21.74	22.01	0-2	2
	15	0	21.83	21.86	21.80		2
	1	0	22.21	22.07	21.94		2
	1	7	22.32	22.03	22.22	0-2	2
	1	14	22.19	21.92	22.08	Ī [2
64QAM	8	0	20.93	20.86	20.93		3
•	8	4	20.93	20.89	20.95	0-3	3
ļ	8	7	20.90	20.85	20.93		3
	15	0	20.91	20.84	20.90	1	3

Table 8-30 LTE Band 25 (1882.5MHz) Conducted Powers – 1.4MHz Bandwidth

			LO (1002.0III112			iz Banawiath	
				LTE Band 25 (PCS) 1.4 MHz Bandwidth			
			Low Channel	Mid Channel	High Channel		
Modulation	RB Size	RB Offset	26047 (1850.7 MHz)	26365 (1882.5 MHz)	26683 (1914.3 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			C	Conducted Power [dBm]		
	1	0	23.75	23.80	23.69		0
	1	2	23.81	23.99	23.77		0
	1	5	23.72	23.86	23.70	0	0
QPSK	3	0	23.79	23.89	23.73] "	0
	3	2	23.80	23.92	23.80		0
	3	3	23.75	23.99	23.73		0
	6	0	22.76	22.95	22.75	0-1	1
	1	0	23.16	23.29	22.99	0-1	1
	1	2	23.24	22.91	22.88		1
	1	5	23.12	22.83	22.81		1
16QAM	3	0	22.96	22.87	22.89		1
	3	2	23.01	22.93	22.94		1
	3	3	22.96	23.05	22.89		1
	6	0	21.84	21.89	21.85	0-2	2
	1	0	22.09	22.21	22.13		2
	1	2	21.88	22.31	22.16	1	2
	1	5	21.83	22.24	22.09	0-2	2
64QAM	3	0	21.90	22.17	22.03	- U-Z - 	2
	3	2	21.94	22.20	22.06		2
Ī	3	3	21.89	22.16	22.01		2
	6	0	20.87	20.98	20.84	0-3	3

FCC ID: A3LSMG960U	CONTEST: HA	HAC (RF EMISSIONS) TEST REPORT		Approved by: Quality Manager	
Filename:	Test Dates:	DUT Type:		Dogo 40 of 104	
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 40 of 104	

h. LTE Band 30

Table 8-31
LTE Band 30 (2310.0MHz) Conducted Powers – 10MHz Bandwidth

LTE Band 30									
			10 MHz Bandwidth						
			Mid Channel						
Modulation	RB Size	RB Offset	27710	MPR Allowed per	MPR [dB]				
Wiodulation	KB 312e	RB Oliset	(2310.0 MHz) Conducted Power	3GPP [dB]	WFK [UD]				
			[dBm]						
	1	0	24.50		0				
	1	25	24.30	0	0				
	1	49	24.28		0				
QPSK	25	0	23.53		1				
	25	12	23.50	0-1	1				
	25	25	23.46	0-1	1				
	50	0	23.50		1				
	1	0	23.70		1				
	1	25	23.54	0-1	1				
	1	49	23.49		1				
16QAM	25	0	22.57		2				
	25	12	22.56	0-2	2				
	25	25	22.48	0-2	2				
	50	0	22.55		2				
	1	0	22.69		2				
	1	25	22.59	0-2	2				
	1	49	22.49		2				
64QAM	25	0	21.66		3				
	25	12	21.57	0-3	3				
	25	25	21.50	0-3	3				
	50	0	21.50		3				

Table 8-32 LTE Band 30 (2310.0MHz) Conducted Powers – 5MHz Bandwidth

E Danu .	30 (23 IC		Conducted	Fowers - 3	VITIZ Dalluw
			LTE Band 30 5 MHz Bandwidth		
			Mid Channel		
Modulation	RB Size	RB Offset	27710 (2310.0 MHz) Conducted Power	MPR Allowed per 3GPP [dB]	MPR [dB]
			[dBm] 24.23		_
	1	0			0
	1	12	24.26	0	0
00011	1	24	24.24		0
QPSK	12	0	23.38		1
	12	6	23.48	0-1	1
	12	13	23.37		1
	25	0	23.34		1
	1	0	23.41		1
	1	12	23.42	0-1	1
	1	24	23.40		1
16QAM	12	0	22.48		2
	12	6	22.40	0-2	2
	12	13	22.35	0-2	2
	25	0	22.40		2
	1	0	22.59		2
	1	12	22.56	0-2	2
	1	24	22.54		2
64QAM	12	0	21.49		3
	12	6	21.51		3
	12	13	21.48	0-3	3
	25	0	21.50		3

Note: Since LTE Band 30 at 5MHz bandwidth does not support 3 non-overlapping channels, conducted power measurements were made only on the middle channel.

FCC ID: A3LSMG960U	PCTEST*	SAMSUNG	Approved by: Quality Manager	
Filename:	Test Dates:	DUT Type:		Page 41 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Fage 41 01 104

i. LTE Band 7

Table 8-33 LTE Band 7 (2535.0MHz) Conducted Powers – 20MHz Bandwidth

		I E Ballu	/ (2000.UIVITIZ)	LTE Band 7	JWEIS - ZUIVIII	Z Danuwium	
				20 MHz Bandwidth			
			Low Channel	Mid Channel	High Channel		
Modulation	RB Size	RB Offset	20850 (2510.0 MHz)	21100 (2535.0 MHz)	21350 (2560.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
				Conducted Power [dBm			
	1	0	23.53	23.45	23.58		0
	1	50	23.19	23.31	23.18	0	0
	1	99	23.26	23.30	23.07		0
QPSK	50	0	22.42	22.44	22.48		1
	50	25	22.32	22.36	22.30	0-1	1
	50	50	22.33	22.35	22.19	0-1	1
	100	0	22.42	22.41	22.34		1
	1	0	22.80	22.77	22.85		1
	1	50	22.49	22.62	22.51	0-1	1
	1	99	22.51	22.64	22.35		1
16QAM	50	0	21.47	21.49	21.53		2
	50	25	21.35	21.45	21.40		2
	50	50	21.39	21.42	21.26	0-2	2
	100	0	21.45	21.38	21.39		2
	1	0	21.77	21.72	21.78		2
	1	50	21.45	21.54	21.41	0-2	2
	1	99	21.51	21.52	21.31		2
64QAM	50	0	20.46	20.49	20.42		3
	50	25	20.36	20.45	20.38	0-3	3
	50	50	20.39	20.40	20.29	0-3	3
	100	0	20.47	20.44	20.40		3

Table 8-34
LTE Band 7 (2535.0MHz) Conducted Powers – 15MHz Bandwidth

			. (2000:0::::::::::::)	LTE Band 7			
				15 MHz Bandwidth			
			Low Channel	Mid Channel	High Channel		
Modulation	RB Size	RB Offset	20825 (2507.5 MHz)	21100 (2535.0 MHz)	21375 (2562.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			C	Conducted Power [dBm]		
	1	0	23.60	23.57	23.65		0
	1	36	23.41	23.47	23.41	0	0
	1	74	23.35	23.49	23.26		0
QPSK	36	0	22.48	22.55	22.55		1
	36	18	22.45	22.55	22.45	0-1	1
	36	37	22.39	22.54	22.36	0-1	1
	75	0	22.42	22.53	22.44		1
	1	0	22.66	22.67	22.81		1
	1	36	22.53	22.63	22.55	0-1	1
	1	74	22.49	22.62	22.48		1
16QAM	36	0	21.56	21.65	21.64		2
	36	18	21.53	21.63	21.51	0-2	2
	36	37	21.43	21.60	21.42	0-2	2
	75	0	21.51	21.59	21.54		2
	1	0	21.79	21.75	21.83		2
	1	36	21.63	21.70	21.65	0-2	2
	1	74	21.50	21.72	21.58		2
64QAM	36	0	20.59	20.65	20.62		3
	36	18	20.54	20.65	20.55	0-3	3
	36	37	20.47	20.60	20.46] 0-3	3
	75	0	20.51	20.61	20.55		3

FCC ID: A3LSMG960U	PETEST.	HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 42 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Fage 42 01 104

Table 8-35 LTE Band 7 (2535.0MHz) Conducted Powers – 10MHz Bandwidth

		I E Ballu	/ (2000.UIVITZ)	LTE Band 7	JWEIS - IUIVIN	z Danuwiutii	
				10 MHz Bandwidth			
Modulation	RB Size	RB Offset	Low Channel 20800 (2505.0 MHz)	Mid Channel 21100 (2535.0 MHz)	High Channel 21400 (2565.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
				Conducted Power [dBm	,	- 0011 [0.0]	
	1	0	23.49	23.47	23.47		0
	1	25	23.34	23.47	23.35	0	0
	1	49	23.25	23.45	23.27	1	0
QPSK	25	0	22.40	22.43	22.47		1
	25	12	22.35	22.49	22.44	0-1	1
	25	25	22.32	22.45	22.38	0-1	1
	50	0	22.38	22.47	22.43		1
	1	0	22.61	22.64	22.66		1
	1	25	22.53	22.58	22.47	0-1	1
	1	49	22.39	22.59	22.55		1
16QAM	25	0	21.50	21.58	21.57		2
	25	12	21.47	21.54	21.53	0-2	2
	25	25	21.39	21.55	21.48	0-2	2
	50	0	21.46	21.59	21.48		2
	1	0	21.65	21.71	21.75		2
	1	25	21.55	21.70	21.65	0-2	2
	1	49	21.53	21.62	21.55		2
64QAM	25	0	20.51	20.61	20.58		3
	25	12	20.47	20.52	20.53	0-3	3
	25	25	20.45	20.58	20.47		3
	50	0	20.48	20.57	20.52		3

Table 8-36 LTE Band 7 (2535.0MHz) Conducted Powers – 5MHz Bandwidth

		LIE Dalic	1 / (2535.UNITZ) Conducted P	owers - Swinz	Danuwiuth	
				LTE Band 7 5 MHz Bandwidth			
			Low Channel	Mid Channel	High Channel		
Modulation	RB Size	RB Offset	20775 (2502.5 MHz)	21100 (2535.0 MHz)	21425 (2567.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			(Conducted Power [dBm]			
	1	0	23.46	23.45	23.38		0
	1	12	23.43	23.44	23.33	0	0
	1	24	23.37	23.45	23.33		0
QPSK	12	0	22.49	22.50	22.42		1
	12	6	22.52	22.53	22.44	0-1	1
	12	13	22.46	22.47	22.37	0-1	1
	25	0	22.50	22.50	22.39		1
	1	0	22.63	22.63	22.49		1
	1	12	22.60	22.61	22.48	0-1	1
	1	24	22.59	22.57	22.53		1
16QAM	12	0	21.57	21.56	21.51		2
	12	6	21.56	21.57	21.50	0-2	2
	12	13	21.52	21.54	21.42	0-2	2
	25	0	21.58	21.57	21.45	1	2
	1	0	21.78	21.69	21.60		2
	1	12	21.68	21.68	21.59	0-2	2
	1	24	21.66	21.62	21.55	1	2
64QAM	12	0	20.65	20.62	20.52		3
	12	6	20.69	20.63	20.56	0-3	3
	12	13	20.59	20.61	20.49]	3
	25	0	20.61	20.56	20.47	1	3

FCC ID: A3LSMG960U	PCTEST HA	AC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 43 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 43 01 104

j. LTE Band 41 - Power Class 3

Table 8-37 LTE Band 41 (2593.0MHz) Conducted Powers – 20MHz Bandwidth

				,	LTE Band 41 0 MHz Bandwidth	OWEIS - 20			
			Low Channel	Low-Mid Channel	Mid Channel	Mid-High Channel	High Channel		
Modulation	RB Size	RB Offset	39750 (2506.0 MHz)	40185 (2549.5 MHz)	40620 (2593.0 MHz)	41055 (2636.5 MHz)	41490 (2680.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
				Co	nducted Power [de	Bm]			
	1	0	23.75	24.01	23.87	23.62	23.91		0
	1	50	23.63	23.84	23.53	23.53	23.78	0	0
	1	99	23.64	23.77	23.42	23.52	23.74		0
QPSK	50	0	22.73	23.04	22.81	22.55	22.85		1
	50	25	22.73	22.97	22.69	22.58	22.81	0-1	1
	50	50	22.68	22.93	22.53	22.54	22.75		1
	100	0	22.72	22.98	22.68	22.51	22.79		1
	1	0	23.04	23.28	23.24	22.82	23.20		1
	1	50	22.83	23.19	22.85	22.75	23.04	0-1	1
	1	99	22.92	23.16	22.74	22.76	23.02		1
16QAM	50	0	21.83	22.12	21.96	21.61	21.94		2
	50	25	21.79	22.05	21.80	21.69	21.90	0-2	2
	50	50	21.75	22.00	21.66	21.62	21.84	0-2	2
	100	0	21.81	22.06	21.83	21.58	21.88		2
	1	0	21.61	21.95	21.83	21.45	21.84		2
	1	50	21.49	21.83	21.51	21.39	21.68	0-2	2
	1	99	21.56	21.76	21.38	21.38	21.66		2
64QAM	50	0	20.80	21.19	20.95	20.69	21.01		3
	50	25	20.78	21.13	20.80	20.71	20.97	0-3	3
	50	50	20.60	21.07	20.68	20.66	20.92		3
	100	0	20.79	21.14	20.81	20.63	20.95		3

Table 8-38
LTE Band 41 (2593.0MHz) Conducted Powers – 15MHz Bandwidth

			,	1!	LTE Band 41 5 MHz Bandwidth				
			Low Channel	Low-Mid Channel	Mid Channel	Mid-High Channel	High Channel		
Modulation	RB Size	RB Offset	39750 (2506.0 MHz)	40185 (2549.5 MHz)	40620 (2593.0 MHz)	41055 (2636.5 MHz)	41490 (2680.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
				Co	nducted Power [de	Bm]			
	1	0	23.75	24.08	23.92	23.80	24.05		0
	1	36	23.64	23.86	23.61	23.60	23.85	0	0
	1	74	23.63	23.75	23.51	23.52	23.79		0
QPSK	36	0	22.70	22.99	22.88	22.73	22.98		1
	36	18	22.69	22.89	22.75	22.66	22.95	0-1	1
	36	37	22.69	22.83	22.65	22.59	22.87	0-1	1
	75	0	22.67	22.88	22.75	22.66	22.92		1
	1	0	22.98	23.38	23.22	23.05	23.32		1
	1	36	22.88	23.06	22.91	22.83	23.08	0-1	1
	1	74	22.91	22.95	22.80	22.74	22.97		1
16QAM	36	0	21.77	22.05	21.92	21.79	22.06		2
	36	18	21.78	21.96	21.87	21.76	22.00	0-2	2
	36	37	21.72	21.88	21.67	21.67	21.91	0-2	2
	75	0	21.77	21.97	21.85	21.75	22.01		2
	1	0	21.49	21.86	21.70	21.56	21.81		2
	1	36	21.40	21.59	21.41	21.36	21.62	0-2	2
	1	74	21.40	21.53	21.30	21.28	21.50		2
64QAM	36	0	20.76	21.02	20.98	20.84	21.06		3
	36	18	20.77	21.01	20.81	20.77	21.02	0-3	3
	36	37	20.73	20.90	20.74	20.68	20.96] ""	3
	75	0	20.77	21.01	20.86	20.79	21.01		3

FCC ID: A3LSMG960U	PCTEST	HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 44 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		raye 44 01 104

Table 8-39 LTE Band 41 (2593.0MHz) Conducted Powers – 10MHz Bandwidth

				10	LTE Band 41 0 MHz Bandwidth				
			Low Channel	Low-Mid Channel	Mid Channel	Mid-High Channel	High Channel		
Modulation	RB Size	RB Offset	39750 (2506.0 MHz)	40185 (2549.5 MHz)	40620 (2593.0 MHz)	41055 (2636.5 MHz)	41490 (2680.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
				Co	nducted Power [di	Bm]			
	1	0	23.67	23.95	23.82	23.69	23.93		0
	1	25	23.66	23.85	23.66	23.57	23.85	0	0
	1	49	23.61	23.79	23.61	23.52	23.79		0
QPSK	25	0	22.67	22.86	22.81	22.64	22.91		1
	25	12	22.71	22.86	22.78	22.64	22.87	0-1	1
	25	25	22.64	22.77	22.66	22.56	22.82	0-1	1
	50	0	22.66	22.87	22.74	22.65	22.89		1
	1	0	22.95	23.25	23.10	22.97	23.26		1
	1	25	22.87	23.13	22.91	22.81	23.05	0-1	1
	1	49	22.93	22.95	22.86	22.75	23.06	Ī	1
16QAM	25	0	21.73	21.91	21.84	21.72	21.95		2
	25	12	21.69	21.88	21.78	21.72	21.95	0-2	2
	25	25	21.67	21.82	21.72	21.63	21.92	0-2	2
	50	0	21.76	21.94	21.83	21.74	21.99	Ī	2
	1	0	21.44	21.76	21.63	21.50	21.73		2
	1	25	21.43	21.63	21.45	21.37	21.59	0-2	2
	1	49	21.38	21.48	21.40	21.29	21.51		2
64QAM	25	0	20.80	21.01	20.96	20.83	21.08	<u> </u>	3
	25	12	20.80	21.01	20.86	20.81	21.02	0-3	3
	25	25	20.74	20.94	20.82	20.76	21.00	1	3
	50	0	20.77	20.96	20.89	20.77	20.99		3

Table 8-40 LTE Band 41 (2593.0MHz) Conducted Powers – 5MHz Bandwidth

		LILD	anu 41 (23	33.UNIHZ) C	LTE Band 41	- Owers - 31	ni iz Danuv	viutii	
				5	MHz Bandwidth				
			Low Channel	Low-Mid Channel	Mid Channel	Mid-High Channel	High Channel		
Modulation	RB Size	RB Offset	39750 (2506.0 MHz)	40185 (2549.5 MHz)	40620 (2593.0 MHz)	41055 (2636.5 MHz)	41490 (2680.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
				Co	nducted Power [de	Bm]			
	1	0	23.62	23.84	23.71	23.62	23.83		0
	1	12	23.64	23.79	23.65	23.59	23.82	0	0
	1	24	23.58	23.75	23.54	23.50	23.74	Ī	0
QPSK	12	0	22.62	22.91	22.79	22.61	22.86		1
	12	6	22.66	22.87	22.79	22.66	22.87	0-1	1
	12	13	22.62	22.84	22.71	22.59	22.84	0-1	1
	25	0	22.63	22.85	22.76	22.58	22.86		1
	1	0	22.88	23.20	22.99	22.85	23.06		1
	1	12	22.87	23.13	22.96	22.80	23.04	0-1	1
	1	24	22.84	22.98	22.81	22.72	22.95	Ī	1
16QAM	12	0	21.70	21.90	21.85	21.69	21.95		2
	12	6	21.73	21.93	21.86	21.67	21.94	0-2	2
	12	13	21.70	21.90	21.72	21.63	21.87	0-2	2
	25	0	21.69	21.86	21.79	21.64	21.88	Ī	2
	1	0	21.40	21.67	21.47	21.37	21.57		2
	1	12	21.38	21.62	21.43	21.33	21.56	0-2	2
	1	24	21.37	21.53	21.36	21.26	21.53		2
64QAM	12	0	20.79	20.99	20.96	20.80	20.97		3
	12	6	20.79	21.04	20.87	20.75	21.01	0-3	3
1	12	13	20.78	20.93	20.82	20.69	20.99	1 L	3
	25	0	20.80	21.00	20.92	20.75	20.97		3

FCC ID: A3LSMG960U	PCTEST	HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 45 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		raye 45 01 104

k. LTE Band 41 - Power Class 2

Table 8-41 LTE Band 41 (2593.0MHz) Conducted Powers – 20MHz Bandwidth

				2	LTE Band 41 0 MHzBandwidth				
			Low Channel	Low-Mid Channel	Mid Channel	Mid-High Channel	High Channel		
Modulation	RB Size	RB Offset	39750 (2506.0 MHz)	40185 (2549.5 MHz)	40620 (2593.0 MHz)	41055 (2636.5 MHz)	41490 (2680.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
				Co	nducted Power [de	Bm]			
	1	0	26.79	26.96	26.95	26.66	26.93		0
	1	50	26.68	26.94	26.67	26.58	26.81	0	0
	1	99	26.70	26.86	26.55	26.56	26.74	Ī	0
QPSK	50	0	25.77	26.11	25.89	25.61	25.93		1
	50	25	25.74	26.05	25.76	25.68	25.91	0-1	1
	50	50	25.71	25.96	25.63	25.63	25.84	0-1	1
	100	0	25.79	26.07	25.79	25.56	25.91		1
	1	0	26.30	26.50	26.49	26.16	26.47		1
	1	50	26.15	26.44	26.15	26.06	26.32	0-1	1
	1	99	26.19	26.37	26.06	26.03	26.25		1
16QAM	50	0	24.87	25.16	24.98	24.70	24.99		2
	50	25	24.86	25.10	24.83	24.78	24.95	0-2	2
	50	50	24.80	25.03	24.70	24.69	24.91	0-2	2
	100	0	24.85	25.10	24.85	24.67	24.97	Ī	2
	1	0	24.96	25.19	25.18	24.84	25.09		2
	1	50	24.84	25.12	24.82	24.76	24.97	0-2	2
	1	99	24.84	25.07	24.75	24.71	24.93	Ī	2
64QAM	50	0	23.85	24.18	23.99	23.72	24.01		3
	50	25	23.86	24.13	23.86	23.77	24.00	0-3	3
	50	50	23.81	24.06	23.73	23.73	23.92] -5	3
	100	0	23.83	24.12	23.86	23.65	23.95	Ī	3

Table 8-42
LTE Band 41 (2593.0MHz) Conducted Powers – 15MHz Bandwidth

			,	1	LTE Band 41 5 MHz Bandwidth				
			Low Channel	Low-Mid Channel	Mid Channel	Mid-High Channel	High Channel		
Modulation	RB Size	RB Offset	39750 (2506.0 MHz)	40185 (2549.5 MHz)	40620 (2593.0 MHz)	41055 (2636.5 MHz)	41490 (2680.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
				Co	nducted Power [de	Bm]			
	1	0	26.57	27.06	26.97	26.66	26.85		0
	1	36	26.53	26.88	26.72	26.49	26.70	0	0
	1	74	26.55	26.79	26.58	26.36	26.68		0
QPSK	36	0	25.53	26.05	25.86	25.60	25.87		1
	36	18	25.53	26.03	25.71	25.52	25.83	0-1	1
	36	37	25.50	25.90	25.60	25.44	25.77	0-1	1
	75	0	25.54	25.94	25.72	25.50	25.80		1
	1	0	26.10	26.50	26.50	26.16	26.39		1
	1	36	25.96	26.40	26.15	25.96	26.27	0-1	1
	1	74	26.00	26.32	26.04	25.86	26.17		1
16QAM	36	0	24.60	25.09	24.94	24.69	24.90		2
	36	18	24.64	25.02	24.87	24.63	24.87	0-2	2
	36	37	24.59	24.99	24.71	24.55	24.84	0-2	2
	75	0	24.61	25.01	24.82	24.62	24.88		2
	1	0	24.65	25.18	25.10	24.76	25.02		2
	1	36	24.59	25.01	24.77	24.57	24.88	0-2	2
	1	74	24.62	24.93	24.68	24.50	24.78		2
64QAM	36	0	23.64	24.07	24.00	23.68	23.94		3
	36	18	23.64	24.10	23.86	23.64	23.94	0-3	3
	36	37	23.62	23.99	23.70	23.57	23.83		3
	75	0	23.64	24.06	23.85	23.63	23.93		3

FCC ID: A3LSMG960U	PCTEST	HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 46 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Fage 40 01 104

Table 8-43 LTE Band 41 (2593.0MHz) Conducted Powers – 10MHz Bandwidth

		LIL Du	114 +1 (200	<u>, </u>	LTE Band 41	owers – 10	MITIZ Dana	Width	
			Low Channel	Low-Mid Channel	MHz Bandwidth Mid Channel	Mid-High Channel	High Channel		
Modulation	RB Size	RB Offset	39750 (2506.0 MHz)	40185 (2549.5 MHz)	40620 (2593.0 MHz)	41055 (2636.5 MHz)	41490 (2680.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
				Co	nducted Power [de	Bm]			
	1	0	26.53	27.00	26.85	26.52	26.86		0
	1	25	26.51	26.89	26.66	26.44	26.74	0	0
	1	49	26.50	26.76	26.56	26.36	26.71	Ī	0
QPSK	25	0	25.54	26.01	25.82	25.55	25.87		1
	25	12	25.56	25.98	25.76	25.52	25.81	0-1	1
	25	25	25.47	25.90	25.61	25.48	25.78	J 0-1	1
	50	0	25.54	25.96	25.76	25.52	25.82		1
	1	0	26.03	26.50	26.40	26.08	26.38		1
	1	25	26.01	26.41	26.19	25.97	26.28	0-1	1
	1	49	26.00	26.32	26.14	25.88	26.26	Ī	1
16QAM	25	0	24.59	25.03	24.88	24.61	24.88		2
	25	12	24.57	24.99	24.82	24.59	24.83	0-2	2
	25	25	24.54	24.95	24.73	24.53	24.80	0-2	2
	50	0	24.63	25.07	24.85	24.64	24.94	Ī	2
	1	0	24.64	25.11	25.00	24.68	24.99		2
	1	25	24.60	25.03	24.81	24.59	24.88	0-2	2
	1	49	24.60	24.88	24.76	24.50	24.86		2
64QAM	25	0	23.68	24.14	24.03	23.76	24.05	1	3
	25	12	23.70	24.16	23.95	23.73	23.97	0-3	3
	25	25	23.68	24.08	23.82	23.67	23.92	ļ	3
	50	0	23.64	24.08	23.85	23.63	23.94		3

Table 8-44 LTE Band 41 (2593.0MHz) Conducted Powers – 5MHz Bandwidth

		LIL D	and +1 (250	73.0WII 12) O	LTE Band 41	owers – si	IIIZ Dallav	vidtii	
				5	MHz Bandwidth				
			Low Channel	Low-Mid Channel	Mid Channel	Mid-High Channel	High Channel		
Modulation	RB Size	RB Offset	39750 (2506.0 MHz)	40185 (2549.5 MHz)	40620 (2593.0 MHz)	41055 (2636.5 MHz)	41490 (2680.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
				Co	nducted Power [de	Bm]			
	1	0	26.43	26.89	26.72	26.55	26.73		0
	1	12	26.44	26.79	26.66	26.52	26.74	0	0
	1	24	26.41	26.81	26.55	26.44	26.70		0
QPSK	12	0	25.49	25.92	25.72	25.53	25.75		1
	12	6	25.51	25.95	25.75	25.51	25.79	0-1	1
	12	13	25.46	25.87	25.62	25.43	25.77	U-1	1
	25	0	25.48	25.90	25.71	25.50	25.76		1
	1	0	25.98	26.43	26.28	26.00	26.27		1
	1	12	25.97	26.40	26.21	25.99	26.30	0-1	1
	1	24	25.94	26.35	26.08	25.89	26.22		1
16QAM	12	0	24.58	25.05	24.84	24.63	24.92		2
	12	6	24.60	25.01	24.81	24.62	24.90	0-2	2
	12	13	24.55	24.97	24.76	24.53	24.89	0-2	2
	25	0	24.54	24.92	24.75	24.54	24.84		2
	1	0	24.57	25.01	24.89	24.61	24.89		2
	1	12	24.58	25.05	24.79	24.59	24.90	0-2	2
	1	24	24.56	24.96	24.70	24.53	24.84		2
64QAM	12	0	23.74	24.13	23.97	23.69	23.95		3
	12	6	23.66	24.09	23.93	23.67	23.98	0-3	3
	12	13	23.66	24.04	23.86	23.66	23.97] ""	3
	25	0	23.65	24.06	23.89	23.66	23.95		3

FCC ID: A3LSMG960U	PCTEST	HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 47 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		raye 47 01 104

VIII. WIFI Conducted Powers (SISO/MIMO)

Table 8-45

IEEE 802.11b/g/n (2.4GHz, SISO) Reduced Average RF Power¹

	2.4GHz Conducted Power [dBm]								
١.	reg [MHz]	Channel	IEEE Transmission Mode						
ľ	red [miriz]	Chainei	802.11b	802.11g	802.11n				
	2412	1	15.07	15.35	15.31				
	2437 6 14.80 15.15 15.05								
	2462	11	15.27	15.35	15.21				

Table 8-46
IEEE 802.11g/n (2.4GHz, MIMO) Reduced Average RF Power¹

2.	2.4GHz Conducted Power [dBm]								
Freq	Channel	IEEE Transmission Mode							
[MHz]	Cilailiei	802.11g	802.11n						
2412	1	18.02	17.88						
2437	6	18.03	17.97						
2462	11	18.37	18.18						

Table 8-47 IEEE 802.11a/n/ac (5GHz, 20MHz BW, SISO) Reduced Average RF Power¹

	5GHz (20MHz) Conducted	Power [dBm]	
Freg [MHz]	Channel	IEEE .	Transmission	Mode
rreq [winz]	Chamilei	802.11a	802.11n	802.11ac
5180	36	12.57	12.61	12.70
5200	40	12.71	12.68	12.68
5220	44	12.69	12.64	12.64
5240	48	12.67	12.75	12.67
5260	52	12.51	12.48	12.44
5280	56	12.60	12.43	12.49
5300	60	12.63	12.58	12.44
5320	64	12.70	12.56	12.53
5500	100	12.68	12.76	12.65
5600	120	12.77	12.74	12.66
5620	124	12.79	12.67	12.76
5720	144	12.58	12.55	12.60
5745	149	12.57	12.57	12.57
5785	157	12.45	12.53	12.48
5825	165	12.40	12.33	12.43

Table 8-48
IEEE 802.11a/n/ac (5GHz, 20MHz BW, MIMO) Reduced Average RF Power¹

5GHz (20MHz) Conducted Power [dBm]						
Freg [MHz]	Channel	IEEE Transmission Mode				
rred [MHZ]	Chainer	802.11a	802.11n	802.11ac		
5180	36	15.57	15.55	15.67		
5200	40	15.58	15.63	15.66		
5220	44	15.48	15.64	15.76		
5240	48	15.57	15.74	15.78		
5260	52	15.48	15.45	15.73		
5280	56	15.63	15.56	15.67		
5300	60	15.52	15.60	15.55		
5320	64	15.58	15.64	15.59		
5500	100	15.79	15.69	15.70		
5600	120	15.80	15.85	15.62		
5620	124	15.78	15.81	15.78		
5720	144	15.53	15.58	15.63		
5745	149	15.60	15.56	15.60		
5785	157	15.82	15.67	15.46		
5825	165	15.74	15.44	15.48		

¹ Note: This device utilizes independent power reduction mechanisms for the WIFI transmitter in all WIFI modes for held-to-ear scenarios.

FCC ID: A3LSMG960U	PCTEST*	HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 48 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Fage 46 01 104

Table 8-49
IEEE 802.11n/ac (5GHz, 40MHz BW, SISO) Reduced Average RF Power¹

112, 40MI 12 DVV, Oloo, Reduced							
5GHz (40MHz) Conducted Power [dBm]							
Channel	IEEE Transmission Mode						
Channel	802.11n 802.11ac						
38	12.51	12.63					
46	12.67	12.62					
54	12.47	12.52					
62	12.60	12.26					
102	12.72	12.63					
118	12.87	12.78					
126	12.90	12.79					
142	12.67	12.56					
151	12.62	12.63					
159	12.56	12.55					
	40MHz) Cond Channel 38 46 54 62 102 118 126 142	40MHz) Conducted Power Channel IEEE Transn 802.11n 38 38 12.51 46 12.67 54 12.47 62 12.60 102 12.72 118 12.87 126 12.90 142 12.67 151 12.62					

Table 8-50 IEEE 802.11n/ac (5GHz, 40MHz BW, MIMO) Reduced Average RF Power¹

5GHz (40MHz) Conducted Power [dBm]						
Freg [MHz]	Channel	IEEE Transmission Mode				
ried [wiriz]	Chamilei	802.11n	802.11ac			
5190	38	15.39	15.39			
5230	46	15.70	15.49			
5270	54	15.52	15.45			
5310	62	15.67	15.46			
5510	102	15.57	15.66			
5590	118	15.77	15.69			
5630	126	15.71	15.67			
5710	142	15.56	15.59			
5755	151	15.51	15.48			
5795	159	15.30	15.30			

Table 8-51 IEEE 802.11ac (5GHz, 8<u>0MHz BW, SISO) Redu</u>ced Average RF Power¹

5GHz (80MHz) Conducted Power [dBm]					
Freq [MHz]	Channel	IEEE Transmission Mode			
		802.11ac			
5210	42	12.79			
5290	58	13.21			
5530	106	12.80			
5610	122	12.75			
5690	138	13.38			
5775	155	13.07			

Table 8-52 IEEE 802.11ac (5GHz, 80MHz BW, MIMO) Reduced Average RF Power¹

5GHz (80MHz) Conducted Power [dBm]					
Freq [MHz]	req [MHz] Channel				
		802.11ac			
5210	42	15.89			
5290	58	16.02			
5530	106	15.78			
5610	122	15.70			
5690	138	16.39			
5775	155	15.97			

¹ Note: This device utilizes independent power reduction mechanisms for the WIFI transmitter in all WIFI modes for held-to-ear scenarios.

FCC ID: A3LSMG960U	PCTEST	HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 49 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		raye 49 01 104

IX. WIFI Conducted Powers for Operations with Simultaneous 2.4GHz and 5GHz

Table 8-53
IEEE 802.11b/g/n (2.4GHz, Ant1) Reduced Average RF Power¹

•	bigin (2:40112; Anti) Reddeed Average					
	2.4GHz Conducted Power [dBm]					
	Freq [MHz] Channel IEEE Transmission Mode					
	ried [winz]	Chainer	802.11b	802.11g	802.11n	
	2412	1	13.46	12.72	12.85	
	2437	6	12.79	13.21	13.36	
	2462	11	13.23	13.48	12.77	

Table 8-54
IEEE 802.11b/g/n (2.4GHz, Ant2) Reduced Average RF Power¹

2.4GHz Conducted Power [dBm]					
Freq [MHz]	Freg [MHz] Channel IEEE Transmission Mode				
ried [MHZ]	Chainei	802.11b	802.11g	802.11n	
2412	1	13.02	13.23	12.97	
2437	6	13.45	13.09	13.00	
2462	11	13.35	12.79	12.70	

Table 8-55
IEEE 802.11a/n/ac (5GHz, 20MHz BW, Ant1) Reduced Average RF Power¹

, (3GHz, 20181Hz BVV, Aliti) Reduced Av						
5GHz (20MHz) Conducted Power [dBm]						
Freg [MHz]	Channel	IEEE .	Transmission			
	Onume:	802.11a	802.11n	802.11ac		
5180	36	12.57	12.61	12.70		
5200	40	12.71	12.68	12.68		
5220	44	12.69	12.64	12.64		
5240	48	12.67	12.75	12.67		
5260	52	12.51	12.48	12.44		
5280	56	12.60	12.43	12.49		
5300	60	12.63	12.58	12.44		
5320	64	12.70	12.56	12.53		
5500	100	12.68	12.76	12.65		
5600	120	12.77	12.74	12.66		
5620	124	12.79	12.67	12.76		
5720	144	12.58	12.55	12.60		
5745	149	12.57	12.57	12.57		
5785	157	12.45	12.53	12.48		
5825	165	12.40	12.33	12.43		

Table 8-56
IEEE 802.11a/n/ac (5GHz, 20MHz BW, Ant2) Reduced Average RF Power¹

5GHz (20MHz) Conducted Power [dBm]						
Freg [MHz]	Channel	IEEE Transmission Mode				
ried [wiriz]	Chainei	802.11a	802.11n			
5180	36	12.54	12.47	12.61		
5200	40	12.43	12.56	12.62		
5220	44	12.24	12.61	12.85		
5240	48	12.44	12.70	12.86		
5260	52	12.43	12.40	12.99		
5280	56	12.63	12.67	12.82		
5300	60	12.38	12.59	12.63		
5320	64	12.44	12.70	12.62		
5500	100	12.88	12.59	12.72		
5600	120	12.81	12.94	12.56		
5620	124	12.74	12.92	12.77		
5720	144	12.46	12.58	12.63		
5745	149	12.60	12.52	12.61		
5785	157	13.15	12.79	12.42		
5825	165	13.03	12.53	12.51		

¹ Note: This device utilizes independent power reduction mechanisms for the WIFI transmitter in all WIFI modes for held-to-ear scenarios.

FCC ID: A3LSMG960U	PCTEST HA	PCTEST HAC (RF EMISSIONS) TEST REPORT		Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogo 50 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 50 of 104

Table 8-57
IEEE 802.11n/ac (5GHz, 40MHz BW, Ant1) Reduced Average RF Power¹

5GHz (5GHz (40MHz) Conducted Power [dBm]										
Freg [MHz]	Channel	IEEE Transmission Mode									
ried [wiriz]	Chainlei	802.11n	802.11ac								
5190	38	12.51	12.63								
5230	46	12.67	12.62								
5270	54	12.47	12.52								
5310	62	12.60	12.26								
5510	102	12.72	12.63								
5590	118	12.87	12.78								
5630	126	12.90	12.79								
5710	142	12.67	12.56								
5755	151	12.62	12.63								
5795	159	12.56	12.55								

Table 8-58
IEEE 802.11n/ac (5GHz, 40MHz BW, Ant2) Reduced Average RF Power¹

		/ \\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \						
5GHz (40MHz) Cond	lucted Power	[dBm]					
Freq [MHz]	Channel	IEEE Transmission Mode						
Freq [WHZ]	Chainlei	802.11n	802.11ac					
5190	38	12.25	12.12					
5230	46	12.71	12.34					
5270	54	12.54	12.36					
5310	62	12.72	12.64					
5510	102	12.40	12.67					
5590	118	12.64	12.57					
5630	126	12.48	12.53					
5710	142	12.42	12.59					
5755	151	12.37	12.31					
5795	159	12.00	12.02					

Table 8-59
IEEE 802.11ac (5GHz, 80MHz BW, Ant1) Reduced Average RF Power¹

	' ' ' ' , '	, ixcau
5GHz (80MH	z) Conducted F	Power [dBm]
Freq [MHz]	Channel	IEEE Transmission M ode
		802.11ac
5210	42	12.79
5290	58	13.21
5530	106	12.80
5610	122	12.75
5690	138	13.38
5775	155	13.07
	5GHz (80MH Freq [MHz] 5210 5290 5530 5610 5690	Freq [MHz] Channel 5210 42 5290 58 5530 106 5610 122 5690 138

Table 8-60 IEEE 802.11ac (5GHz, 80MHz BW, Ant2) Reduced Average RF Power¹

5GHz (80MH	z) Conducted F	ower [dBm]
Freq [MHz]	Channel	IEEE Transmission M ode
		802.11ac
5210	42	12.97
5290	58	12.81
5530	106	12.73
5610	122	12.63
5690	138	13.37
5775	155	12.85

¹ Note: This device utilizes independent power reduction mechanisms for the WIFI transmitter in all WIFI modes for held-to-ear scenarios.

FCC ID: A3LSMG960U	PCTEST	HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager	
Filename:	Test Dates:	DUT Type:		Page 51 of 104	
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Fage 31 01 104	

9. JUSTIFICATION OF HELD TO EAR MODES TESTED

I. Analysis of RF Air Interface Technologies

An analysis was performed, following the guidance of §4.3 and §4.4 of the ANSI standard, of the RF air interface technologies being evaluated. The factors that will affect the RF interference potential were evaluated, and the worst case operating modes were identified and used in the evaluation. A WD's interference potential is a function both of the WD's average near-field field strength and of the signal's audio-frequency amplitude modulation characteristics. Per §4.4, RF air interface technologies that have low power have been found to produce sufficiently low RF interference potential, so it is possible to exempt them from the product testing specified in Clause 5 of the ANSI standard. An RF air interface technology of a device is exempt from testing when its average antenna input power plus its MIF is ≤17dBm for all of its operating modes. RF air interface technologies exempted from testing in this manner are automatically assigned an M4 rating to be used in determining the overall rating for the WD.

The worst case MIF plus the worst case average antenna input power for all modes are investigated below to determine the testing requirements for this device.

II. Individual Mode Evaluations

Table 9-1
Max Power + MIF calculations for Low Power Exemptions

Air Interface	Maximum Average Power (dBm)	Worst Case MIF (dB)	Total (Power + MIF, dB)	C63.19 Testing Required
CDMA - RC1/SO55 Full Frame Rate	24.88	-19.48	5.40	No
CDMA - RC1/SO3 1/8 th Frame Rate	15.80*	3.07	18.87	Yes
CDMA - EVDO RevA	24.87	-19.33	5.54	No
GSM850	23.97*	3.55	27.52	Yes
GSM1900	20.61*	3.56	24.17	Yes
EDGE 850	17.97*	3.78	21.75	Yes***
EDGE 1900	16.46*	3.56	20.02	Yes***
UMTS - RMC	24.69	-21.12	3.57	No
UMTS - AMR	24.72	-12.77	11.95	No
UMTS - HSUPA	23.98	-22.21	1.77	No
LTE - FDD	24.81	-9.53	15.28	No
LTE - TDD (PC3)	17.39*	1.62	19.01	Yes
LTE - TDD (PC2)	20.37*	1.67	22.04	Yes
2.4GHz WIFI	18.37	-4.74	13.63	No
5GHz WIFI	16.39	-10.82	5.57	No
Simultaneous 2.4GHz and 5GHz WLAN Operations	19.45**	-5.45	14.00	No

^{*} Note: ANSI C63.19-2011 Sec. 4.4 Footnote 20 indicates the use of a long averaging time for measuring the antenna input power when using this method of exclusion. Therefore, the frame averaged power was calculated for these modes in this investigation.

FCC ID: A3LSMG960U	PCTEST	HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 52 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		raye 32 01 104

© 2017 PCTEST Engineering Laboratory, Inc.

REV 3.1.M

- ** Note: This value is calculated as the linear sum of the worst-case power for each band and antenna combination while in simultaneous 2.4GHz and 5GHz operation. This calculation is conservative and for use in this investigation only.
- *** Note: GSM data modes were not evaluated as GSM voice modes were found to the worst-case modes for the GSM air interface.

III. Low-Power Exemption Conclusions

Per ANSI C63.19-2011, RF Emissions testing for this device is only required for GSM and 1/8th Frame Rate CDMA voices modes as well as LTE TDD (Power Class 3 and Power Class 2) data modes.

FCC ID: A3LSMG960U	PCTEST HA	AC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogo F2 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 53 of 104

10. LTE TDD UPLINK-DOWNLINK CONFIGURATION

I. Uplink-Downlink Configuration Additional Testing

An investigation was performed on each supported power class for LTE TDD to determine the worst-case Uplink-Downlink configuration for RFE testing.

Per 3GPP TS 36.211, the total frame length for each TDD radio frame of length T_f = 307200 · T_s = 10 ms, where T_s is a number of time units equal to 1/(15000 x 2048) seconds. Additionally, each radio frame consists of 10 subframes, each of length $30720 \cdot T_s$ = 1 ms, and subframes can be designated as uplink (U), downlink (D), or special subframe (S), depending on the Uplink-Downlink configuration as indicated in Table 4.2-2 of 3GPP TS 36.211. In the transmission duty factor calculation, the special subframe configuration with the shortest UpPTS duration within the special subframe is used and will be applied for measurement. From 3GPP TS 36.211 Table 4.2-1, the shortest UpPTS is 2192 · Ts which occurs in the normal cyclic prefix and special subframe configuration 4.

See table below outlining the calculated transmission duty cycles for each Uplink-Downlink configuration:

Table 10-1
Uplink-Downlink Configurations for Type 2 Frame Structures

Uplink-downlink configuration	Downlink-to-Uplink Switch-point periodicity	Subframe number										Calculated Transmission
Comiguration	Switch-point periodicity	0	1	2	3	4	5	6	7	8	9	Duty Cycle (%)
0	5 ms	D	S	U	U	U	D	S	U	U	U	61.4%
1	5 ms	D	S	U	U	D	D	S	U	U	D	41.4%
2	5 ms	D	S	U	D	D	D	S	U	D	D	21.4%
3	10 ms	D	S	U	U	U	D	D	D	D	D	30.7%
4	10 ms	D	S	U	U	D	D	D	D	D	D	20.7%
5	10 ms	D	S	U	D	D	D	D	D	D	D	10.7%
6	5 ms	D	S	U	U	U	D	S	U	U	D	51.4%

II. Power Class 3 Uplink-Downlink Configuration Additional Testing

LTE TDD was evaluated with the following radio configuration: channel 40620, 20MHz BW, 16QAM, 1RB, 0RB Offset. For Power Class 3, all configurations (0-6) are supported. The configuration which resulted in the worst-case emission was used for full testing. See Table 10-2 below for investigation results. The configuration determined in the investigation below was used to measure the MIF values in Table 7-5.

Table 10-2
LTE TDD Power Class 3 UL-DL Configuration Investigation Results

Mode / Band	Bandwidth	Channel	UL-DL Config.		RB Size	RB Offset	Scan Center	Time Avg. Field (V/m)	Time Avg. Field [dB(V/m)]	MIF (dB)	Audio Interference Level [dB(V/m)]	FCC Limit (dBV/m)	FCC Margin (dB)	Result	Excl Blocks per 5.5
E-Field Emiss	ions														
	20	40620	0	16QAM	1	0	Acoustic	17.10	24.66	-3.17	21.49	35.00	-13.51	M4	none
	20	40620	1	16QAM	1	0	Acoustic	13.70	22.73	-1.45	21.28	35.00	-13.72	M4	none
	20	40620	2	16QAM	1	0	Acoustic	10.27	20.23	1.50	21.73	35.00	-13.27	M4	none
LTE TDD / Band 41	20	40620	3	16QAM	1	0	Acoustic	11.90	21.51	-1.44	20.07	35.00	-14.93	M4	none
	20	40620	4	16QAM	1	0	Acoustic	9.83	19.85	0.69	20.54	35.00	-14.46	M4	none
	20	40620	5	16QAM	1	0	Acoustic	7.22	17.17	3.55	20.72	35.00	-14.28	M4	none
	20	40620	6	16QAM	1	0	Acoustic	16.28	24.23	-2.51	21.72	35.00	-13.28	M4	none

FCC ID: A3LSMG960U	PCTEST HA	AC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 54 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Fage 54 01 104

III. Power Class 2 Uplink-Downlink Configuration Additional Testing

LTE TDD was evaluated with the following radio configuration: channel 40620, 20MHz BW, 16QAM, 1RB, 0RB Offset. For Power Class 2, only configurations 1-5 are supported. The configuration which resulted in the worst-case emission was used for full testing. See Table 10-3 below for investigation results. The configuration determined in the investigation below was used to measure the MIF values in Table 7-6.

 Table 10-3

 LTE TDD Power Class 2 UL-DL Configuration Investigation Results

Mode / Band		Channel	UL-DL Config.	Mod	RB Size	RB Offset	Scan Center	Time Avg. Field (V/m)	Time Avg. Field [dB(V/m)]	MIF (dB)	Audio Interference Level [dB(V/m)]	FCC Limit (dBV/m)	FCC Margin (dB)	Result	Excl Blocks per 5.5
E-Field Emiss	ions														
	20	40620	1	16QAM	1	0	Acoustic	15.00	23.52	-1.56	21.96	35.00	-13.04	M4	none
	20	40620	2	16QAM	1	0	Acoustic	14.95	23.49	1.64	25.13	35.00	-9.87	M4	none
LTE TDD / Band 41	20	40620	3	16QAM	1	0	Acoustic	12.49	21.93	-1.28	20.65	35.00	-14.35	M4	none
	20	40620	4	16QAM	1	0	Acoustic	10.08	20.07	0.74	20.81	35.00	-14.19	M4	none
	20	40620	5	16QAM	1	0	Acoustic	8.20	18.28	3.67	21.95	35.00	-13.05	M4	none

IV. Conclusion

Per the investigations above, UL-DL Configuration 2 was used for both LTE TDD Power Class 3 and LTE TDD Power Class 2 testing.

FCC ID: A3LSMG960U	PCTEST HA	AC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 55 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Fage 55 01 104

11. OVERALL MEASUREMENT SUMMARY

FCC ID:	A3LSMG960U
S/N:	86391

I. E-FIELD EMISSIONS:

Table 11-1 HAC Data Summary for CDMA E-field

	TIAO Data Guillilary for Oblita E-field											
Mode	Channel	RC/SO	Scan Center	Conducted Power at BS (dBm)	Time Avg. Field (V/m)	Time Avg. Field [dB(V/m)]	MIF (dB)	Audio Interference Level [dB(V/m)]	FCC Limit (dBV/m)	FCC Margin (dB)	Result	Excl Blocks per 5.5
E-Field Emissi	ions											
	564*	RC1/SO3	Acoustic	24.83	16.48	24.34	3.07	27.41	45.00	-17.59	M4	none
Cellular	1013	RC1/SO3	Acoustic	24.31	12.41	21.88	3.05	24.93	45.00	-20.07	M4	none
CDMA	384	RC1/SO3	Acoustic	24.45	10.67	20.56	3.03	23.59	45.00	-21.41	M4	none
	777	RC1/SO3	Acoustic	24.47	10.90	20.75	3.04	23.79	45.00	-21.21	M4	none
	25	RC1/SO3	Acoustic	24.25	8.82	18.91	3.02	21.93	35.00	-13.07	M4	none
PCS CDMA	600	RC1/SO3	Acoustic	24.16	7.35	17.32	3.02	20.34	35.00	-14.66	M4	none
	1175	RC1/SO3	Acoustic	24.30	5.95	15.49	3.05	18.54	35.00	-16.46	M4	none

*Note: Cell. CDMA Ch. 564 is the Part 90S test channel.

Table 11-2
HAC Data Summary for GSM E-field

		1									
Mode	Channel	Scan Center	Conducted Power at BS (dBm)	Time Avg. Field (V/m)	Time Avg. Field [dB(V/m)]	MIF (dB)	Audio Interference Level [dB(V/m)]	FCC Limit (dBV/m)	FCC Margin (dB)	Result	Excl Blocks per 5.5
E-Field Emissi	ons										
	128	Acoustic	32.87	25.88	28.26	3.55	31.81	45.00	-13.19	M4	none
GSM850	190	Acoustic	32.80	26.23	28.38	3.55	31.93	45.00	-13.07	M4	none
	251	Acoustic	33.00	31.17	29.88	3.55	33.43	45.00	-11.57	M4	none
	512	Acoustic	29.64	14.68	23.34	3.56	26.90	35.00	-8.10	M4	none
GSM1900	661	Acoustic	29.47	13.49	22.60	3.56	26.16	35.00	-8.84	M4	none
G3W1900	810	Acoustic	29.64	8.82	18.91	3.56	22.47	35.00	-12.53	M4	none
	512	T-Coil	29.64	14.68	23.34	3.56	26.90	35.00	-8.10	M4	none

Table 11-3 HAC Data Summary for LTE TDD Power Class 3 E-field

Mode / Band	Bandwidth	Channel	UL-DL Config.		RB Size	RB Offset	Scan Center	Conducted Power at BS (dBm)	Time Avg. Field (V/m)	Time Avg. Field [dB(V/m)]	MIF (dB)	Audio Interference Level [dB(V/m)]	FCC Limit (dBV/m)	FCC Margin (dB)	Result	Excl Blocks per 5.5
E-Field Emissi	ions															
	20	39750	2	16QAM	1	0	Acoustic	23.04	8.64	18.73	1.61	20.34	35.00	-14.66	M4	none
	20	40185	2	16QAM	1	0	Acoustic	23.28	9.18	19.25	1.62	20.87	35.00	-14.13	M4	none
LTE TDD / Band 41	20	40620	2	16QAM	1	0	Acoustic	23.24	10.14	20.12	1.62	21.74	35.00	-13.26	M4	none
	20	41055	2	16QAM	1	0	Acoustic	22.82	10.48	20.41	1.60	22.01	35.00	-12.99	M4	none
	20	41490	2	16QAM	1	0	Acoustic	23.20	9.32	19.38	1.61	20.99	35.00	-14.01	M4	none

Table 11-4 HAC Data Summary for LTE TDD Power Class 2 E-field

Mode / Band	Bandwidth	Channel	UL-DL Config.		RB Size	RB Offset	Scan Center	Conducted Power at BS (dBm)	Time Avg. Field (V/m)	Time Avg. Field [dB(V/m)]	MIF (dB)	Audio Interference Level [dB(V/m)]	FCC Limit (dBV/m)	FCC Margin (dB)	Result	Excl Blocks per 5.5
E-Field Emissi	ons															
	20	39750	2	16QAM	1	0	Acoustic	26.30	12.41	21.88	1.65	23.53	35.00	-11.47	M4	none
	20	40185	2	16QAM	1	0	Acoustic	26.50	11.72	21.38	1.65	23.03	35.00	-11.97	M4	none
LTE TDD / Band 41	20	40620	2	16QAM	1	0	Acoustic	26.49	14.43	23.18	1.67	24.85	35.00	-10.15	M4	none
	20	41055	2	16QAM	1	0	Acoustic	26.16	10.85	20.71	1.64	22.35	35.00	-12.65	M4	none
	20	41490	2	16QAM	1	0	Acoustic	26.47	11.98	21.57	1.65	23.22	35.00	-11.78	M4	none

FCC ID: A3LSMG960U	PCTEST HA	AC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogg F6 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 56 of 104

© 2017 PCTEST Engineering Laboratory, Inc.

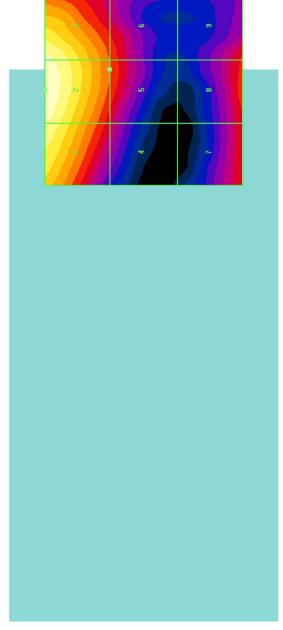


Figure 11-1
Sample E-field Scan Overlay
(See Test Setup Photographs for actual WD overlay)

FCC ID: A3LSMG960U	PCTEST*	HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogo 57 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 57 of 104

II. Worst-case Configuration Evaluation

Table 11-5
Peak Reading 360° Probe Rotation at Azimuth axis

Mode	Channel	Scan Center	Time Avg. Field (V/m)	Time Avg. Field [dB(V/m)]	MIF (dB)	Audio Interference Level [dB(V/m)]	FCC Limit (dBV/m)	FCC Margin (dB)	Result	Excl Blocks per 5.5
Probe Rotatio	n at Worst-Cas	е								
GSM1900	512	Acoustic	14.73	23.36	3.56	26.92	35.00	-8.08	M4	none

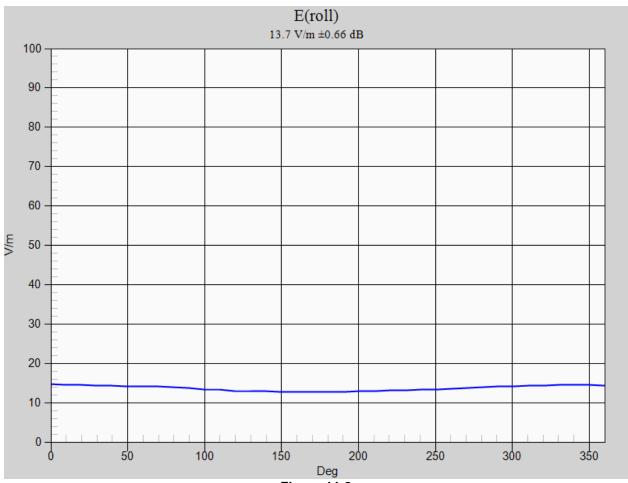


Figure 11-2
Worst-Case Probe Rotation about Azimuth axis

FCC ID: A3LSMG960U	PCTEST*	HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 58 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Faye 30 01 104

^{*} Note: Locations of probe rotation (with and without exclusions) are shown in Figure 11-1 denoted by the green square markers.

12. EQUIPMENT LIST

Table 12-1 Equipment List

Manufacturer	Model	Description	Cal Date	Cal Interval	Cal Due	Serial Number
Agilent	E4438C	ESG Vector Signal Generator	3/24/2017	Biennial	3/24/2019	MY42082385
Agilent	E4432B	ESG-D Series Signal Generator	3/24/2017	Annual	3/24/2018	US40053896
Agilent	N5182A	MXG Vector Signal Generator	2/28/2017	Annual	2/28/2018	MY47420800
Amplifier Research	15S1G6	Amplifier	N/A	CBT*	N/A	433978
Anritsu	ML2496A	Power Meter	4/20/2017	Annual	4/20/2018	1306009
Anritsu	MA2411B	Pulse Power Sensor	2/10/2017	Annual	2/10/2018	1207364
Anritsu	MA2411B	Pulse Power Sensor	2/10/2017	Annual	2/10/2018	1339018
Anritsu	MA24106A	USB Power Sensor	6/7/2017	Annual	6/7/2018	1244512
Anritsu	MA24106A	USB Power Sensor	6/7/2017	Annual	6/7/2018	1248508
Anritsu	MT8821C	Radio Communication Analyzer	8/15/2017	Annual	8/15/2018	6200901190
Mini-Circuits	NLP-1200+	Low Pass Filter DC to 1000 MHz	N/A	CBT*	N/A	N/A
Mini-Circuits	NLP-2950+	Low Pass Filter DC to 2700 MHz	N/A	CBT*	N/A	N/A
Mini-Circuits	BW-N20W5	Power Attenuator	N/A	CBT*	N/A	1226
Pasternack	PE2237-20	Bidirectional Coupler	N/A	CBT*	N/A	N/A
Rohde & Schwarz	CMU200	Base Station Simulator	4/11/2017	Annual	4/11/2018	836371/0079
Rohde & Schwarz	CMU200	Base Station Simulator	12/12/2016	Annual	12/12/2017	833855/0010
Rohde & Schwarz	CMW500	Radio Communication Tester	4/12/2017	Annual	4/12/2018	128635
Seekonk	NC-100	Torque Wrench (8" lb)	9/1/2016	Biennial	9/1/2018	21053
SPEAG	AIA	Audio Interference Analzyer	N/A	CBT*	N/A	1010
SPEAG	DAE4	Dasy Data Acquisition Electronics	5/17/2017	Annual	5/17/2018	859
SPEAG	CD2600V3	Freespace 2600 MHz Dipole	6/14/2017	Biennial	6/14/2019	1013
SPEAG	CD1880V3	Freespace 1880 MHz Dipole	5/12/2016	Biennial	5/12/2018	1064
SPEAG	CD835V3	Freespace 835 MHz Dipole	5/10/2016	Biennial	5/10/2018	1082
SPEAG	ER3DV6	Freespace E-field Probe	1/16/2017	Annual	1/16/2018	2353

Calibration traceable to the National Institute of Standards and Technology (NIST).

*Note: CBT (Calibrated Before Testing). Prior to testing, the measurement paths containing a cable, attenuator, coupler or filter were connected to a calibrated source (i.e. a signal generator) to determine the losses of the measurement path. The power meter offset was then adjusted to compensate for the measurement system losses. This level offset is stored within the power meter before measurements are made. This calibration verification procedure applies to the system verification and output power measurements. The calibrated reading is then taken directly from the power meter after compensation of the losses for all final power measurements.

FCC ID: A3LSMG960U	PCTEST HA	C (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 59 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Fage 59 01 104

13. MEASUREMENT UNCERTAINTY

Table 13-1 Uncertainty Estimation Table

Wireless Communications Device Near-Field Measurement							
		Uncert	ainty Estima	ation			
Uncertainty Component	Data (dB)	Data Type	Prob. Dist.	Divisor	Ci (E)	Unc. (dB)	Notes/Comments
Measurement System	•	-	-			-	
RF System Reflections	0.50	Tolerance	N	1.00	1	0.50	* Refl. < -20 dB
Field Probe Calibration	0.21	Tolerance	N	1.00	1	0.21	
Field Probe Isotropy	0.01	Tolerance	N	1.00	1	0.01	
Field Probe Frequency Response	0.135	Tolerance	N	1.00	1	0.14	
Field Probe Linearity	0.013	Tolerance	N	1.00	1	0.01	
Modulation Interference Factor	0.20	Tolerance	R	1.73	1	0.12	Applicable for M-rating testing
Boundary Effects	0.105	Accuracy	R	1.73	1	0.06	*
Probe Positioning Accuracy	0.20	Accuracy	R	1.73	1	0.12	*
Probe Positioner	0.050	Accuracy	R	1.73	1	0.03	*
Extrapolation/Interpolation	0.045	Tolerance	R	1.73	1	0.03	*
Resolution to 2mm error	0.21	Tolerance	N	1.00	1	0.21	
System Detection Limit	0.05	Tolerance	R	1.73	1	0.03	*
Readout Electronics	0.015	Tolerance	N	1.00	1	0.02	*
Integration Time	0.11	Tolerance	R	1.73	1	0.06	*
Response Time	0.033	Tolerance	R	1.73	1	0.02	*
Phantom Thickness	0.10	Tolerance	R	1.73	1	0.06	*
System Repeatability (Field x 2=power)	0.17	Tolerance	N	1.00	1	0.17	*
Test Sample Related							
Device Positioning Vertical	0.2	Tolerance	R	1.73	1	0.12	*
Device Positioning Lateral	0.045	Tolerance	R	1.73	1	0.03	*
Device Holder and Phantom	0.1	Tolerance	R	1.73	1	0.06	*
Power Drift	0.21	Tolerance	R	1.73	1	0.12	
Combined Standard Uncertainty (k=1)						0.66	16.3%
Expanded Uncertainty [95% confidence]					1.31	32.6%	
xpanded Uncertainty [95% confidence] on Field					0.66	16.3%	

Notes:

- Test equipments are calibrated according to techniques outlined in NIS81, NIS3003 and NIST Tech Note 1297. All
 equipments have traceability according to NIST. Measurement Uncertainties are defined in further detail in NIS 81
 and NIST Tech Note 1297 and UKAS M3003.
- 2. * Uncertainty specifications from Schmidt & Partner Engineering AG (not site specific)

Measurement uncertainty reflects the quality and accuracy of a measured result as compared to the true value. Such statements are generally required when stating results of measurements so that it is clear to the intended audience that the results may differ when reproduced by different facilities. Measurement results vary due to the measurement uncertainty of the instrumentation, measurement technique, and test engineer. Most uncertainties are calculated using the tolerances of the instrumentation used in the measurement, the measurement setup variability, and the technique used in performing the test. While not generally included, the variability of the equipment under test also figures into the overall measurement uncertainty. Another component of the overall uncertainty is based on the variability of repeated measurements (so-called Type A uncertainty). This may mean that the Hearing Aid immunity tests may have to be repeated by taking down the test setup and resetting it up so that there are a statistically significant number of repeat measurements to identify the measurement uncertainty. By combining the repeat measurement results with that of the instrumentation chain using the technique contained in NIS 81 and NIS 3003, the overall measurement uncertainty was estimated.

FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 60 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		rage ou of 104

TEST DATA 14.

See following Attached Pages for Test Data.

FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogo 61 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 61 of 104



DUT: CD835V3 - SN1082

Type: CD835V3 Serial: 1082

Communication System: CW; Frequency: 835 MHz;

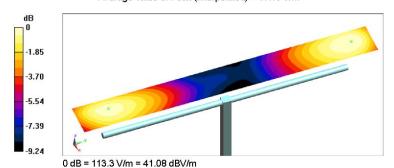
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

DASY5 Configuration:

- Probe: ER3DV6 SN2353; Calibrated: 1/16/2017;
- · Sensor-Surface: 0mm (Fix Surface)
- Electronics: DAE4 Sn859; Calibrated: 5/17/2017
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

835 MHz / 100mW HAC Dipole Validation at 15mm/Hearing Aid Compatibility Test (41x361x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 120.4 V/m; Power Drift = -0.05 dB
Applied MIF = 0.00 dB
Average Value of Peak (interpolated) = 111.6 V/m



FCC ID: A3LSMG960U	PCTEST	HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 62 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		raye 02 01 104



DUT: CD1880V3 - SN1064

Type: CD1880V3 Serial: 1064

Communication System: CW; Frequency: 1880 MHz;

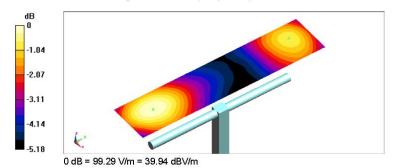
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

DASY5 Configuration:

- Probe: ER3DV6 SN2353; Calibrated: 1/16/2017;
- · Sensor-Surface: 0mm (Fix Surface)
- Electronics: DAE4 Sn859; Calibrated: 7/21/2009
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

1880 MHz / 100mW HAC Dipole Validation at 15mm/Hearing Aid Compatibility Test (41x181x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 161.3 V/m; Power Drift = 0.03 dB
Applied MIF = 0.00 dB
Average Value of Peak (interpolated) = 95.3 V/m



FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 63 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Fage 03 01 104

Date: 12/11/2017



DUT: CD2600V3 - SN1013

Type: CD2600V3 Serial: 1013

Communication System: CW; Frequency: 2600 MHz;

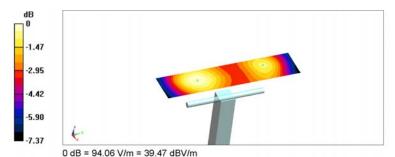
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

DASY5 Configuration:

- Probe: ER3DV6 SN2353; Calibrated: 1/16/2017;
- Sensor-Surface: 0mm (Fix Surface)
- Electronics: DAE4 Sn859; Calibrated: 7/21/2009
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

2600 MHz / 100mW HAC Dipole Validation at 15mm/Hearing Aid Compatibility Test (41x181x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 68.38 V/m; Power Drift = 0.01 dB
Applied MIF = 0.00 dB
Average Value of Peak (interpolated) = 89.7 V/m



FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogo 64 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 64 of 104



DUT: A3LSMG960U

Type: Portable Handset Serial: 86391 Backlight off Duty Cycle: 1:8

Communication System: CDMA; Frequency: 820.1 MHz;

Measurement Standard: DASY5 (IEEE/IEC/ANSI 063.19-2011)

DASY5 Configuration:

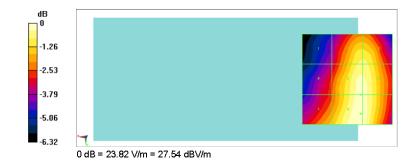
- Probe: ER3DV6 SN2353; Calibrated: 1/16/2017;
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn859; Calibrated: 5/17/2017
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

Extended Cell. CDMA Mid Channel / Hearing Aid Compatibility Test (101x101x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 20.40 V/m; Power Drift = -0.13 dB
Applied MIF = 3.07 dB
RF audio interference level = 27.41 dBV/m
Emission category: M4

MIF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
24.05 dBV/m	26.86 dBV/m	26.86 dBV/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
24.97 dBV/m	27.29 dBV/m	27.28 dBV/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
26.09 dBV/m	27.41 dBV/m	27.39 dBV/m



FCC ID: A3LSMG960U	PCTEST	HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 65 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Fage 03 01 104



DUT: A3LSMG960U

Type: Portable Handset Serial: 86391 Backlight off Duty Cycle: 1:8

Communication System: CDMA; Frequency: 1851.25 MHz;

Measurement Standard: DASY5 (IEEE/IEC/ANSI 063.19-2011)

DASY5 Configuration:

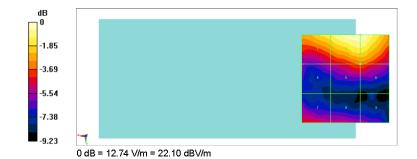
- Probe: ER3DV6 SN2353; Calibrated: 1/16/2017;
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn859; Calibrated: 5/17/2017
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

PCS CDMA Low Channel / Hearing Aid Compatibility Test (101x101x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 5.338 V/m; Power Drift = 0.19 dB
Applied MIF = 3.02 dB
RF audio interference level = 21.93 dBV/m
Emission category: M4

MIF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
20.79 dBV/m	21.93 dBV/m	21.93 dBV/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
16.98 dBV/m	18.61 dBV/m	18.61 dBV/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
17.79 dBV/m	17.09 dBV/m	16.52 dBV/m



FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 66 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		raye 00 01 104



DUT: A3LSMG960U

Type: Portable Handset Serial: 86391 Backlight off Duty Cycle: 1:8.3

Communication System: GSM; Frequency: 848.8 MHz;

Measurement Standard: DASY5 (IEEE/IEC/ANSI 063.19-2011)

DASY5 Configuration:

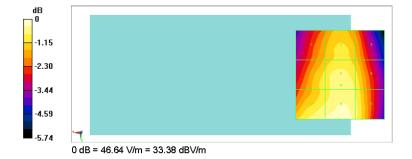
- Probe: ER3DV6 SN2353; Calibrated: 1/16/2017;
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn859; Calibrated: 5/17/2017
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

GSM850 High Channel / Hearing Aid Compatibility Test (101x101x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 37.07 V/m; Power Drift = 0.11 dB
Applied MIF = 3.55 dB
RF audio interference level = 33.43 dBV/m
Emission category: M4

MIF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
31.94 dBV/m	32.41 dBV/m	32.01 dBV/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
32.48 dBV/m	32.87 dBV/m	32.59 dBV/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
33.09 dBV/m	33.43 dBV/m	32.79 dBV/m



Ī	FCC ID: A3LSMG960U	PCTEST	HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
	Filename:	Test Dates:	DUT Type:		Page 67 of 104
	1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Fage 07 01 104



DUT: A3LSMG960U

Type: Portable Handset Serial: 86391 Backlight off Duty Cycle: 1:8.3

Communication System: GSM; Frequency: 1850.2 MHz;

Measurement Standard: DASY5 (IEEE/IEC/ANSI 063.19-2011)

DASY5 Configuration:

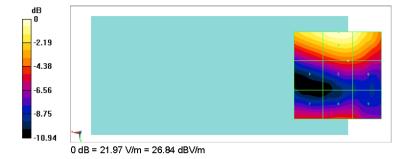
- Probe: ER3DV6 SN2353; Calibrated: 1/16/2017;
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn859; Calibrated: 5/17/2017
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

GSM1900 Low Channel / Hearing Aid Compatibility Test (101x101x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm
Device Reference Point: 0, 0, -6.3 mm
Reference Value = 8.346 V/m; Power Drift = -0.16 dB
Applied MIF = 3.56 dB
RF audio interference level = 26.90 dBV/m
Emission category: M4

MIF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
26.25 dBV/m	26.9 dBV/m	26.47 dBV/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
21.24 dBV/m	22.47 dBV/m	22.42 dBV/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
21.84 dBV/m	22.29 dBV/m	22.01 dBV/m



FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dago 69 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 68 of 104

Date: 12/11/2017



DUT: A3LSMG960U

Type: Portable Handset Serial: 86391 Backlight off Duty Cycle: 1:4.67

Communication System: LTE TDD41; Frequency: 2636.5 MHz;

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

DASY5 Configuration:

- Probe: ER3DV6 SN2353; Calibrated: 1/16/2017;
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn859; Calibrated: 5/17/2017
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

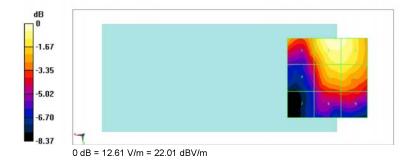
Power Class 3 TDD LTE Band 41 Mid High Channel, 20MHz BW, 16QAM, 1RB, 0 RB Offset

Hearing Aid Compatibility Test (101x101x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 8.617 V/m; Power Drift = 0.11 dB Applied MIF = 1.60 dB RF audio interference level = 22.01 dBV/m Emission category: M4

MIF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
19.99 dBV/m	22.01 dBV/m	21.85 dBV/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
18.19 dBV/m	20.89 dBV/m	20.89 dBV/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
16.26 dBV/m	18.59 dBV/m	18.62 dBV/m



FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 69 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Fage 09 01 104

Date: 12/11/2017



DUT: A3LSMG960U

Type: Portable Handset Serial: 86391 Backlight off Duty Cycle: 1:4.67

Communication System: LTE TDD41; Frequency: 2593 MHz;

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

DASY5 Configuration:

- Probe: ER3DV6 SN2353; Calibrated: 1/16/2017;
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn859; Calibrated: 5/17/2017
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

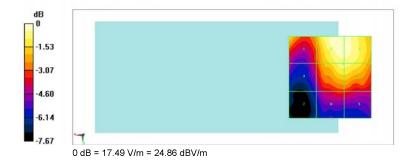
Power Class 2 TDD LTE Band 41 Mid Channel, 20MHz BW, 16QAM, 1RB, 0 RB Offset

Hearing Aid Compatibility Test (101x101x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 13.44 V/m; Power Drift = -0.12 dB Applied MIF = 1.67 dB RF audio interference level = 24.85 dBV/m Emission category: M4

MIF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
23.58 dBV/m	24.85 dBV/m	24.83 dBV/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
21.46 dBV/m	24.09 dBV/m	24.09 dBV/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
19.51 dBV/m	21.58 dBV/m	21.5 dBV/m



FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 70 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Fage 70 01 104

15. CALIBRATION CERTIFICATES

The following pages include the probe calibration used to evaluate HAC for the DUT.

FCC ID: A3LSMG960U	PCTEST HA	HAC (RF EMISSIONS) TEST REPORT		Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogg 71 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 71 of 104

Calibration Laboratory of Schmid & Partner Engineering AG Zeughausstrasse 43, 8004 Zurich, Switzerland





S Schweizerischer Kalibrierdienst
C Service suisse d'étalonnage
S Servizio svizzero di taratura
Swiss Calibration Service

Accreditation No.: SCS 0108

Accredited by the Swiss Accreditation Service (SAS)

The Swiss Accreditation Service is one of the signatories to the EA

Multilateral Agreement for the recognition of calibration certificates

Client PC Test

1

Certificate No: ER3-2353_Jan17

CALIBRATION CERTIFICATE

Object

ER3DV6 - SN:2353

Calibration procedure(s)

QA CAL-02.v8, QA CAL-25.v6

Calibration procedure for E-field probes optimized for close near field

evaluations in air

Calibration date:

January 16, 2017

This calibration certificate documents the traceability to national standards, which realize the physical units of measurements (SI).

The measurements and the uncertainties with confidence probability are given on the following pages and are part of the certificate.

/OH 2/2/2017

All calibrations have been conducted in the closed laboratory facility: environment temperature (22 ± 3)°C and humidity < 70%.

Calibration Equipment used (M&TE critical for calibration)

Primary Standards	ID	Cal Date (Certificate No.)	Scheduled Calibration
Power meter NRP	SN: 104778	06-Apr-16 (No. 217-02288/02289)	Apr-17
Power sensor NRP-Z91	SN: 103244	06-Apr-16 (No. 217-02288)	Apr-17
Power sensor NRP-Z91	SN: 103245	06-Apr-16 (No. 217-02289)	Apr-17
Reference 20 dB Attenuator	SN: S5277 (20x)	05-Apr-16 (No. 217-02293)	Apr-17
Reference Probe ER3DV6	SN: 2328	14-Oct-16 (No. ER3-2328_Oct16)	Oct-17
DAE4	SN: 789	11-Nov-16 (No. DAE4-789_Nov16)	Nov-17
Secondary Standards	ID	Check Date (in house)	Scheduled Check
Power meter E4419B	SN: GB41293874	06-Apr-16 (in house check Jun-16)	In house check: Jun-18
Power sensor E4412A	SN: MY41498087	06-Apr-16 (in house check Jun-16)	In house check: Jun-18
Power sensor E4412A	SN: 000110210	06-Apr-16 (in house check Jun-16)	In house check: Jun-18
RF generator HP 8648C	SN: US3642U01700	04-Aug-99 (in house check Jun-16)	In house check: Jun-18
Network Analyzer HP 8753F	SN: US37390585	18-Oct-01 (in house check Oct-16)	In house check: Oct-17

Calibrated by:

Name Johannes Kurikka Function

Signature

Approved by:

Katja Pokovic

Technical Manager

Laboratory Technician

Issued: January 16, 2017

This calibration certificate shall not be reproduced except in full without written approval of the laboratory.

Certificate No: ER3-2353_Jan17

Page 1 of 10

FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogo 72 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 72 of 104

Calibration Laboratory of Schmid & Partner

Engineering AG Zeughausstrasse 43, 8004 Zurich, Switzerland





Schwelzerischer Kalibrierdienst Service suisse d'étalonnage C Servizio svizzero di taratura **Swiss Calibration Service**

Accreditation No.: SCS 0108

Accredited by the Swiss Accreditation Service (SAS)

The Swiss Accreditation Service is one of the signatories to the EA Multilateral Agreement for the recognition of calibration certificates

Glossary:

NORMx,y,z

sensitivity in free space diode compression point

DCP CF

crest factor (1/duty_cycle) of the RF signal modulation dependent linearization parameters

A, B, C, D

Polarization ϕ

φ rotation around probe axis

Polarization 9

9 rotation around an axis that is in the plane normal to probe axis (at measurement center),

i.e., 9 = 0 is normal to probe axis

Connector Angle

information used in DASY system to align probe sensor X to the robot coordinate system

Calibration is Performed According to the Following Standards:

- a) IEEE Std 1309-2005, "IEEE Standard for calibration of electromagnetic field sensors and probes, excluding antennas, from 9 kHz to 40 GHz", December 2005
- b) CTIA Test Plan for Hearing Aid Compatibility, Rev 3.0, November 2013

Methods Applied and Interpretation of Parameters:

- NORMx,y,z: Assessed for E-field polarization ϑ = 0 for XY sensors and ϑ = 90 for Z sensor (f \leq 900 MHz in TEM-cell; f > 1800 MHz: R22 waveguide).
- $NORM(f)x,y,z = NORMx,y,z * frequency_response$ (see Frequency Response Chart).
- DCPx,y,z: DCP are numerical linearization parameters assessed based on the data of power sweep with CW signal (no uncertainty required). DCP does not depend on frequency nor media.
- PAR: PAR is the Peak to Average Ratio that is not calibrated but determined based on the signal characteristics
- Ax,y,z; Bx,y,z; Cx,y,z; Dx,y,z; VRx,y,z: A, B, C, D are numerical linearization parameters assessed based on the data of power sweep for specific modulation signal. The parameters do not depend on frequency nor media. VR is the maximum calibration range expressed in RMS voltage across the diode.
- Spherical isotropy (3D deviation from isotropy): in a locally homogeneous field realized using an open wavequide setup.
- Sensor Offset: The sensor offset corresponds to the offset of virtual measurement center from the probe tip (on probe axis). No tolerance required.
- Connector Angle: The angle is assessed using the information gained by determining the NORMx (no uncertainty required).

Certificate No: ER3-2353 Jan17

Page 2 of 10

FCC ID: A3LSMG960U	PCTEST HA	HAC (RF EMISSIONS) TEST REPORT		Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 73 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Fage 73 01 104

ER3DV6 – SN:2353 January 16, 2017

Probe ER3DV6

SN:2353

Manufactured: Calibrated:

March 8, 2005 January 16, 2017

Calibrated for DASY/EASY Systems (Note: non-compatible with DASY2 system!)

Certificate No: ER3-2353_Jan17

Page 3 of 10

FCC ID: A3LSMG960U	PCTEST HA	HAC (RF EMISSIONS) TEST REPORT		Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogo 74 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 74 of 104

ER3DV6 -- SN:2353 January 16, 2017

DASY/EASY - Parameters of Probe: ER3DV6 - SN:2353

Basic Calibration Parameters

	Sensor X	Sensor Y	Sensor Z	Unc (k=2)
Norm (µV/(V/m) ²)	1.49	1.68	1.78	± 10.1 %
DCP (mV) ^B	99.3	98.2	100.1	

Modulation Calibration Parameters

UID	Communication System Name		A dB	B dB√μV	С	D dB	VR mV	Unc ^E (k=2)
0	CW	X	0.0	0.0	1.0	0.00	210.4	±3.8 %
		Y	0.0	0.0	1.0		207.1	
		Z	0.0	0.0	1.0		201.5	

The reported uncertainty of measurement is stated as the standard uncertainty of measurement multiplied by the coverage factor k=2, which for a normal distribution corresponds to a coverage probability of approximately 95%.

Certificate No: ER3-2353_Jan17

Page 4 of 10

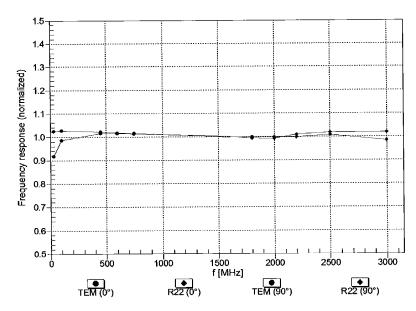
FCC ID: A3LSMG960U	PCTEST HA	HAC (RF EMISSIONS) TEST REPORT		Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 75 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Fage 75 01 104

B Numerical linearization parameter: uncertainty not required.

E Uncertainty is determined using the max. deviation from linear response applying rectangular distribution and is expressed for the square of the field value.

January 16, 2017 ER3DV6 - SN:2353

Frequency Response of E-Field (TEM-Cell:ifi110 EXX, Waveguide: R22)



Uncertainty of Frequency Response of E-field: ± 6.3% (k=2)

Certificate No: ER3-2353_Jan17 Page 5 of 10

FCC ID: A3LSMG960U	PCTEST: HA	HAC (RF EMISSIONS) TEST REPORT		Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogg 76 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 76 of 104

ER3DV6 – SN:2353 January 16, 2017

Receiving Pattern (ϕ), $\vartheta = 0^{\circ}$

f=600 MHz,TEM,0° f=2500 MHz,R22,0°

1355
186

02 04 06 08

Tot X

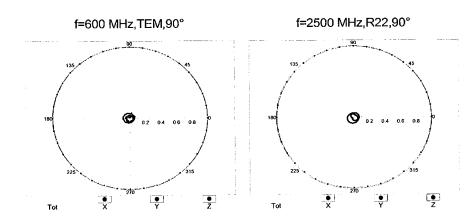
Tot X

Tot X

Tot X

Tot X

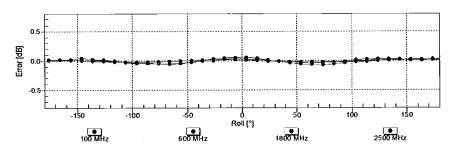
Receiving Pattern (ϕ), θ = 90°



Certificate No: ER3-2353_Jan17 Page 6 of 10

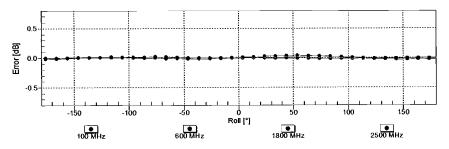
FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 77 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		rage 11 01 104

Receiving Pattern (ϕ), $\vartheta = 0^{\circ}$



Uncertainty of Axial Isotropy Assessment: $\pm 0.5\%$ (k=2)

Receiving Pattern (ϕ), $\vartheta = 90^{\circ}$



Uncertainty of Axial Isotropy Assessment: ± 0.5% (k=2)

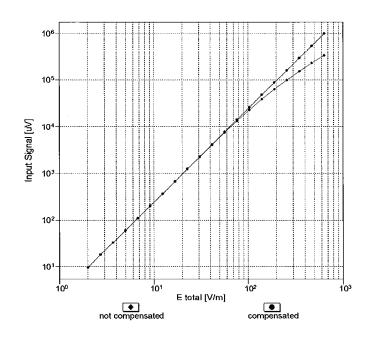
Certificate No: ER3-2353_Jan17

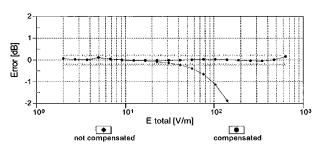
Page 7 of 10

FCC ID: A3LSMG960U	PCTEST HA	HAC (RF EMISSIONS) TEST REPORT		Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogg 70 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 78 of 104

ER3DV6 -- SN:2353 January 16, 2017

Dynamic Range f(E-field) (TEM cell , f = 900 MHz)





Uncertainty of Linearity Assessment: ± 0.6% (k=2)

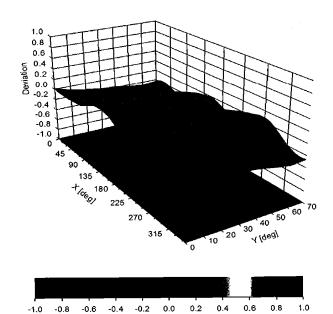
Certificate No: ER3-2353_Jan17 Page 8 of 10

FCC ID: A3LSMG960U	PCTEST HA	HAC (RF EMISSIONS) TEST REPORT		Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 79 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Fage 79 01 104

ER3DV6 – SN:2353 January 16, 2017

Deviation from Isotropy in Air

Error (φ, θ), f = 900 MHz



Uncertainty of Spherical Isotropy Assessment: ± 2.6% (k=2)

Certificate No: ER3-2353_Jan17 Page 9 of 10

FCC ID: A3LSMG960U	PCTEST HA	HAC (RF EMISSIONS) TEST REPORT		Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogg 90 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 80 of 104

ER3DV6 - SN:2353 January 16, 2017

DASY/EASY - Parameters of Probe: ER3DV6 - SN:2353

Other Probe Parameters

Sensor Arrangement	Rectangular
Connector Angle (°)	23.8
Mechanical Surface Detection Mode	enabled
Optical Surface Detection Mode	disabled
Probe Overall Length	337 mm
Probe Body Diameter	10 mm
Tip Length	10 mm
Tip Diameter	8 mm
Probe Tip to Sensor X Calibration Point	2.5 mm
Probe Tip to Sensor Y Calibration Point	2.5 mm
Probe Tip to Sensor Z Calibration Point	2.5 mm

Certificate No: ER3-2353_Jan17 Page 10 of 10

FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 81 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		rage of 01 104

Calibration Laboratory of Schmid & Partner **Engineering AG**

Zeughausstrasse 43, 8004 Zurich, Switzerland





Schweizerischer Kalibrierdienst Service suisse d'étalonnage Servizio svizzero di taratura **Swiss Calibration Service**

Accredited by the Swiss Accreditation Service (SAS) The Swiss Accreditation Service is one of the signatories to the EA Multilateral Agreement for the recognition of calibration certificates

Accreditation No.: SCS 0108

Client **PC Test**

Certificate No: CD835V3-1082_May16

CALIBRATION CERTIFICATE Object CD835V3 - SN: 1082 Calibration procedure(s) QA CAL-20.v6 Calibration procedure for dipoles in air Calibration date: May 10, 2016 This calibration certificate documents the traceability to national standards, which realize the physical units of measurements (SI). The measurements and the uncertainties with confidence probability are given on the following pages and are part of the certificate. All calibrations have been conducted in the closed laboratory facility: environment temperature $(22 \pm 3)^{\circ}$ C and humidity < 70%. Calibration Equipment used (M&TE critical for calibration) Primary Standards ID# Cal Date (Certificate No.) Scheduled Calibration Power meter NRP SN: 104778 06-Apr-16 (No. 217-02288/02289) Apr-17 Power sensor NRP-Z91 SN: 103244 06-Apr-16 (No. 217-02288) Apr-17 Power sensor NRP-Z91 SN: 103245 06-Apr-16 (No. 217-02289) Apr-17 Reference 20 dB Attenuator SN: 5058 (20k) 05-Apr-16 (No. 217-02292) Apr-17 Type-N mismatch combination SN: 5047.2 / 06327 05-Apr-16 (No. 217-02295) Apr-17 Probe ER3DV6 SN: 2336 31-Dec-15 (No. ER3-2336_Dec15) Dec-16 Probe H3DV6 SN: 6065 31-Dec-15 (No. H3-6065_Dec15) Dec-16 DAE4 SN: 781 04-Sep-15 (No. DAE4-781_Sep15) Sep-16 Secondary Standards ID# Check Date (in house) Scheduled Check SN: GB42420191 Power meter Agilent 4419B 09-Oct-09 (in house check Sep-14) In house check: Oct-17 Power sensor HP E4412A SN: US38485102 05-Jan-10 (in house check Sep-14) In house check: Oct-17 Power sensor HP 8482A SN: US37295597 09-Oct-09 (in house check Sep-14) In house check: Oct-17 RF generator R&S SMT-06 SN: 832283/011 27-Aug-12 (in house check Oct-15) In house check: Oct-17 Network Analyzer HP 8753E SN: US37390585 18-Oct-01 (in house check Oct-15) In house check: Oct-16 Name Function Signature Calibrated by: Jeton Kastrati Laboratory Technician Approved by: Katja Pokovic Technical Manager Issued: May 12, 2016 This calibration certificate shall not be reproduced except in full without written approval of the laboratory.

Approved by: PCTEST FCC ID: A3LSMG960U HAC (RF EMISSIONS) TEST REPORT SAMSUNG Quality Manager Filename: Test Dates: **DUT Type:** Page 82 of 104 1M1711010281-13-R1.A3L 11/06/2017 - 12/11/2017 Portable Handset

Page 1 of 5

Certificate No: CD835V3-1082_May16

Calibration Laboratory of Schmid & Partner **Engineering AG** Zeughausstrasse 43, 8004 Zurich, Switzerland





C

Schweizerischer Kalibrierdienst Service suisse d'étalonnage Servizio svizzero di taratura Swiss Calibration Service

Accreditation No.: SCS 0108

Accredited by the Swiss Accreditation Service (SAS) The Swiss Accreditation Service is one of the signatories to the EA Multilateral Agreement for the recognition of calibration certificates

References

ANSI-C63.19-2011 [1]

American National Standard, Methods of Measurement of Compatibility between Wireless Communications Devices and Hearing Aids.

Methods Applied and Interpretation of Parameters:

- Coordinate System: y-axis is in the direction of the dipole arms. z-axis is from the basis of the antenna (mounted on the table) towards its feed point between the two dipole arms. x-axis is normal to the other axes. In coincidence with the standards [1], the measurement planes (probe sensor center) are selected to be at a distance of 15 mm above the top metal edge of the dipole arms.
- Measurement Conditions: Further details are available from the hardcopies at the end of the certificate. All figures stated in the certificate are valid at the frequency indicated. The forward power to the dipole connector is set with a calibrated power meter connected and monitored with an auxiliary power meter connected to a directional coupler. While the dipole under test is connected, the forward power is adjusted to the same level.
- Antenna Positioning: The dipole is mounted on a HAC Test Arch phantom using the matching dipole positioner with the arms horizontal and the feeding cable coming from the floor. The measurements are performed in a shielded room with absorbers around the setup to reduce the reflections. It is verified before the mounting of the dipole under the Test Arch phantom, that its arms are perfectly in a line. It is installed on the HAC dipole positioner with its arms parallel below the dielectric reference wire and able to move elastically in vertical direction without changing its relative position to the top center of the Test Arch phantom. The vertical distance to the probe is adjusted after dipole mounting with a DASY5 Surface Check job. Before the measurement, the distance between phantom surface and probe tip is verified. The proper measurement distance is selected by choosing the matching section of the HAC Test Arch phantom with the proper device reference point (upper surface of the dipole) and the matching grid reference point (tip of the probe) considering the probe sensor offset. The vertical distance to the probe is essential for the
- Feed Point Impedance and Return Loss: These parameters are measured using a HP 8753E Vector Network Analyzer. The impedance is specified at the SMA connector of the dipole. The influence of reflections was eliminating by applying the averaging function while moving the dipole in the air, at least 70cm away from any
- E-field distribution: E field is measured in the x-y-plane with an isotropic ER3D-field probe with 100 mW forward power to the antenna feed point. In accordance with [1], the scan area is 20mm wide, its length exceeds the dipole arm length (180 or 90mm). The sensor center is 15 mm (in z) above the metal top of the dipole arms. Two 3D maxima are available near the end of the dipole arms. Assuming the dipole arms are perfectly in one line, the average of these two maxima (in subgrid 2 and subgrid 8) is determined to compensate for any non-parallelity to the measurement plane as well as the sensor displacement. The E-field value stated as calibration value represents the maximum of the interpolated 3D-E-field, in the plane above the dipole surface.

The reported uncertainty of measurement is stated as the standard uncertainty of measurement multiplied by the coverage factor k=2, which for a normal distribution corresponds to a coverage probability of approximately 95%.

Certificate No: CD835V3-1082_May16 Page 2 of 5

FCC ID: A3LSMG960U	PCTEST HA	AC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogg 93 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 83 of 104

Measurement Conditions

DASY system configuration, as far as not given on page 1.

DASY Version	DASY5	V52.8.8
Phantom	HAC Test Arch	
Distance Dipole Top - Probe Center	15 mm	
Scan resolution	dx, dy = 5 mm	
Frequency	835 MHz ± 1 MHz	
Input power drift	< 0.05 dB	

Maximum Field values at 835 MHz

E-field 15 mm above dipole surface	condition	Interpolated maximum	
Maximum measured above high end	100 mW input power	107.5 V/m = 40.63 dBV/m	
Maximum measured above low end	100 mW input power	106.1 V/m = 40.51 dBV/m	
Averaged maximum above arm	100 mW input power	106.8 V/m ± 12.8 % (k=2)	

Appendix (Additional assessments outside the scope of SCS 0108)

Antenna Parameters

Frequency	Return Loss	Impedance
800 MHz	16.4 dB	44.5 Ω - 13.4 jΩ
835 MHz	26.3 dB	50.0 Ω + 4.9 jΩ
900 MHz	16.4 dB	57.4 Ω - 14.7 jΩ
950 MHz	21.9 dB	43.6 Ω + 4.0 jΩ
960 MHz	17.2 dB	47.9 Ω + 13.5 jΩ

3.2 Antenna Design and Handling

The calibration dipole has a symmetric geometry with a built-in two stub matching network, which leads to the enhanced bandwidth.

The dipole is built of standard semirigid coaxial cable. The internal matching line is open ended. The antenna is therefore open for DC signals.

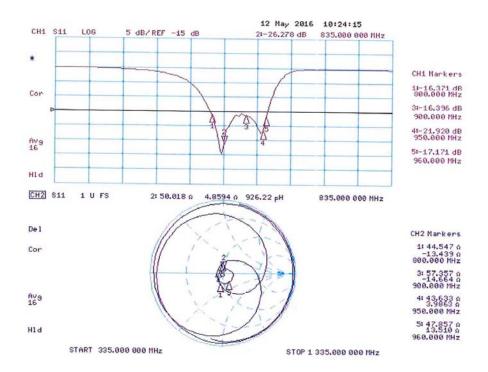
Do not apply force to dipole arms, as they are liable to bend. The soldered connections near the feedpoint may be damaged. After excessive mechanical stress or overheating, check the impedance characteristics to ensure that the internal matching network is not affected.

After long term use with 40W radiated power, only a slight warming of the dipole near the feedpoint can be measured.

Certificate No: CD835V3-1082_May16 Page 3 of 5

FCC ID: A3LSMG960U	PETEST*	HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogo 94 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 84 of 104

Impedance Measurement Plot



Certificate No: CD835V3-1082_May16

Page 4 of 5

FCC ID: A3LSMG960U	PCTEST	HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 85 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Fage 65 01 104

DASY5 E-field Result

Date: 10.05.2016

Test Laboratory: SPEAG Lab2

DUT: HAC-Dipole 835 MHz; Type: CD835V3; Serial: CD835V3 - SN: 1082

Communication System: UID 0 - CW; Frequency: 835 MHz Medium parameters used: $\sigma = 0$ S/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

DASY52 Configuration:

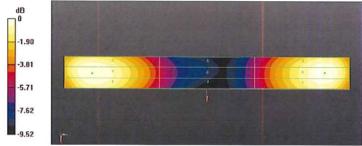
- Probe: ER3DV6 SN2336; ConvF(1, 1, 1); Calibrated: 31.12.2015;
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn781; Calibrated: 04.09.2015
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1070
- DASY52 52.8.8(1258); SEMCAD X 14.6.10(7372)

Dipole E-Field measurement @ 835MHz/E-Scan - 835MHz d=15mm/Hearing Aid Compatibility Test (41x361x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 109.8 V/m; Power Drift = 0.02 dB Applied MIF = 0.00 dB RF audio interference level = 40.63 dBV/m Emission category: M3

MIF scaled E-field

Grid 2 M3 40.63 dBV/m	Grid 3 M3 40.46 dBV/m
Grid 5 M4 35.78 dBV/m	Grid 6 M4 35.62 dBV/m
Grid 8 M3 40.51 dBV/m	Grid 9 M3 40.37 dBV/m



0 dB = 107.5 V/m = 40.63 dBV/m

Certificate No: CD835V3-1082_May16

Page 5 of 5

FCC ID: A3LSMG960U	PCTEST	HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 86 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		raye 00 01 104

Calibration Laboratory of Schmid & Partner Engineering AG Zeughausstrasse 43, 8004 Zurich, Switzerland





Schweizerischer Kalibrierdienst Service suisse d'étalonnage Servizio svizzero di taratura Swiss Calibration Service

Accredited by the Swiss Accreditation Service (SAS)

The Swiss Accreditation Service is one of the signatories to the EA

Multilateral Agreement for the recognition of calibration certificates

Accreditation No.: SCS 0108

Client PC Test

Certificate No: CD1880V3-1064 May16

	CERTIFICAT		
Object	CD1880V3 - SN	: 1064	
0.00	04.041.00		/
Calibration procedure(s)	QA CAL-20.v6 Calibration proce	edure for dipoles in air	05/25/201
Calibration date:	May 12, 2016		
This calibration certificate docum	ents the traceability to nati	onal standards, which realize the physical unitrobability are given on the following pages and	ts of measurements (SI).
All calibrations have been conduct Calibration Equipment used (M&		ry facility: environment temperature (22 ± 3)°C	and humidity < 70%.
Primary Standards	ID#	Cal Date (Certificate No.)	Scheduled Calibration
Power meter NRP	SN: 104778	06-Apr-16 (No. 217-02288/02289)	Apr-17
Power sensor NRP-Z91	SN: 103244	06-Apr-16 (No. 217-02288)	Apr-17
Power sensor NRP-Z91	SN: 103245	06-Apr-16 (No. 217-02289)	Apr-17
Reference 20 dB Attenuator	SN: 5058 (20k)	05-Apr-16 (No. 217-02292)	Apr-17
Type-N mismatch combination	SN: 5047.2 / 06327	05-Apr-16 (No. 217-02295)	Apr-17
Probe ER3DV6	SN: 2336	31-Dec-15 (No. ER3-2336 Dec15)	Dec-16
Probe H3DV6	SN: 6065	31-Dec-15 (No. H3-6065_Dec15)	Dec-16
	SN: 781	04-Sep-15 (No. DAE4-781_Sep15)	Sep-16
DAE4			
	ID#	Check Date (in house)	Scheduled Check
Secondary Standards	ID # SN: GB42420191	Check Date (in house) 09-Oct-09 (in house check Sep-14)	Scheduled Check In house check: Oct-17
Secondary Standards Power meter Agilent 4419B			
Secondary Standards Power meter Agilent 4419B Power sensor HP E4412A	SN: GB42420191	09-Oct-09 (in house check Sep-14)	In house check: Oct-17
DAE4 Secondary Standards Power meter Agilent 4419B Power sensor HP E4412A Power sensor HP 8482A RF generator R&S SMT-06	SN: GB42420191 SN: US38485102	09-Oct-09 (in house check Sep-14) 05-Jan-10 (in house check Sep-14)	In house check: Oct-17 In house check: Oct-17
Secondary Standards Power meter Agilent 4419B Power sensor HP E4412A Power sensor HP 8482A RF generator R&S SMT-06	SN: GB42420191 SN: US38485102 SN: US37295597	09-Oct-09 (in house check Sep-14) 05-Jan-10 (in house check Sep-14) 09-Oct-09 (in house check Sep-14)	In house check: Oct-17 In house check: Oct-17 In house check: Oct-17
Secondary Standards Power meter Agilent 4419B Power sensor HP E4412A Power sensor HP 8482A RF generator R&S SMT-06 Network Analyzer HP 8753E	SN: GB42420191 SN: US38485102 SN: US37295597 SN: 832283/011 SN: US37390585	09-Oct-09 (in house check Sep-14) 05-Jan-10 (in house check Sep-14) 09-Oct-09 (in house check Sep-14) 27-Aug-12 (in house check Oct-15) 18-Oct-01 (in house check Oct-15) Function	In house check: Oct-17 In house check: Oct-17 In house check: Oct-17 In house check: Oct-17
Secondary Standards Power meter Agilent 4419B Power sensor HP E4412A Power sensor HP 8482A RF generator R&S SMT-06	SN: GB42420191 SN: US38485102 SN: US37295597 SN: 832283/011 SN: US37390585	09-Oct-09 (in house check Sep-14) 05-Jan-10 (in house check Sep-14) 09-Oct-09 (in house check Sep-14) 27-Aug-12 (in house check Oct-15) 18-Oct-01 (in house check Oct-15)	In house check: Oct-17 In house check: Oct-17 In house check: Oct-17 In house check: Oct-17 In house check: Oct-17
Secondary Standards Power meter Agilent 4419B Power sensor HP E4412A Power sensor HP 8482A RF generator R&S SMT-06 Network Analyzer HP 8753E	SN: GB42420191 SN: US38485102 SN: US37295597 SN: 832283/011 SN: US37390585	09-Oct-09 (in house check Sep-14) 05-Jan-10 (in house check Sep-14) 09-Oct-09 (in house check Sep-14) 27-Aug-12 (in house check Oct-15) 18-Oct-01 (in house check Oct-15) Function	In house check: Oct-17 In house check: Oct-17 In house check: Oct-17 In house check: Oct-17 In house check: Oct-16

Certificate No: CD1880V3-1064_May16

Page 1 of 7

FCC ID: A3LSMG960U	PCTEST	HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 87 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Fage 67 01 104

Calibration Laboratory of Schmid & Partner Engineering AG Zeughausstrasse 43, 8004 Zurich, Switzerland





S Schweizerischer Kalibrierdienst
C Service suisse d'étalonnage
Servizio svizzero di taratura
Swiss Calibration Service

Accreditation No.: SCS 0108

Accredited by the Swiss Accreditation Service (SAS)

The Swiss Accreditation Service is one of the signatories to the EA

Multilateral Agreement for the recognition of calibration certificates

References

1] ANSI-C63.19-2011

American National Standard, Methods of Measurement of Compatibility between Wircless Communications Devices and Hearing Aids.

Methods Applied and Interpretation of Parameters:

- Coordinate System: y-axis is in the direction of the dipole arms. z-axis is from the basis of the antenna
 (mounted on the table) towards its feed point between the two dipole arms. x-axis is normal to the other axes.
 In coincidence with the standards [1], the measurement planes (probe sensor center) are selected to be at a
 distance of 15 mm above the top metal edge of the dipole arms.
- Measurement Conditions: Further details are available from the hardcopies at the end of the certificate. All
 figures stated in the certificate are valid at the frequency indicated. The forward power to the dipole connector
 is set with a calibrated power meter connected and monitored with an auxiliary power meter connected to a
 directional coupler. While the dipole under test is connected, the forward power is adjusted to the same level.
- Antenna Positioning: The dipole is mounted on a HAC Test Arch phantom using the matching dipole positioner with the arms horizontal and the feeding cable coming from the floor. The measurements are performed in a shielded room with absorbers around the setup to reduce the reflections. It is verified before the mounting of the dipole under the Test Arch phantom, that its arms are perfectly in a line. It is installed on the HAC dipole positioner with its arms parallel below the dielectric reference wire and able to move elastically in vertical direction without changing its relative position to the top center of the Test Arch phantom. The vertical distance to the probe is adjusted after dipole mounting with a DASYS Surface Check job. Before the measurement, the distance between phantom surface and probe tip is verified. The proper measurement distance is selected by choosing the matching section of the HAC Test Arch phantom with the proper device reference point (upper surface of the dipole) and the matching grid reference point (tip of the probe) considering the probe sensor offset. The vertical distance to the probe is essential for the accuracy.
- Feed Point Impedance and Return Loss: These parameters are measured using a HP 8753E Vector Network Analyzer. The impedance is specified at the SMA connector of the dipole. The influence of reflections was eliminating by applying the averaging function while moving the dipole in the air, at least 70cm away from any obstacles.
- E-field distribution: E field is measured in the x-y-plane with an isotropic ER3D-field probe with 100 mW forward power to the antenna feed point. In accordance with [1], the scan area is 20mm wide, its length exceeds the dipole arm length (180 or 90mm). The sensor center is 15 mm (in z) above the metal top of the dipole arms. Two 3D maxima are available near the end of the dipole arms. Assuming the dipole arms are perfectly in one line, the average of these two maxima (in subgrid 2 and subgrid 8) is determined to compensate for any non-parallelity to the measurement plane as well as the sensor displacement. The E-field value stated as calibration value represents the maximum of the interpolated 3D-E-field, in the plane above the dipole surface.

The reported uncertainty of measurement is stated as the standard uncertainty of measurement multiplied by the
coverage factor k=2, which for a normal distribution corresponds to a coverage probability of approximately 95%

Certificate No: CD1880V3-1064_May16 Page 2 of 7

 FCC ID: A3LSMG960U
 HAC (RF EMISSIONS) TEST REPORT
 Approved by: Quality Manager

 Filename:
 Test Dates:
 DUT Type:

 1M1711010281-13-R1.A3L
 11/06/2017 - 12/11/2017
 Portable Handset

Measurement Conditions

DASY system configuration, as far as not given on page 1.

DASY Version	DASY5	V52.8.8
Phantom	HAC Test Arch	
Distance Dipole Top - Probe Center	15 mm	
Scan resolution	dx, dy = 5 mm	
Frequency	1730 MHz ± 1 MHz 1880 MHz ± 1 MHz	
Input power drift	< 0.05 dB	

Maximum Field values at 1730 MHz

E-field 15 mm above dipole surface	condition	Interpolated maximum	
Maximum measured above high end	100 mW input power	96.1 V/m = 39.66 dBV/m	
Maximum measured above low end	100 mW input power	95.3 V/m = 39.58 dBV/m	
Averaged maximum above arm	100 mW input power	95.7 V/m ± 12.8 % (k=2)	

Maximum Field values at 1880 MHz

E-field 15 mm above dipole surface	condition	Interpolated maximum	
Maximum measured above high end	100 mW input power	91.2 V/m = 39.20 dBV/m	
Maximum measured above low end	100 mW input power	88.0 V/m = 38.89 dBV/m	
Averaged maximum above arm	100 mW input power	89.6 V/m ± 12.8 % (k=2)	

Certificate No: CD1880V3-1064_May16

Page 3 of 7

FCC ID: A3LSMG960U	PCTEST HA	C (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dago 90 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 89 of 104

Appendix (Additional assessments outside the scope of SCS 0108)

Antenna Parameters

Nominal Frequencies

Frequency	Return Loss	Impedance	
1730 MHz	24.0 dB	$49.6 \Omega + 6.3 jΩ$	
1880 MHz	19.8 dB	49.5 Ω + 10.2 jΩ	
1900 MHz	20.4 dB	52.9 Ω + 9.4 jΩ	
1950 MHz	26.8 dB	54.4 Ω + 1.8 jΩ	
2000 MHz	22.7 dB	$43.2 \Omega + 0.8 j\Omega$	

3.2 Antenna Design and Handling

The calibration dipole has a symmetric geometry with a built-in two stub matching network, which leads to the enhanced bandwidth.

The dipole is built of standard semirigid coaxial cable. The internal matching line is open ended. The antenna is therefore open for DC signals.

Do not apply force to dipole arms, as they are liable to bend. The soldered connections near the feedpoint may be damaged. After excessive mechanical stress or overheating, check the impedance characteristics to ensure that the internal matching network is not affected.

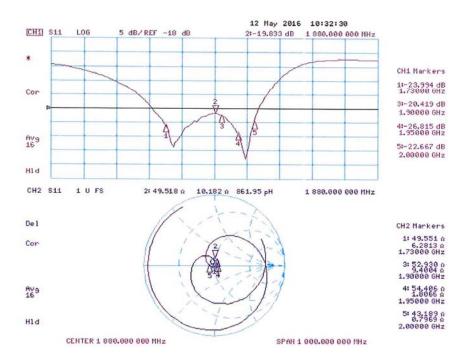
After long term use with 40W radiated power, only a slight warming of the dipole near the feedpoint can be measured.

Certificate No: CD1880V3-1064_May16

Page 4 of 7

FCC ID: A3LSMG960U	PCTEST HA	C (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dago 00 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 90 of 104

Impedance Measurement Plot



Certificate No: CD1880V3-1064_May16

Page 5 of 7

FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogg 01 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 91 of 104

DASY5 E-field Result

Date: 10.05.2016

Test Laboratory: SPEAG Lab2

DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: CD1880V3 - SN: 1064

Communication System: UID 0 - CW; Frequency: 1880 MHz, Frequency: 1730 MHz Medium parameters used: σ = 0 S/m, ε_r = 1; ρ = 1000 kg/m³ Phantom section: RF Section Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

DASY52 Configuration:

- Probe: ER3DV6 SN2336; ConvF(1, 1, 1); Calibrated: 31.12.2015;
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn781; Calibrated: 04.09.2015
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1070
- DASY52 52.8.8(1258); SEMCAD X 14.6.10(7372)

Dipole E-Field measurement @ 1880MHz/E-Scan - 1880MHz d=15mm/Hearing Aid Compatibility Test (41x181x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 151.7 V/m; Power Drift = -0.01 dB Applied MIF = 0.00 dB RF audio interference level = 39.20 dBV/m Emission category: M2

MIF scaled E-field

Grid 1 M2 39.04 dBV/m		Grid 3 M2 39.08 dBV/m
Grid 4 M2 36.76 dBV/m	Grid 5 M2 36.86 dBV/m	Grid 6 M2 36.75 dBV/m
	Grid 8 M2 38.89 dBV/m	Grid 9 M2 38.8 dBV/m

Certificate No: CD1880V3-1064_May16

Page 6 of 7

FCC ID: A3LSMG960U	PCTEST HA	C (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogo 02 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 92 of 104

Dipole E-Field measurement @ 1880MHz/E-Scan - 1730MHz d=15mm/Hearing Aid Compatibility Test (41x181x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 168.3 V/m; Power Drift = 0.00 dB

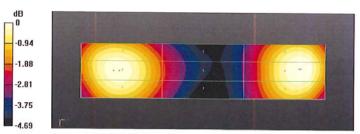
Applied MIF = 0.00 dB

RF audio interference level = 39.66 dBV/m

Emission category: M2

MIF scaled E-field

Grid 2 M2 39.58 dBV/m	Grid 3 M2 39.44 dBV/m
Grid 5 M2 37.56 dBV/m	
Grid 8 M2 39.66 dBV/m	



0 dB = 91.23 V/m = 39.20 dBV/m

Certificate No: CD1880V3-1064_May16

Page 7 of 7

FCC ID: A3LSMG960U	PCTEST HA	AC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 93 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		raye 93 01 104

Calibration Laboratory of Schmid & Partner Engineering AG Zeughausstrasse 43, 8004 Zurich, Switzerland





Schweizerischer Kalibrierdienst Service suisse d'étalonnage Servizio svizzero di taratura Swiss Calibration Service

Accredited by the Swiss Accreditation Service (SAS)

The Swiss Accreditation Service is one of the signatories to the EA

Multilateral Agreement for the recognition of calibration certificates

Client

PC Test

Certificate No: CD2600V3-1013_Jun17/2

Accreditation No.: SCS 0108

CALIBRATION CERTIFICATE (Replacement of No:CD2600V3-1013_Jun17)

Object

CD2600V3 - SN: 1013

Calibration procedure(s)

QA CAL-20.v6

Calibration procedure for dipoles in air

08/02/201

Calibration date:

June 14, 2017

This calibration certificate documents the traceability to national standards, which realize the physical units of measurements (SI).

The measurements and the uncertainties with confidence probability are given on the following pages and are part of the certificate.

All calibrations have been conducted in the closed laboratory facility: environment temperature (22 ± 3)°C and humidity < 70%.

Calibration Equipment used (M&TE critical for calibration)

Primary Standards	ID#	Cal Date (Certificate No.)	Scheduled Calibration
Power meter NRP	SN: 104778	04-Apr-17 (No. 217-02521/02522)	Apr-18
Power sensor NRP-Z91	SN: 103244	04-Apr-17 (No. 217-02521)	Apr-18
Power sensor NRP-Z91	SN: 103245	04-Apr-17 (No. 217-02522)	Apr-18
Reference 20 dB Attenuator	SN: 5058 (20k)	07-Apr-17 (No. 217-02528)	Apr-18
Type-N mismatch combination	SN: 5047.2 / 06327	07-Apr-17 (No. 217-02529)	Apr-18
Probe EF3DV6	SN: 4013	21-Jun-16 (No. EF3-4013_Jun16)	Jun-17
DAE4	SN: 781	02-Sep-16 (No. DAE4-781_Sep16)	Sep-17
Secondary Standards	ID#	Check Date (in house)	Scheduled Check
Power meter Agilent 4419B	SN: GB42420191	09-Oct-09 (in house check Sep-14)	In house check: Oct-17
Power sensor HP E4412A	SN: US38485102	05-Jan-10 (in house check Sep-14)	In house check: Oct-17
Power sensor HP 8482A	SN: US37295597	09-Oct-09 (in house check Sep-14)	In house check: Oct-17
RF generator R&S SMT-06	SN: 832283/011	27-Aug-12 (in house check Oct-15)	In house check: Oct-17
Network Analyzer HP 8753E	SN: US37390585	18-Oct-01 (in house check Oct-16)	In house check: Oct-17
	Name	Function	Signature
Calibrated by:	Johannes Kurikka	Laboratory Technician	me la
Approved by:	Kalja Pokovic	Technical Manager	000

Issued: July 20, 2017

This calibration certificate shall not be reproduced except in full without written approval of the laboratory.

Certificate No: CD2600V3-1013_Jun17/2

Page 1 of 5

FCC ID: A3LSMG960U	PCTEST HA	C (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 94 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		raye 94 01 104

Calibration Laboratory of Schmid & Partner Engineering AG Zeughausstrasse 43, 8004 Zurich, Switzerland





Schweizerischer Kalibrierdienst Service suisse d'étalonnage Servizio svizzero di taratura Swiss Calibration Service

Accreditation No.: SCS 0108

Accredited by the Swiss Accreditation Service (SAS)

The Swiss Accreditation Service is one of the signatories to the EA

Multilateral Agreement for the recognition of calibration certificates

References

 ANSI-C63.19-2011
 American National Standard, Methods of Measurement of Compatibility between Wireless Communications Devices and Hearing Aids.

Methods Applied and Interpretation of Parameters:

- Coordinate System: y-axis is in the direction of the dipole arms. z-axis is from the basis of the antenna
 (mounted on the table) towards its feed point between the two dipole arms. x-axis is normal to the other axes.
 In coincidence with the standards [1], the measurement planes (probe sensor center) are selected to be at a
 distance of 15 mm above the top metal edge of the dipole arms.
- Measurement Conditions: Further details are available from the hardcopies at the end of the certificate. All
 figures stated in the certificate are valid at the frequency indicated. The forward power to the dipole connector
 is set with a calibrated power meter connected and monitored with an auxiliary power meter connected to a
 directional coupler. While the dipole under test is connected, the forward power is adjusted to the same level.
- Antenna Positioning: The dipole is mounted on a HAC Test Arch phantom using the matching dipole positioner with the arms horizontal and the feeding cable coming from the floor. The measurements are performed in a shielded room with absorbers around the setup to reduce the reflections. It is verified before the mounting of the dipole under the Test Arch phantom, that its arms are perfectly in a line. It is installed on the HAC dipole positioner with its arms parallel below the dielectric reference wire and able to move elastically in vertical direction without changing its relative position to the top center of the Test Arch phantom. The vertical distance to the probe is adjusted after dipole mounting with a DASY5 Surface Check job. Before the measurement, the distance between phantom surface and probe tip is verified. The proper measurement distance is selected by choosing the matching section of the HAC Test Arch phantom with the proper device reference point (upper surface of the dipole) and the matching grid reference point (tip of the probe) considering the probe sensor offset. The vertical distance to the probe is essential for the accuracy.
- Feed Point Impedance and Return Loss: These parameters are measured using a HP 8753E Vector Network Analyzer. The impedance is specified at the SMA connector of the dipole. The influence of reflections was eliminating by applying the averaging function while moving the dipole in the air, at least 70cm away from any obstacles
- E-field distribution: E field is measured in the x-y-plane with an isotropic ER3D-field probe with 100 mW forward power to the antenna feed point. In accordance with [1], the scan area is 20mm wide, its length exceeds the dipole arm length (180 or 90mm). The sensor center is 15 mm (in z) above the metal top of the dipole arms. Two 3D maxima are available near the end of the dipole arms. Assuming the dipole arms are perfectly in one line, the average of these two maxima (in subgrid 2 and subgrid 8) is determined to compensate for any non-parallelity to the measurement plane as well as the sensor displacement. The E-field value stated as calibration value represents the maximum of the interpolated 3D-E-field, in the plane above the dipole surface.

The reported uncertainty of measurement is stated as the standard uncertainty of measurement multiplied by the
coverage factor k=2, which for a normal distribution corresponds to a coverage probability of approximately 95%,

Certificate No: CD2600V3-1013	Jun 17/2	Page 2 of 5		

FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogo 05 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 95 of 104

Measurement Conditions

DASY system configuration, as far as not given on page 1

DASY Version	DASY5	V52.10.0
Phantom	HAC Test Arch	
Distance Dipole Top - Probe Center	15 mm	
Scan resolution	dx, dy = 5 mm	
Frequency	2600 MHz ± 1 MHz	
Input power drift	< 0.05 dB	

Maximum Field values at 2600 MHz

E-field 15 mm above dipole surface	condition	Interpolated maximum
Maximum measured above high end	100 mW input power	84.9 V/m = 38.58 dBV/m
Maximum measured above low end	100 mW input power	84.0 V/m = 38.48 dBV/m
Averaged maximum above arm	100 mW input power	84.5 V/m ± 12.8 % (k=2)

Appendix (Additional assessments outside the scope of SCS 0108)

Antenna Parameters

Frequency	Return Loss	Impedance	
2450 MHz	23.3 dB	44.8 Ω - 3.8 jΩ	
2550 MHz	32.2 dB	51.0 Ω + 2.3 jΩ	
2600 MHz	29.5 dB	53.4 Ω - 0.3 jΩ	
2650 MHz	27.0 dB	53.2 Ω - 3.3 jΩ	
2750 MHz	19.7 dB	45.7 Ω - 8.9 jΩ	

3.2 Antenna Design and Handling

The calibration dipole has a symmetric geometry with a built-in two stub matching network, which leads to the enhanced bandwidth.

The dipole is built of standard semirigid coaxial cable. The internal matching line is open ended. The antenna is therefore open for DC signals.

Do not apply force to dipole arms, as they are liable to bend. The soldered connections near the feedpoint may be damaged. After excessive mechanical stress or overheating, check the impedance characteristics to ensure that the internal matching network is not affected.

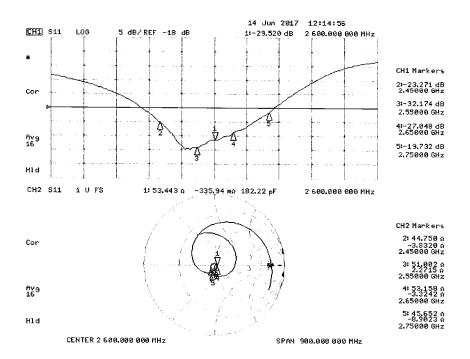
After long term use with 40W radiated power, only a slight warming of the dipole near the feedpoint can be measured.

Certificate No: CD2600V3-1013_Jun17/2

Page 3 of 5

FCC ID: A3LSMG960U	PCTEST	HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 96 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Fage 90 01 104

Impedance Measurement Plot



Certificate No: CD2600V3-1013_Jun17/2

Page 4 of 5

FCC ID: A3LSMG960U	PCTEST*	AC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 97 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		rage 97 01 104

DASY5 E-field Result

Date: 14.06.2017

Test Laboratory: SPEAG Lab2

DUT: HAC Dipole 2600 MHz; Type: CD2600V3; Serial: CD2600V3 - SN: 1013

Communication System: UID 0 - CW ; Frequency: 2600 MHz Medium parameters used: σ = 0 S/m, ϵ_{r} = 1; ρ = 1000 kg/m³ Phantom section: RF Section

DASY52 Configuration:

- Probe: EF3DV3 SN4013; ConvF(1, 1, 1); Calibrated:21.06.2016;
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn781; Calibrated: 02.09.2016
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1070
- DASY52 52.10.0(1444); SEMCAD X 14.6.10(7416)

Dipole E-Field measurement @ 2600MHz - with EF_4013/E-Scan - 2600MHz d=15mm/Hearing Aid Compatibility Test (41x181x1): Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 68.41 V/m; Power Drift = -0.01 dB

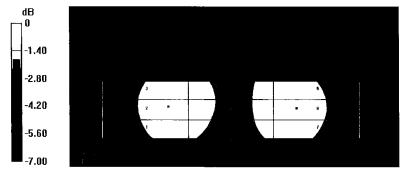
PMR not calibrated. PMF = 1.000 is applied.

E-field emissions = 84.92 V/m

Near-field category: M3 (AWF 0 dB)

PMF scaled E-field

Grid 1 M3 81.71 V/m	
Grid 4 M3 77.39 V/m	
Grid 7 M3 82.82 V/m	



0 dB = 84.92 V/m = 38.58 dBV/m

Certificate No: CD2600V3-1013_Jun17/2

Page 5 of 5

FCC ID: A3LSMG960U	PCTEST	HAC (RF EMISSIONS) TEST REPORT	SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 98 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		raye 90 01 104

16. CONCLUSION

The measurements, taken in accordance with the procedures provided in the CTIA Test Plan for Hearing Aid Compatibility Rev 3.1, February 2017, indicate that the wireless communications device complies with the HAC limits specified in the ANSI C63.19 Standard and FCC WT Docket No. 01-309 RM-8658. Precise laboratory measures were taken to assure repeatability of the tests. The tested device complies with the requirements in respect to all parameters specific to the test. The test results and statements relate only to the item(s) tested.

Please note that the M-rating for this equipment only represents the field interference possible against a hypothetical and typical hearing aid. The measurement system and techniques presented in this evaluation are proposed in the ANSI standard as a means of best approximating wireless device compatibility with a hearing-aid. The literature is under continual re-construction.

FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Page 99 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Fage 99 01 104

17. REFERENCES

- ANSI/IEEE C63.19-2011, "American National Standard for Methods of Measurement of Compatibility between Wireless Communication Devices and Hearing Aids.", New York, NY, IEEE, May 2011
- 2. CTIA Certification Program, "Test Plan for Hearing Aid Compatibility Rev 3.1", Washington, DC, CTIA, February 2017
- 3. FCC Office of Engineering and Technology KDB, "285076 D01 HAC Guidance v05," September 13, 2017
- 4. FCC Office of Engineering and Technology KDB, "285076 D02 T-Coil Testing for CMRS IP v03," September 13, 2017
- FCC Public Notice DA 06-1215, Wireless Telecommunications Bureau and Office of Engineering and Technology Clarify Use of Revised Wireless Phone Hearing Aid Compatibility Standard, June 6, 2006
- 6. FCC 3G Review Guidance, Laboratory Division OET FCC, May/June 2006
- 7. Berger, H. S., "Compatibility Between Hearing Aids and Wireless Devices," Electronic Industries Forum, Boston, MA, May, 1997
- Berger, H. S., "Hearing Aid and Cellular Phone Compatibility: Working Toward Solutions," Wireless Telephones and Hearing Aids: New Challenges for Audiology, Gallaudet University, Washington, D.C., May, 1997 (To be reprinted in the American Journal of Audiology).
- Berger, H. S., "Hearing Aid Compatibility with Wireless Communications Devices, " IEEE International Symposium on Electromagnetic Compatibility, Austin, TX, August, 1997.
- 10. Bronaugh, E. L., "Simplifying EMI Immunity (Susceptibility) Tests in TEM Cells," in the 1990 IEEE International Symposium on Electromagnetic Compatibility Symposium Record, Washington, D.C., August 1990, pp. 488-491
- 11. Byme, D. and Dillon, H., The National Acoustics Laboratory (NAL) New Procedure for Selecting the Gain and Frequency Response of a Hearing Aid, Ear and Hearing 7:257-265, 1986.
- 12. Crawford, M. L., "Measurement of Electromagnetic Radiation from Electronic Equipment using TEM Transmission Cells, "U.S. Department of Commerce, National Bureau of Standards, NBSIR 73-306, Feb. 1973.
- 13. Crawford, M. L., and Workman, J. L., "Using a TEM Cell for EMC Measurements of Electronic Equipment," U.S. Department of Commerce, National Bureau of Standards. Technical Note 1013, July 1981.
- 14. Decker, W. F., Crawford, M. L., and Wilson, W. A., "Construction of a Large Transverse Electromagnetic Cell", U.S. Department of Commerce, National Bureau of Standards, Technical Note 1011, Feb. 1979.
- 15. EHIMA GSM Project, Development phase, Project Report (1st part) Revision A. Technical-Audiological Laboratory and Telecom Denmark, October 1993.
- 16. EHIMA GSM Project, Development phase, Part II Project Report. Technical-Audiological Laboratory and Telecom Denmark, June 1994.
- 17. EHIMA GSM Project Final Report, Hearing Aids and GSM Mobile Telephones: Interference Problems, Methods of Measurement and Levels of Immunity. Technical-Audiological Laboratory and Telecom Denmark, 1995.
- 18. HAMPIS Report, Comparison of Mobile phone electromagnetic near field with an upscaled electromagnetic far field, using hearing aid as reference, 21 October 1999.

FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager
Filename:	Test Dates:	DUT Type:		Dogg 100 of 104
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 100 of 104

- 19. Hearing Aids/GSM, Report from OTWIDAM, Technical-Audiological Laboratory and Telecom Denmark, April 1993
- 20. IEEE 100, The Authoritative Dictionary of IEEE Standards Terms, Seventh Edition.
- Joyner, K. H, et. al., Interference to Hearing Aids by the New Digital Mobile Telephone System, Global System for Mobile (GSM) Communication Standard, National Acoustic Laboratory, Australian Hearing Series, Sydney 1993.
- 22. Joyner, K. H., et. al., Interference to Hearing Aids by the Digital Mobile Telephone System, Global System for Mobile Communications (GSM), NAL Report #131, National Acoustic Laboratory, Australian Hearing Series, Sydney, 1995.
- 23. Konigstein, D., and Hansen, D., "A New Family of TEM Cells with enlarged bandwidth and Optimized working Volume," in the Proceedings of the 7th International Symposium on EMC, Zurich, Switzerland, March 1987; 50:9, pp. 127-132.
- 24. Kuk, F., and Hjorstgaard, N. K., "Factors affecting interference from digital cellular telephones," Hearing Journal, 1997; 50:9, pp 32-34.
- 25. Ma, M. A., and Kanda, M., "Electromagnetic Compatibility and Interference Metrology," U.S. Department of Commerce, National Bureau of Standards, Technical Note 1099, July 1986, pp. 17-43.
- 26. Ma, M. A., Sreenivashiah, I., and Chang, D. C., "A Method of Determining the Emission and Susceptibility Levels of Electrically Small Objects Using a TEM Cell," U.S. Department of Commerce, National Bureau of Standards, Technial Note 1040, July 1981.
- 27. McCandless, G. A., and Lyregaard, P. E., Prescription of Gain/Output (POGO) for Hearing Aids, Hearing Instruments 1:16-21, 1983
- 28. Skopec, M., "Hearing Aid Electromagnetic Interference from Digital Wireless Telephones, "IEEE Transactions on Rehabilitation Engineering, vol. 6, no. 2, pp. 235-239, June 1998.
- 29. Technical Report, GSM 05.90, GSM EMC Considerations, European Telecommunications Standards Institute, January 1993.
- 30. Victorian, T. A., "Digital Cellular Telephone Interference and Hearing Aid Compatibility—an Update," Hearing Journal 1998; 51:10, pp. 53-60
- 31. Wong, G. S. K., and Embleton, T. F. W., eds., AIP Handbook of Condenser Microphones: Theory, Calibration and Measurements, AIP Press.

FCC ID: A3LSMG960U	HAC (RF EMISSIONS) TEST REPORT		SAMSUNG	Approved by: Quality Manager	
Filename:	Test Dates:	DUT Type:		Dogg 101 of 104	
1M1711010281-13-R1.A3L	11/06/2017 - 12/11/2017	Portable Handset		Page 101 of 104	